

ARM®-based 32-bit Cortex®-M4 MCU+FPU with 256 to 1024 KB Flash, sLib, 17 timers, 3 ADCs, 21 communication interfaces (USBFS and Ethernet)

Feature

- **AEC Q-100 Grade 2 certification**
- **Core: ARM® 32-bit Cortex®-M4 CPU with FPU**
 - 200 MHz maximum frequency, with a memory protection unit (MPU), single-cycle multiplication and hardware division
 - Floating point unit (FPU)
 - DSP instructions
- **Memories**
 - 256 to 1024 KBytes of internal Flash memory
 - sLib: configurable part of main Flash set as a library area with code executable but secured, non-readable
 - SPIM interface: Extra interfacing up to 16 Mbytes of the external SPI Flash
 - Up to 96+128 KBytes of SRAM
 - External memory controller (XMC) with 16-bit data bus supporting multiplexed PSRAM/NOR and NAND memories
- **XMC as LCD parallel interface, compatible with 8080/6800 modes**
- **Power control (PWC)**
 - 2.6 to 3.6 V application supply
 - Power on reset (POR), low voltage reset (LVR), and power voltage monitoring (PVM)
 - Low power modes: Sleep, Deepsleep, and Standby modes
 - V_{BAT} supply for LEXT, RTC, and forty-two 16-bit battery powered registers (BPR)
- **Clock and reset management (CRM)**
 - 4 to 25 MHz crystal oscillator (HEXT)
 - 48 MHz internal factory-trimmed high speed internal clock (HICK), 1 % accuracy at T_A = 25 °C and 2.5 % accuracy at T_A = -40 to +105 °C, with automatic clock calibration (ACC)
 - 32 kHz crystal oscillator (LEXT)
 - Low speed internal clock (LICK)
- **Analog**
 - 3 x 12-bit 2 MSPS A/D converters, up to 16 input channels
 - Temperature sensor (V_{TS}) and internal reference voltage (V_{INTRV})
 - 2 x 12-bit D/A converters
- **DMA: 14-channel DMA controller**
- **Up to 80 fast GPIOs**
 - All mappable on 16 external interrupts (EXINT)
 - Almost all 5 V-tolerant
- **Up to 17 timers (TMR)**
 - Up to 2 x 16-bit motor control PWM advanced timers with dead-time generator and emergency brake
 - Up to 8 x 16-bit + 2 x 32-bit timers, each with 4 IC/OC/PWM or pulse counter and quadrature encoder input
 - 2 x 16-bit basic timers to drive the DAC
 - 2 x watchdog timers (general WDT and windowed WWDT)
 - SysTick timer: a 24-bit downcounter
- **Up to 21 communication interfaces**
 - Up to 3 x I²C interfaces (SMBus/PMBus)
 - Up to 8 x USARTs (ISO7816 interface, LIN, IrDA capability, modem control)
 - Up to 4 x SPIs (50 Mbit/s), all with I²S interface multiplexed, I²S2/I²S3 support full-duplex mode
 - Up to 2 x CAN interfaces (2.0B Active)
 - USB 2.0 full speed interface supporting crystal-less mode
 - Up to 2 x SDIO interfaces
 - 10/100M Ethernet MAC (EMAC) with dedicated DMA and SRAM (4 KBytes): IEEE1588 hardware support, MII/RMII available
- **CRC calculation unit**
- **96-bit unique ID (UID)**
- **Debug mode**
 - Serial wire debug (SWD) and JTAG interfaces
 - Cortex®-M4 Embedded Trace Macrocell (ETM)
- **Operating temperatures: -40 to +105 °C**
- **Packages**
 - LQFP100 14 x 14 mm
 - LQFP64 10 x 10 mm
 - LQFP48 7 x 7 mm
 - QFN48 6 x 6 mm

Table 1. Device summary

Internal Flash	Part number
1024 KBytes	AT32A403ACGT7, AT32A403ACGU7, AT32A403ARGT7, AT32A403AVGT7
512 KBytes	AT32A403ACET7, AT32A403ACEU7, AT32A403ARET7, AT32A403AVET7
256 KBytes	AT32A403ACCT7, AT32A403ACCU7, AT32A403ARCT7, AT32A403AVCT7

1 Descriptions

The AT32A403A series microcontroller has passed AEC-Q-100 Grade 2 certification.

The AT32A403A is based on the high-performance ARM®Cortex®-M4 32-bit RISC core operating at a frequency of up to 200 MHz. The Cortex®-M4 core features a Floating point unit (FPU) single precision which supports all ARM® single-precision data processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The AT32A403A incorporates high-speed embedded memories (up to 1024 KBytes of internal Flash memory, 96+128 KBytes of SRAM), external SPI Flash (up to 16 MBytes addressing capability), and a wide range of enhanced GPIOs and peripherals connected to two APB buses. Any block of the embedded Flash memory can be protected by the “sLib” (security library), functioning as a security area with code-executable only.

The AT32A403A offers three 12-bit ADCs, two 12-bit DACs, eight general-purpose 16-bit timers plus two general-purpose 32-bit timers, and up to two PWM timers for motor control. It supports standard and advanced communication interfaces: up to three I²Cs, four SPIs (all multiplexed as I²Ss), two SDIOs, eight USARTs/UARTs, an USBFS, two CANs, and one Ethernet MAC.

The AT32A403A operates in the -40 to +105 °C temperature range, from a 2.6 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power application.

The AT32A403A offers devices in different package types. They are fully pin-to-pin, software and functionally compatible with the entire AT32A403A series devices, except that the configurations of peripherals are not completely identical, depending on the package types.

Table 2. AT32A403A features and peripheral counts

Part Number		AT32A403AxxU7			AT32A403AxxT7								
		CC	CE	CG	CC	CE	CG	RC	RE	RG	VC	VE	VG
CPU frequency (MHz)		200											
Int. Flash ⁽¹⁾⁽²⁾	ZW (KBytes)	256	256	256	256	256	256	256	256	256	256	256	256
	NZW (KBytes)	0	256	768	0	256	768	0	256	768	0	256	768
	Total (KBytes)	256	512	1024	256	512	1024	256	512	1024	256	512	1024
SRAM ⁽²⁾ (KBytes)		96 + 128											
SPIM ⁽³⁾		1 ch / up to 16 MB											
XMC		-			-			1 ⁽⁴⁾			1		
Timers	Advanced	2			2			2			2		
	32-bit general-purpose	2			2			2			2		
	16-bit general-purpose	8			8			8			8		
	Basic	2			2			2			2		
	SysTick	1			1			1			1		
	WDT	1			1			1			1		
	WWDT	1			1			1			1		
	RTC	1			1			1			1		
Communication	I ² C	3			3			3			3		
	SPI ⁽⁵⁾	4			4			4			4		
	I ² S ⁽⁵⁾	4 (2 full-duplex)			4 (2 full-duplex)			4 (2 full-duplex)			4 (2 full-duplex)		
	USART + UART	3 + 4 ⁽⁶⁾			3 + 4 ⁽⁶⁾			4 + 4			4 + 4		
	SDIO	1 ⁽⁷⁾			1 ⁽⁷⁾			2			2		
	USBFS device	1			1			1			1		
	CAN	2			2			2			2		
	Ethernet MAC	-			-			1			1		
Analog	12-bit ADC numbers/channels	3											
		10			10			16			16		
	12-bit DAC numbers	2											
GPIO		37			37			51			80		
Operating temperatures		-40 to +105 °C											
Packages		QFN48 6 x 6 mm			LQFP48 7 x 7 mm			LQFP64 10 x 10 mm			LQFP100 14 x 14 mm		

- (1) ZW = zero wait-state, up to SYSCLK 200 MHz
NZW = non-zero wait-state
- (2) The internal Flash and SRAM sizes are configurable with User System Data. Take the AT32A403AVGT7 as an example, on which the Flash/SRAM can be configured into two options below:
 - ZW: 256 KBytes, NZW: 768 KBytes, SRAM: 96 KBytes;
 - ZW: 128 KBytes, NZW: 896 KBytes, SRAM: 224 KBytes.
- (3) SPIM = External four-wire SPI Flash memory extension, for both program execution and data storage with encryption capability.
- (4) For LQFP64 package, XMC only supports the LCD panel with 8-bit mode.
- (5) Half-duplexed I²S share the same pin with SPI.
- (6) For LQFP48 and QFN48 packages, UART8 is not available and USART6 is used as UART for no CK pin.
- (7) For LQFP48 and QFN48 packages, only SDIO2 exists and supports maximum 4-bit (D0~D3) mode.

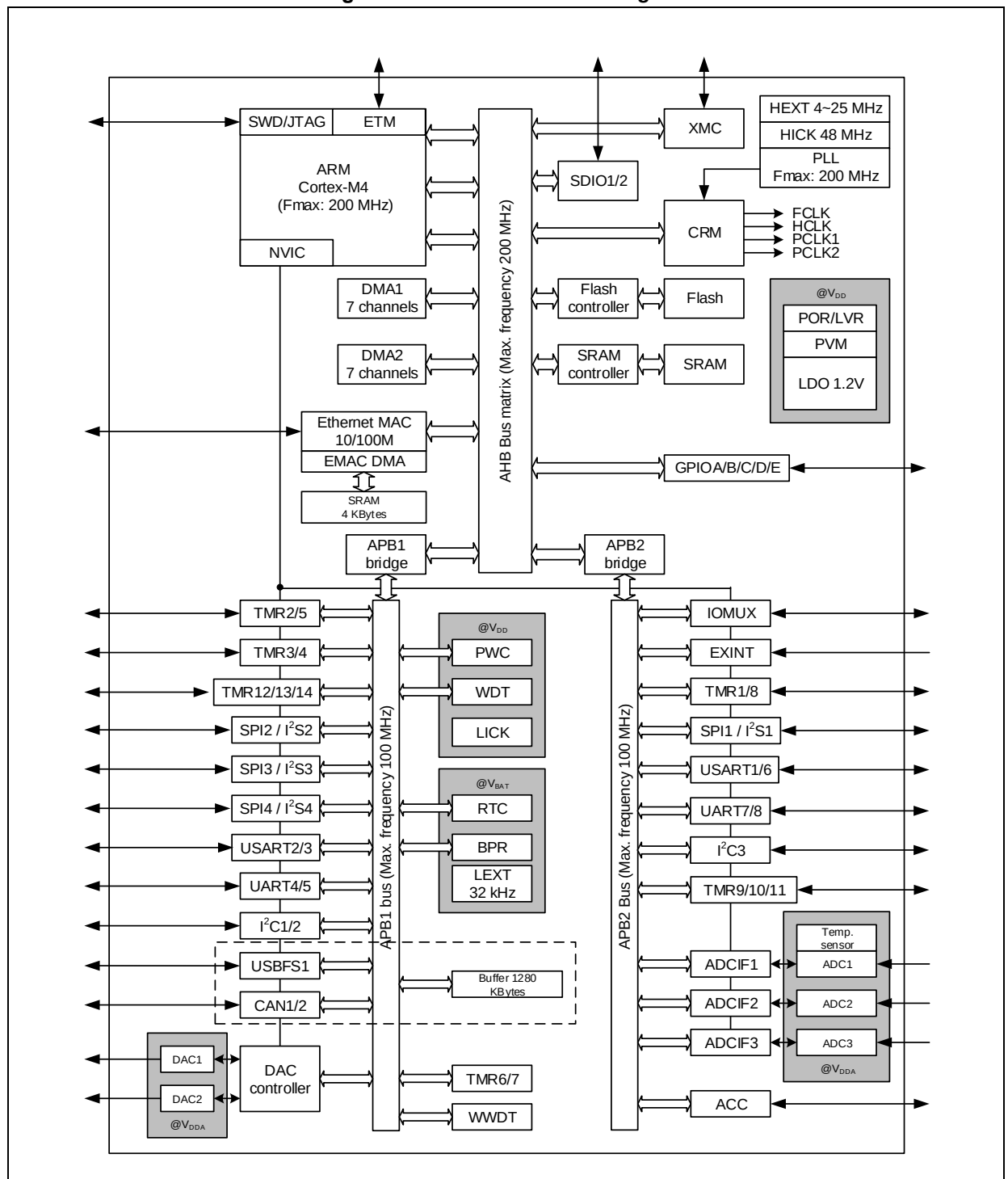
2 Functional overview

2.1 ARM® Cortex®-M4 with FPU

The ARM®Cortex®-M4 processor is the latest generation of ARM® processors for embedded systems. It is a 32-bit RISC processor that features exceptional code efficiency, outstanding computing performance and advanced response to interrupts. The processor supports a set of DSP instructions which enable efficient signal processing and complex algorithm execution. Its single precision FPU (floating point unit) speeds up floating point calculation while avoiding saturation.

Figure 1 shows the general block diagram of the AT32A403A.

Figure 1. AT32A403A block diagram



2.2 Memory

2.2.1 Internal Flash memory

Up to 1024 KBytes of embedded Flash is available for storing programs and data. Any part of the embedded Flash memory can be protected by the sLib (security library), a security area that is code-executable only but non-readable. “sLib” is a mechanism designed to protect the intelligence of solution vendors and facilitate the second-level development by customers.

Additionally, there is an external four-wire SPI Flash memory interface available for accessing up to 16MB. The external SPI Flash memory is used as an extended Flash memory bank 3. Ciphertext protection feature is also supported. Thus it is possible to select whether to encrypt data by setting the user system data. The range to be encrypted is configured through the corresponding register.

There is another 18-KByte boot code area in which the bootloader is stored.

A User System Data block is included, which is used to configure the hardware operations such as read/erase/write protection and watchdog self-enable. User System Data allows the independent configuration of Flash memory erase/write and access protection.

2.2.2 Memory protection unit (MPU)

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area consists of up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the entire 4 gigabytes of addressable memory.

The MPU is especially suited to the applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system).

2.2.3 Embedded SRAM

The device offers up to 224 KBytes of embedded SRAM that is accessible (read/write) at CPU clock speed with 0 wait states.

2.2.4 External memory controller (XMC)

The XMC peripheral is embedded in the AT32A403A series. It has two Chip Select outputs supporting the following modes: multiplexed PSRAM/NOR and 16-bit/8-bit NAND memory.

Main features:

- Write buffer area
- Code execution from external memory of the multiplexed PSRAM/NOR

The XMC can be configured to interface with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes.

2.3 Interrupts

2.3.1 Nested vectored interrupt controller (NVIC)

The AT32A403A series embeds a nested vectored interrupt controller able to manage 16 priority levels and handle maskable interrupt channels plus the 16 interrupt lines of the Cortex®-M4 core. This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.3.2 External interrupts (EXINT)

The external interrupt (EXINT), which is connected directly with NVIC, consists of 19 edge detector lines used to generate interrupt requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The external interrupt lines connects up to 16 GPIOs.

2.4 Power control (PWC)

2.4.1 Power supply schemes

- $V_{DD} = 2.6\sim 3.6$ V: external power supply for GPIOs and the internal block such as regulator (LDO), provided externally through V_{DD} pins.
- $V_{DDA} = 2.6\sim 3.6$ V: external analog power supply for ADC and DAC. V_{DDA} and V_{SSA} must be the same voltage potential as V_{DD} and V_{SS} , respectively.
- $V_{BAT} = 1.8\sim 3.6$ V: power supply for V_{BAT} domain through the external battery or super capacitor, or from V_{DD} when the external battery or super capacitor is not present. V_{BAT} (through power switch) supplies the RTC, external crystal 32 kHz (LEXT), and battery powered registers (BPR) when V_{DD} is not present.

2.4.2 Reset and power voltage monitoring (POR / LVR / PVM)

The device has an integrated power-on reset (POR)/low voltage reset (LVR) circuitry. It is always active, and allows proper operation starting from/down to 2.6 V. The device remains in reset mode when V_{DD} is below a specified threshold (V_{LVR}) without the need for an external reset circuit.

The device features an embedded power voltage monitor (PVM) that monitors the V_{DD} power supply and compares it to the V_{PVM} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVM} threshold and/or when V_{DD} rises above the V_{PVM} threshold. The PVM is enabled by software.

2.4.3 Voltage regulator (LDO)

The LDO has three operation modes: normal, low-power, and power down.

- Normal mode: It is used in Run/Sleep mode and in Deepsleep mode;
- Low-power mode: It can be used in Deepsleep mode;
- Power-down mode: It is used in Standby mode: The LDO output is in high impedance and the kernel circuitry is powered down but the contents of the registers and SRAM are lost.

This LDO operates always in normal mode after reset.

2.4.4 Low-power modes

The AT32A403A series supports three low-power modes:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Deepsleep mode**

Deepsleep mode achieves low power consumption while retaining the content of SRAM and registers. All clocks in the LDO domain are stopped, disabling the PLL, the HICK clock, and the HEXT crystal oscillator. The voltage regulator (LDO) can also be put in normal or low-power mode.

The device can be woken up from Deepsleep mode by any of the EXINT line. The EXINT line source can be one of the 16 external lines, the PVM output, the RTC alarm, the USBFS wakeup, or EMAC wakeup.

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire LDO domain is powered off. The PLL, the HICK clock and the HEXT crystal oscillator are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the BPR domain, RTC and Standby circuitry.

The device leaves Standby mode when an external reset (NRST pin), a WDT reset, a rising edge on the WKUP pin, or an RTC alarm occurs.

Note: The RTC and the corresponding clock sources are not stopped by entering Deepsleep or Standby mode. WDT depends on User System Data setting.

2.5 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from the internal Flash memory. The AT32A403AxG gives users an option to boot from any of two memory banks (Bank 1 and Bank 2). By default, boot from Flash memory Bank 1 is selected. User can also choose to boot from Flash memory Bank 2 using the User System Data;
- Boot from boot code area;
- Boot from embedded SRAM.

The bootloader is stored in boot code area. It is used to reprogram the Flash memory through USART1, USART2, or USBFS1. Of them, USBFS1 supports crystal-less operation. If the SPIM_IO0/1 pin is configured to be shared with USBFS1 pin, the SPIM Flash memory Bank 3 cannot be programmed through USBFS1. [Table 3](#) presents AT32A403A pin configurations relative to Bootloader.

Table 3. The Bootloader supporting part numbers and pin configurations

Interface	Part number	Pin
USART1	All part numbers	PA9: USART1_TX PA10: USART1_RX
USART2	AT32A403AVGT7	PD5: USART2_TX (remapped) PD6: USART2_RX (remapped)
	Part numbers except AT32A403AVGT7	PA2: USART2_TX PA3: USART2_RX
USBFS1	All part numbers	PA11: USBFS1_D- PA12: USBFS1_D+

2.6 Clocks

On reset, the internal 48 MHz clock (HICK) divided by 6 (that is 8 MHz) is selected as the default CPU clock. The application can select an external 4 to 25 MHz clock (HEXT) as a system clock. This clock can be monitored for failure. If failure is detected, HEXT will be switched off and the system automatically switches back to the internal HICK. A software interrupt is generated. Similarly, the system takes the same action once HEXT fails when it is used as the source of PLL. Multiple prescalers are available to allow the configuration of the AHB and the APB (APB1 and APB2) frequencies. The maximum frequency of the AHB domain is 200 MHz. The maximum frequency of the APB domain is 100 MHz.

The AT32A403A series embeds an automatic clock calibration (ACC) block, which calibrates the internal 48 MHz HICK clock, assuring the most precise accuracy of the HICK in the full range of the operating temperatures.

2.7 General-purpose inputs / outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down), or as multiple function. Most of the GPIO pins are shared with digital or analog peripherals. All GPIOs are high current-capable.

The GPIO's configuration can be locked, if needed, in order to avoid spurious writing to the GPIO registers by following a specific sequence.

2.8 Remap capability

This feature allows the use of a maximum number of peripherals in a given application. Indeed, multiple functions are available not only on the default pins but also on other specific pins onto which they are remappable. This has the advantage of making board design and port usage much more flexible.

For details refer to [Table 6](#), which gives a list of remappable peripherals and the pins onto which they can be remapped. See the AT32A403A reference manual for software considerations.

2.9 Direct Memory Access Controller (DMA)

The device features two general-purpose DMAs (7 channels for DMA1 and 7 channels for DMA2). They are able to manage memory-to-memory, peripheral-to-memory, and memory-to-peripheral transfers. The two DMA controllers support circular buffer management, so that no interrupt is generated when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, advanced, general-purpose, and basic timers TMRx, DAC, I²S, SDIO, and ADC.

2.10 Timers (TMR)

The AT32A403A device includes two advanced timers, ten general-purpose timers, two basic timers and a SysTick timer.

The table below compares the features of the advanced, general-purpose, and basic timers.

Table 4. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TMR1, TMR8	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	Yes
TMR2, TMR5	16-bit or 32-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TMR3, TMR4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TMR9, TMR12	16-bit	Up	Any integer between 1 and 65536	No	2	No
TMR10, TMR11 TMR13, TMR14	16-bit	Up	Any integer between 1 and 65536	No	1	No
TMR6, TMR7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

2.10.1 Advanced timers (TMR1 and TMR8)

The two advanced timers (TMR1 and TMR8) can each be seen as three-phase PWM generators multiplexed onto 6 channels. They have complementary PWM outputs with programmable dead-time insertion. They can also be seen as a complete general-purpose timer. Their four independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes)
- One-cycle mode output

If configured as a standard 16-bit timer, it has the same features as the TMRx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0-100%).

In debug mode, the advanced timer counter can be frozen and the PWM outputs disabled to turn off any power switch driven by these outputs.

Many features are shared with those of the general-purpose TMR which have the same architecture. The advanced timer can therefore work together with the general-purpose timers via the timer link feature for synchronization or event chaining.

2.10.2 General-purpose timers (TMRx)

There are 10 synchronizable general-purpose timers embedded in the AT32A403A series.

- **TMR2, TMR3, TMR4, and TMR5**

The AT32A403A series has 4 general-purpose timers: TMR2, TMR3, TMR4, and TMR5. The TMR2 and TMR5 timers are based on a 32-bit auto-reload up/down counter and a 16-bit prescaler. The TMR3 and TMR4 timers are based on a 16-bit auto-reload up/down counter and a 16-bit prescaler. They can offer four independent channels on the largest package. Each channel can be used for input capture/output compare, PWM or one-cycle mode output.

These general-purpose timers can work together with advanced timers via the timer link feature for synchronization or event chaining. In debug mode, their counters can be frozen.

Any of these general-purpose timers can be used to generate PWM outputs. Each timer has its individual DMA request mechanism.

These timers are capable of handling incremental quadrature encoder signals and the digital outputs coming from 1 to 3 hall-effect sensors.

- **TMR9 and TMR12**

TMR9 and TMR12 are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. They all feature two independent channels for input capture/output compare, PWM, or one-cycle mode output. The TMR9 and TMR12 can be synchronized with the TMR2, TMR3, TMR4, and TMR5 full-featured general-purpose timers. They can also be used as simple time bases.

- **TMR10, TMR11, TMR13, and TMR14**

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. They all feature one independent channel for input capture/output compare, PWM, or one-cycle mode output. These timers can be synchronized with the TMR2, TMR3, TMR4, and TMR5 full-featured general-purpose timers. They can also be used as simple time bases.

2.10.3 Basic timers (TMR6 and TMR7)

These two timers are mainly used for DAC trigger generation. Each of them can also be used as a generic 16-bit time base.

2.10.4 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features include:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source (HCLK or HCLK/8)

2.11 Watchdog (WDT)

The watchdog consists of a 12-bit downcounter and 8-bit prescaler. It is clocked by an independent internal LICK clock. As it operates independently from the main clock, it can operate in DeepSleep and Standby modes. It can be used either as a watchdog to reset the device when an error occurs, or as a free running timer for application timeout management. It is self-enabled through the User System Data configuration. The counter can be frozen in debug mode.

2.12 Window watchdog (WWDT)

The window watchdog embeds a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

2.13 Real-time clock (RTC) and battery powered register (BPR)

The RTC and the battery powered registers (BPR) are supplied with a power switch that is powered either from V_{DD} when present or from the V_{BAT} pin. The battery powered registers are forty-two 16-bit registers used to store 84 bytes of user application data. The RTC and BPR are not reset by a system or power reset, and they are not reset when the device wakes up from Standby mode.

The real-time clock provides a continuous-running counter. The RTC provides clock calendar, and alarm interrupt and periodic interrupt functions. It is clocked by a 32.768 kHz external crystal (LEXT), the internal low-power clock (LICK), or the high-speed external clock (HEXT) divided by 128. The RTC can be calibrated using a divided-by-64 output of TAMPER pin to compensate for any natural quartz deviation. The RTC features a 32-bit programmable counter that allows long time measurement with the help of the Compare register. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

2.14 Communication interfaces

2.14.1 Serial peripheral interface (SPI)

There are up to four SPI interfaces in slave and master modes in full-duplex and simplex communication modes. They can communicate at up to 50 Mbits/s. The 3-bit prescaler generates eight master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC/SDHC modes. All SPIs can be served by the DMA controller.

2.14.2 Inter-integrated sound interface (I²S)

Four standard I²S interfaces (multiplexed with SPI) can be operated in master or slave mode in half-duplex mode, and I2S2 and I2S3 can be operated in full duplex mode. These interfaces can be configured to operate with 16/24/32 bit resolution, as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When I²S configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency. All I²Ss can be served by the DMA controller.

2.14.3 Universal synchronous / asynchronous receiver transmitter (USART)

The AT32A403A series embeds four universal synchronous/asynchronous receiver transmitters (USART1, USART2, USART3, and USART6) and 4 universal asynchronous receiver transmitters (UART4, UART5, UART7, and UART8).

These eight interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode, and have LIN Master/Slave capability.

These eight interfaces are able to communicate at speeds of up to 6.25 Mbit/s.

USART1, USART2, and USART3 provide hardware management of the CTS and RTS signals.

USART1, USART2, USART3, and USART6 provide Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.

Table 5. USART / UART feature comparison

USART/UART name	USART1	USART2	USART3	UART4	UART5	USART6	UART7	UART8
Hardware flow control for modem	Yes	Yes	Yes	-	-	-	-	-
Continuous communication using DMA	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
Multiprocessor communication	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
Synchronous mode	Yes	Yes	Yes	-	-	Yes	-	-
Smartcard mode	Yes	Yes	Yes	-	-	Yes	-	-
Single-wire half-duplex communication	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
IrDA SIR ENDEC block	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
LIN mode	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes

2.14.4 Inter-integrated-circuit interface (I²C)

Up to three I²C bus interfaces can operate in multi-master and slave modes. They support standard mode (max. 100 kHz) and fast mode (max. 400 kHz). The I²C bus frequency can be increased up to 1 MHz. For more details, please contact your local Artery sales office for technical support.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is included.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.14.5 Secure digital input / output interface (SDIO)

Two SD/SDIO/MMC host interfaces are available that support MultiMediaCard System Specification Version 4.2 in three different data bus modes: 1-bit (default), 4-bit and 8-bit. The interface allows data transfer at up to 48 MHz in 8-bit mode, and is compliant with SD Memory Card Specifications Version 2.0.

Two different data bus modes supported in the SDIO Card Specification Version 2.0 are: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC/eMMC, this interface is also fully compliant with the CE-ATA digital protocol Rev1.1.

2.14.6 Controller area network (CAN)

Two CANs are compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive buffers with 3 stages, and 14 scalable filter banks.

2.14.7 Universal serial bus full-speed (USBFS)

The AT32A403A series embeds a USB device peripheral compatible with the USB full-speed 12 Mbit/s. It has software-configurable endpoint setting and suspend/resume support. The dedicated 48 MHz clock is generated from the internal main PLL or directly from the 48 MHz HICK clock source.

2.14.8 Ethernet MAC interface (EMAC)

The AT32A403A device provide an IEEE-802.3-2002-compliant media access controller (MAC) for Ethernet LAN communications through an industry-standard media-independent interface (MII) or a reduced media-independent interface (RMII). The AT32A403A requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). The PHY is connected to the AT32A403A MAC port using as many as 17 signals (MII) or 9 signals (RMII) and can be clocked by means of the 25 MHz (MII) or 50 MHz (RMII) output from the AT32A403A.

The EMAC has the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller for high-speed transfer between the dedicated SRAM and the descriptors
- Supports tagged MAC frame (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- Supports MAC control sublayer (control frames)
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmitted and received frames. The transmit FIFO and the receive FIFO are both 2 KBytes, that is, 4 KBytes in total
- Supports hardware PTP (precision time protocol) in line with IEEE 1588 with the timestamp comparator connected to the TMR2 trigger input
- Interrupt trigger when system time becomes greater than the target time

2.15 Cyclic redundancy check (CRC) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial. Among other applications, CRC-based techniques are used to verify data transmission or storage integrity.

2.16 Analog-to-digital converter (ADC)

Three 12-bit analog-to-digital converters are embedded into AT32A403A device and they share up to 16 external channels, performing conversions in single-shot or sequential modes. In sequence mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sampling and hold
- Interleaved sampling and hold
- Single sampling

These ADCs can be served by the DMA controller.

The voltage monitoring feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TMRx) and the advanced timers (TMR1 and TMR8) can be internally connected to the ADC regular trigger and injection trigger, respectively, to allow the application to synchronize A/D conversion and timers.

2.16.1 Temperature sensor (V_{TS})

The temperature sensor has to generate a voltage V_{TS} that varies linearly with temperature. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The offset of this line varies from chip to chip due to process variation. The internal temperature sensor is more suited to applications that detect temperature variations instead of absolute temperatures. If accurate temperature readings are needed, an external temperature sensor part should be used.

2.16.2 Internal reference voltage (V_{INTRV})

The internal reference voltage (V_{INTRV}) provides a stable voltage source for ADC. The V_{INTRV} is internally connected to the ADC1_IN17 input channel.

2.17 Digital-to-analog converter (DAC)

The two 12-bit buffered DACs can be used to convert two-channel digital signals into two-channel analog voltage signal outputs.

The DAC has the following features:

- Two DAC converters with an output channel each
- 8-bit or 12-bit monotonic output
- Left- or right-alignment data in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability for each DAC
- External triggers for conversion
- Input voltage reference V_{REF+}

Several DAC trigger inputs are available in the AT32A403A series. DAC outputs can be triggered through the timer update outputs. The update output can also be connected to different DMA channels.

2.18 Debug

2.18.1 Serial wire (SWD) / JTAG port

The ARM® SWJ-DP Interface is embedded, consisting of a serial wire debug port and JTAG. It enables either a serial wire debug or a JTAG probe to be connected to the target for programming and debug operation. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK.

2.18.2 Embedded Trace Macrocell (ETM™)

The ARM® Embedded Trace Macrocell (ETM™) provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the AT32A403A through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. The TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

3 Pin functional definitions

Figure 2. AT32A403A LQFP100 pinout

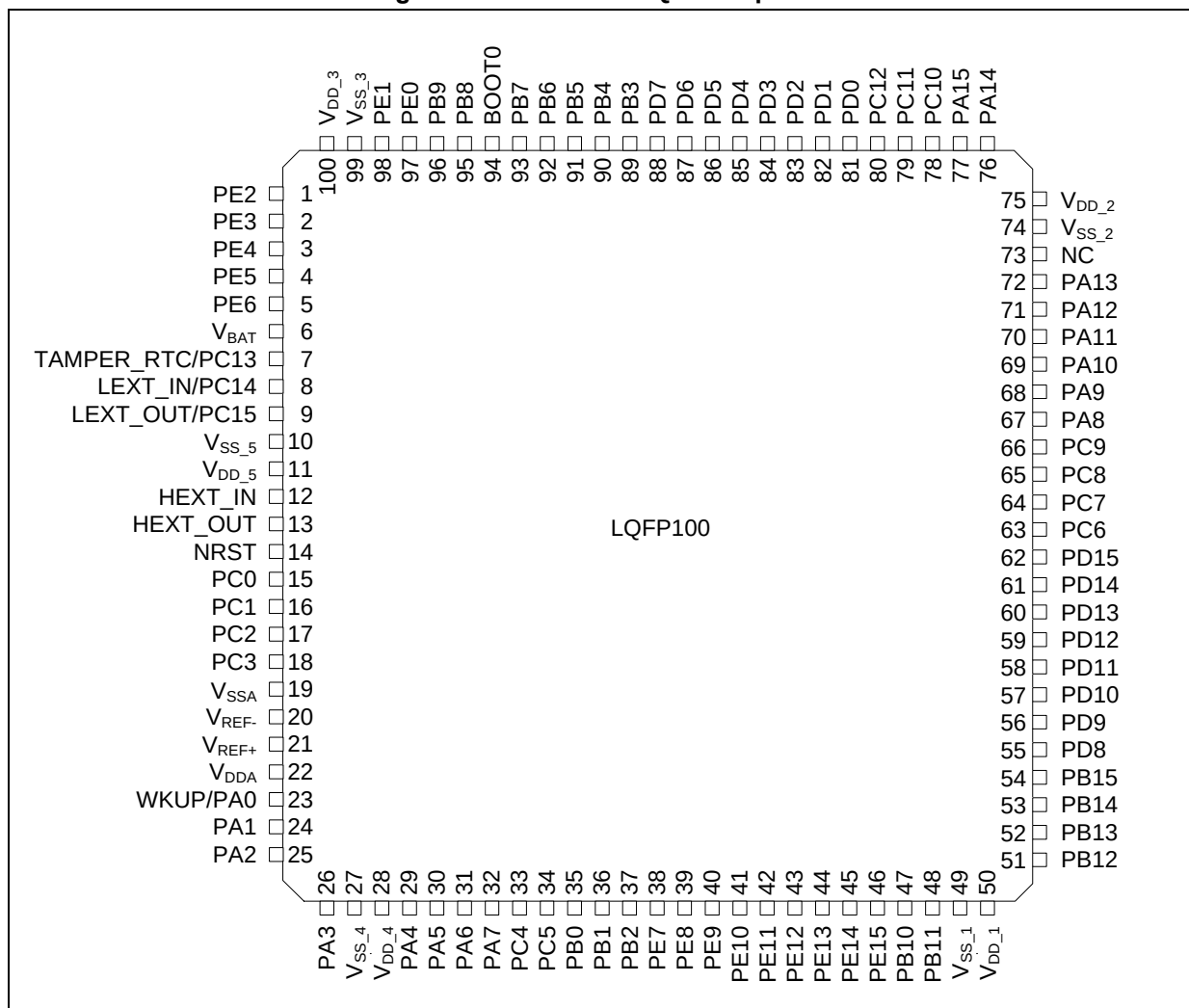


Figure 3. AT32A403A LQFP64 pinout

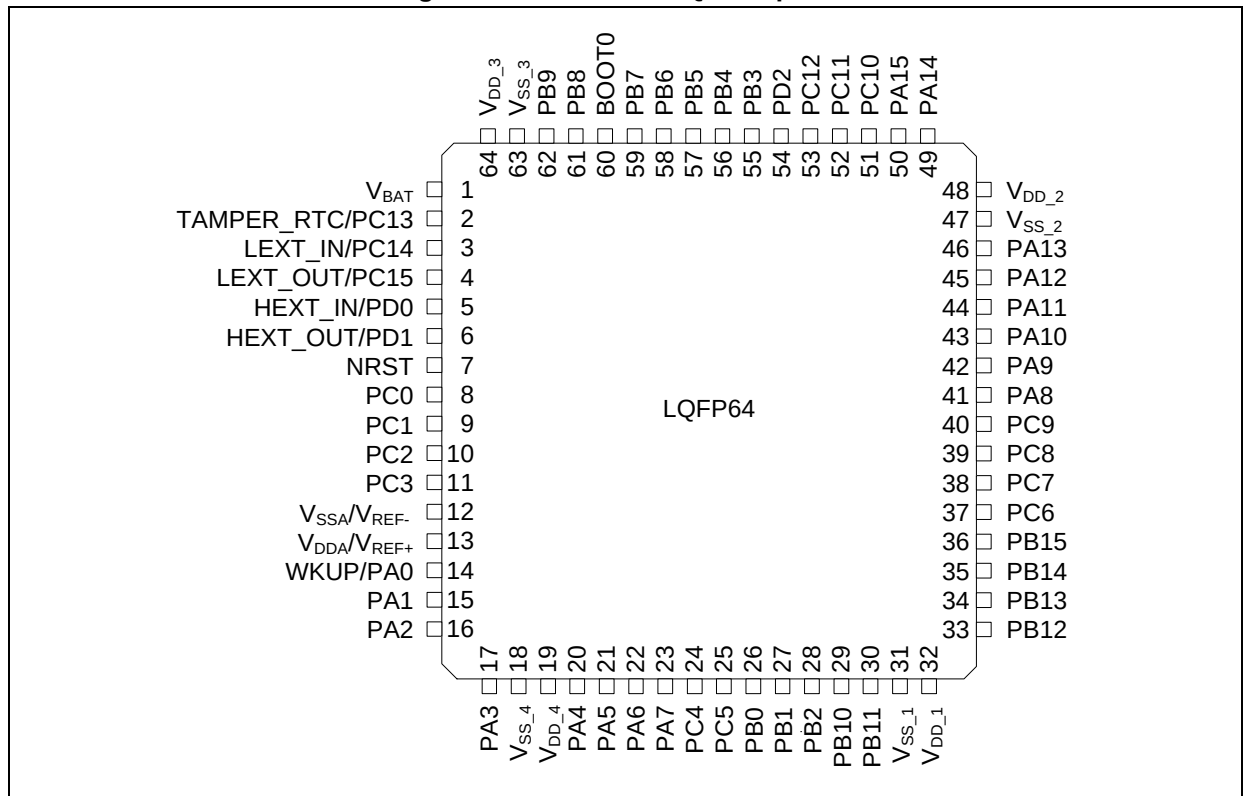


Figure 4. AT32A403A LQFP48 pinout

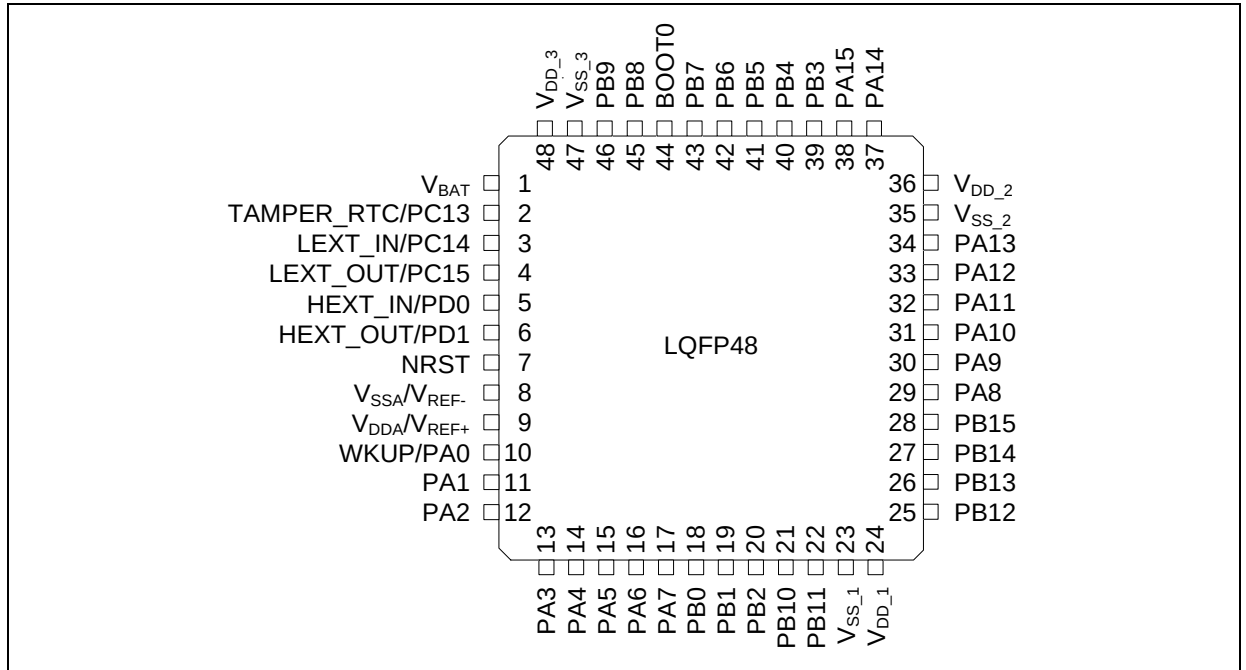
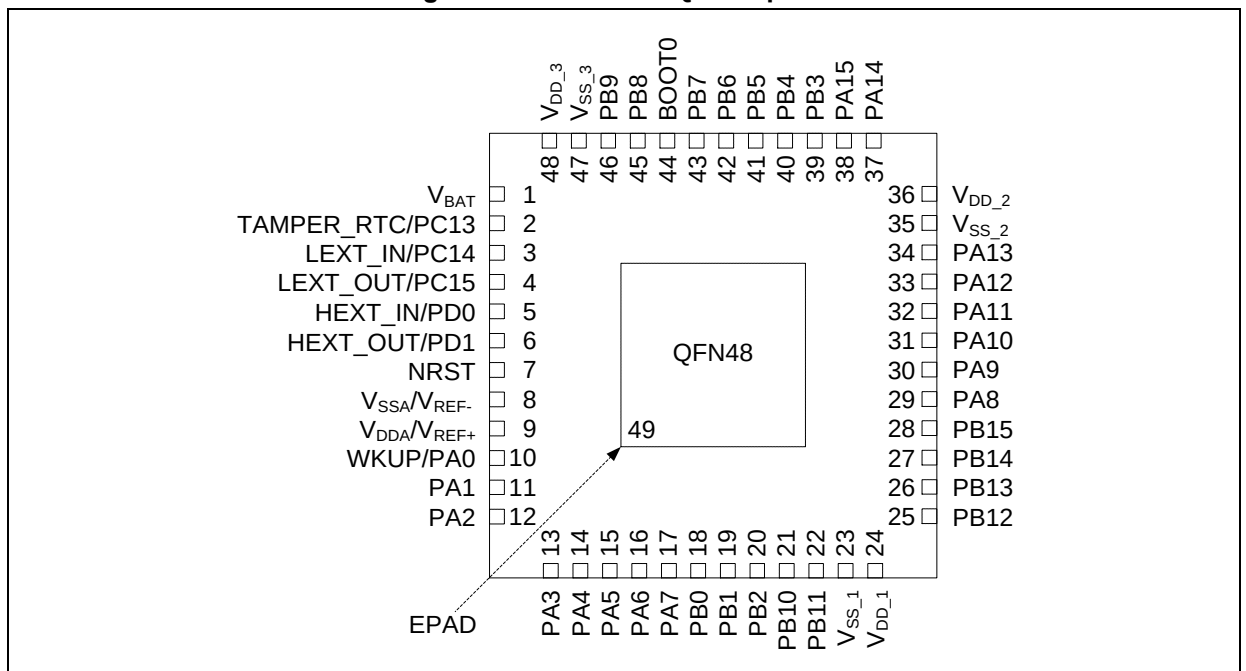


Figure 5. AT32A403A QFN48 pinout



The table below presents the pin definitions of the AT32A403A series. "-" means there is no such pinout on the related package. The "multiplexed functions" here below follows the priority order from high to low. Typically the analog signals have priority over digital signals, and the digital output signals get priority over digital input signals.

Table 6. AT32A403A series pin definitions

Pin number				Pin name	Type ⁽¹⁾	IO level ⁽²⁾	Main function ⁽³⁾	Multiflexed functions ⁽⁴⁾	
LQFP48	QFN48	LQFP64	LQFP100					Default	Remap
-	-	-	1	PE2	I/O	FT	PE2	SPI4_SCK ⁽⁷⁾ / I2S4_CK ⁽⁷⁾ / XMC_A23 / TRACECK	-
-	-	-	2	PE3	I/O	FT	PE3	XMC_A19 / TRACED0	-
-	-	-	3	PE4	I/O	FT	PE4	SPI4_CS ⁽⁷⁾ / I2S4_WS ⁽⁷⁾ / XMC_A20 / TRACED1	-
-	-	-	4	PE5	I/O	FT	PE5	SPI4_MISO ⁽⁷⁾ / XMC_A21 / TRACED2	TMR9_CH1
-	-	-	5	PE6	I/O	FT	PE6	SPI4_MOSI ⁽⁷⁾ / I2S4_SD ⁽⁷⁾ / XMC_A22 / TRACED3	TMR9_CH2
1	1	-	6	V _{BAT}	S	-	V _{BAT}	-	-
2	2	-	7	TAMPER-RTC / PC13 ⁽⁵⁾	I/O	TC	PC13 ⁽⁶⁾	TAMPER-RTC	-
3	3	-	8	LEXT_IN / PC14 ⁽⁵⁾	I/O	TC	PC14 ⁽⁶⁾	LEXT_IN	-
4	4	-	9	LEXT_OUT / PC15 ⁽⁵⁾	I/O	TC	PC15 ⁽⁶⁾	LEXT_OUT	-
-	-	-	10	V _{SS_5}	S	-	V _{SS_5}	-	-
-	-	-	11	V _{DD_5}	S	-	V _{DD_5}	-	-
-	-	-	12	HEXT_IN	I	-	HEXT_IN	-	-
-	-	-	13	HEXT_OUT	O	-	HEXT_OUT	-	-
5	5	-	-	HEXT_IN / PD0 ⁽⁸⁾	I/O	TC	HEXT_IN	-	PD0 ⁽⁸⁾
6	6	-	-	HEXT_OUT / PD1 ⁽⁸⁾	I/O	TC	HEXT_OUT	-	PD1 ⁽⁸⁾
7	7	-	14	NRST	I/O	-	NRST	-	-
-	8	-	15	PC0	I/O	FTa	PC0	ADC123_IN10 / SDIO2_D0 ⁽⁷⁾	-
-	9	-	16	PC1	I/O	FTa	PC1	ADC123_IN11 / SDIO2_D1 ⁽⁷⁾ / EMAC_MDC	-
-	10	-	17	PC2	I/O	FTa	PC2	ADC123_IN12 / SDIO2_D2 ⁽⁷⁾ / EMAC_MII_TXD2	UART8_TX / XMC_NWE
-	11	-	18	PC3	I/O	FTa	PC3	ADC123_IN13 / SDIO2_D3 ⁽⁷⁾ / XMC_A0 / EMAC_MII_TX_CLK	UART8_RX
-	-	-	19	V _{SSA}	S	-	V _{SSA}	-	-
-	-	-	20	V _{REF-}	S	-	V _{REF-}	-	-
8	12	-	-	V _{SSA} / V _{REF-}	S	-	V _{SSA} / V _{REF-}	-	-
-	-	-	21	V _{REF+}	S	-	V _{REF+}	-	-
-	-	-	22	V _{DDA}	S	-	V _{DDA}	-	-
9	13	-	-	V _{DDA} / V _{REF+}	S	-	V _{DDA} / V _{REF+}	-	-

Pin number				Pin name	Type ⁽¹⁾	IO level ⁽²⁾	Main function ⁽³⁾	Multiflexed functions ⁽⁴⁾	
LQFP48	QFN48	LQFP64	LQFP100					Default	Remap
10	14	23		PA0 / WKUP	I/O	TC	PA0	ADC123_IN0 / WKUP / USART2_CTS ⁽⁷⁾ / EMAC_MII_CRS_WKUP / TMR2_CH1 ⁽⁷⁾ / TMR2_EXT ⁽⁷⁾ / TMR5_CH1 / TMR8_EXT	UART4_TX
11	15	24		PA1	I/O	FTa	PA1	ADC123_IN1 / USART2_RTS ⁽⁷⁾ / EMAC_MII_RX_CLK / EMAC_RMII_REF_CLK / TMR2_CH2 ⁽⁷⁾ / TMR5_CH2	UART4_RX
12	16	25		PA2	I/O	FTa	PA2	ADC123_IN2 / USART2_TX ⁽⁷⁾ / EMAC_MDIO / TMR2_CH3 ⁽⁷⁾ / TMR5_CH3 / TMR9_CH1 ⁽⁷⁾	SDIO2_CK / XMC_D4
13	17	26		PA3	I/O	FTa	PA3	ADC123_IN3 / USART2_RX ⁽⁷⁾ / EMAC_MII_COL / TMR2_CH4 ⁽⁷⁾ / TMR5_CH4 / TMR9_CH2 ⁽⁷⁾	I2S2_MCK / SDIO2_CMD / XMC_D5
-	18	27		V _{SS_4}	S	-	V _{SS_4}	-	-
-	19	28		V _{DD_4}	S	-	V _{DD_4}	-	-
14	20	29		PA4	I/O	FTa	PA4	DAC1_OUT / ADC12_IN4 / USART2_CK ⁽⁷⁾ / SPI1_CS ⁽⁷⁾ / I2S1_WS ⁽⁷⁾ / SDIO2_D4	USART6_TX / SPI3_CS / I2S3_WS / SDIO2_D0 / XMC_D6
15	21	30		PA5	I/O	FTa	PA5	DAC2_OUT / ADC12_IN5 / SPI1_SCK ⁽⁷⁾ / I2S1_CK ⁽⁷⁾ / SDIO2_D5	USART6_RX / SDIO2_D1 / XMC_D7
16	22	31		PA6	I/O	FTa	PA6	ADC12_IN6 / SPI1_MISO ⁽⁷⁾ / SDIO2_D6 / TMR3_CH1 ⁽⁷⁾ / TMR8_BRK / TMR13_CH1	I2S2_MCK / SDIO2_D2 / TMR1_BRK
17	23	32		PA7	I/O	FTa	PA7	ADC12_IN7 / SPI1_MOSI ⁽⁷⁾ / I2S1_SD ⁽⁷⁾ / SDIO2_D7 / EMAC_MII_RX_DV ⁽⁷⁾ / EMAC_RMII_CRS_DV ⁽⁷⁾ / TMR3_CH2 ⁽⁷⁾ / TMR8_CH1C / TMR14_CH1	SDIO2_D3 / TMR1_CH1C
-	24	33		PC4	I/O	FTa	PC4	ADC12_IN14 / SDIO2_CK ⁽⁷⁾ / XMC_NE4 / EMAC_MII_RXD0 ⁽⁷⁾ / EMAC_RMII_RXD0 ⁽⁷⁾	-
-	25	34		PC5	I/O	FTa	PC5	ADC12_IN15 / SDIO2_CMD ⁽⁷⁾ / EMAC_MII_RXD1 ⁽⁷⁾ / EMAC_RMII_RXD1 ⁽⁷⁾	XMC_NOE
18	26	35		PB0	I/O	FTa	PB0	ADC12_IN8 / I2S1_MCK ⁽⁷⁾ / EMAC_MII_RXD2 ⁽⁷⁾ / TMR3_CH3 ⁽⁷⁾ / TMR8_CH2C	TMR1_CH2C
19	27	36		PB1	I/O	FTa	PB1	ADC12_IN9 / SPIM_SCK / EMAC_MII_RXD3 ⁽⁷⁾ / TMR3_CH4 ⁽⁷⁾ / TMR8_CH3C	TMR1_CH3C
20	28	37		PB2	I/O	FT	PB2 / BOOT1 ⁽¹⁰⁾	-	-
-	-	38		PE7	I/O	FT	PE7	UART7_RX ⁽⁷⁾ / XMC_D4 ⁽⁷⁾	TMR1_EXT
-	-	39		PE8	I/O	FT	PE8	UART7_TX ⁽⁷⁾ / XMC_D5 ⁽⁷⁾	TMR1_CH1C
-	-	40		PE9	I/O	FT	PE9	XMC_D6 ⁽⁷⁾	TMR1_CH1
-	-	41		PE10	I/O	FT	PE10	XMC_D7 ⁽⁷⁾	TMR1_CH2C

Pin number			Pin name	Type ⁽¹⁾	IO level ⁽²⁾	Main function ⁽³⁾	Multiflexed functions ⁽⁴⁾	
LQFP48	QFN48	LQFP64					Default	Remap
-	-	42	PE11	I/O	FT	PE11	XMC_D8	SPI4_SCK / I2S4_CK / TMR1_CH2
-	-	43	PE12	I/O	FT	PE12	XMC_D9	SPI4_CS / I2S4_WS / TMR1_CH3C
-	-	44	PE13	I/O	FT	PE13	XMC_D10	SPI4_MISO / TMR1_CH3
-	-	45	PE14	I/O	FT	PE14	XMC_D11	SPI4_MOSI / I2S4_SD / TMR1_CH4
-	-	46	PE15	I/O	FT	PE15	XMC_D12	TMR1_BRK
21	29	47	PB10	I/O	FT	PB10	USART3_TX ⁽⁷⁾ / I2C2_SCL ⁽⁹⁾ / EMAC_MII_RX_ER	I2S3_MCK / SPIM_IO0 / TMR2_CH3
22	30	48	PB11	I/O	FT	PB11	USART3_RX ⁽⁷⁾ / I2C2_SDA ⁽⁹⁾ / EMAC_MII_TX_EN / EMAC_RMII_TX_EN	SPIM_IO1 / TMR2_CH4
23	31	49	V _{SS_1}	S	-	V _{SS_1}	-	-
24	32	50	V _{DD_1}	S	-	V _{DD_1}	-	-
25	33	51	PB12	I/O	FT	PB12	USART3_CK ⁽⁷⁾ / CAN2_RX ⁽⁷⁾ / I2C2_SMBA ⁽⁹⁾ / SPI2_CS ⁽⁹⁾ / I2S2_WS ⁽⁹⁾ / EMAC_MII_TXD0 / EMAC_RMII_TXD0 / TMR1_BRK ⁽⁷⁾	XMC_D13
26	34	52	PB13	I/O	FT	PB13	USART3_CTS ⁽⁷⁾ / CAN2_TX ⁽⁷⁾ / SPI2_SCK ⁽⁹⁾ / I2S2_CK ⁽⁹⁾ / EMAC_MII_TXD1 / EMAC_RMII_TXD1 / TMR1_CH1C ⁽⁷⁾	-
27	35	53	PB14	I/O	FT	PB14	USART3_RTS ⁽⁷⁾ / SPI2_MISO ⁽⁹⁾ / I2S2_SDEXT ⁽⁹⁾ / TMR1_CH2C ⁽⁷⁾ / TMR12_CH1	XMC_D0
28	36	54	PB15	I/O	FT	PB15	SPI2_MOSI ⁽⁹⁾ / I2S2_SD ⁽⁹⁾ / TMR1_CH3C ⁽⁷⁾ / TMR12_CH2	-
-	-	55	PD8	I/O	FT	PD8	XMC_D13 ⁽⁷⁾	USART3_TX / EMAC_MII_RX_DV / EMAC_RMII_CRS_DV
-	-	56	PD9	I/O	FT	PD9	XMC_D14	USART3_RX / EMAC_MII_RXD0 / EMAC_RMII_RXD0
-	-	57	PD10	I/O	FT	PD10	XMC_D15	USART3_CK / EMAC_MII_RXD1 / EMAC_RMII_RXD1
-	-	58	PD11	I/O	FT	PD11	XMC_A16	USART3_CTS / EMAC_MII_RXD2
-	-	59	PD12	I/O	FT	PD12	XMC_A17	USART3_RTS / EMAC_MII_RXD3 / TMR4_CH1
-	-	60	PD13	I/O	FT	PD13	XMC_A18	TMR4_CH2
-	-	61	PD14	I/O	FT	PD14	XMC_D0 ⁽⁷⁾	TMR4_CH3
-	-	62	PD15	I/O	FT	PD15	XMC_D1 ⁽⁷⁾	TMR4_CH4
-	37	63	PC6	I/O	FT	PC6	USART6_TX ⁽⁷⁾ / I2S2_MCK ⁽⁷⁾ / SDIO1_D6 / TMR8_CH1	XMC_D1 / TMR3_CH1

Pin number			Pin name	Type ⁽¹⁾	IO level ⁽²⁾	Main function ⁽³⁾	Multiflexed functions ⁽⁴⁾	
LQFP48	QFN48	LQFP64					Default	Remap
-	38	64	PC7	I/O	FT	PC7	USART6_RX ⁽⁷⁾ / I2S3_MCK ⁽⁷⁾ / SDIO1_D7 / TMR8_CH2	TMR3_CH2
-	39	65	PC8	I/O	FT	PC8	USART6_CK / I2S4_MCK ⁽⁷⁾ / SDIO1_D0 / TMR8_CH3	TMR3_CH3
-	40	66	PC9	I/O	FT	PC9	I2C3_SDA ⁽⁷⁾ / SDIO1_D1 / TMR8_CH4	TMR3_CH4
29	41	67	PA8	I/O	FT	PA8	CLKOUT / USART1_CK / I2C3_SCL / USBFS_SOF / SPIM_CS / TMR1_CH1 ⁽⁷⁾	-
30	42	68	PA9	I/O	FT	PA9	USART1_TX ⁽⁷⁾ / I2C3_SMBA / TMR1_CH2 ⁽⁷⁾	-
31	43	69	PA10	I/O	FT	PA10	USART1_RX ⁽⁷⁾ / TMR1_CH3 ⁽⁷⁾	I2S4_MCK
32	44	70	PA11	I/O	TC	PA11	USBFS1_D- / USART1_CTS / CAN1_RX ⁽⁷⁾ / SPIM_IO0 ⁽⁷⁾ / TMR1_CH4 ⁽⁷⁾	-
33	45	71	PA12	I/O	TC	PA12	USBFS1_D+ / USART1_RTS / CAN1_TX ⁽⁷⁾ / SPIM_IO1 ⁽⁷⁾ / TMR1_EXT ⁽⁷⁾	-
34	46	72	PA13	I/O	FT	JTMS-SWDIO	-	PA13
-	-	73	Disconnected					
35	47	74	V _{SS_2}	S	-	V _{SS_2}	-	-
36	48	75	V _{DD_2}	S	-	V _{DD_2}	-	-
37	49	76	PA14	I/O	FT	JTCK-SWCLK	-	PA14
38	50	77	PA15	I/O	FT	JTDI	SPI3_CS ⁽⁷⁾ / I2S3_WS ⁽⁷⁾	PA15 / SPI1_CS / I2S1_WS / TMR2_CH1 / TMR2_EXT
-	51	78	PC10	I/O	FT	PC10	UART4_TX ⁽⁷⁾ / SDIO1_D2	USART3_TX / SPI3_SCK / I2S3_CK
-	52	79	PC11	I/O	FT	PC11	UART4_RX ⁽⁷⁾ / SDIO1_D3	USART3_RX / SPI3_MISO / I2S3_SDEXT / XMC_D2
-	53	80	PC12	I/O	FT	PC12	UART5_TX ⁽⁷⁾ / SDIO1_CK	USART3_CK / SPI3_MOSI / I2S3_SD / XMC_D3
-	-	81	PD0	I/O	FT	PD0	XMC_D2 ⁽⁷⁾	CAN1_RX
-	-	82	PD1	I/O	FT	PD1	XMC_D3 ⁽⁷⁾	CAN1_TX
-	54	83	PD2	I/O	FT	PD2	UART5_RX ⁽⁷⁾ / SDIO1_CMD / TMR3_EXT	XMC_NWE
-	-	84	PD3	I/O	FT	PD3	XMC_CLK	USART2_CTS
-	-	85	PD4	I/O	FT	PD4	XMC_NOE ⁽⁷⁾	USART2_RTS
-	-	86	PD5	I/O	FT	PD5	XMC_NWE ⁽⁷⁾	USART2_TX
-	-	87	PD6	I/O	FT	PD6	XMC_NWAIT	USART2_RX
-	-	88	PD7	I/O	FT	PD7	XMC_NE1 / XMC_NCE2	USART2_CK

Pin number			Pin name	Type ⁽¹⁾	IO level ⁽²⁾	Main function ⁽³⁾	Multiflexed functions ⁽⁴⁾	
LQFP48	QFN48	LQFP64					Default	Remap
39	55	89	PB3	I/O	FT	JTDO	SPI3_SCK ⁽⁷⁾ / I2S3_CK ⁽⁷⁾	PB3 / UART7_RX / SPI1_SCK / I2S1_CK / SWO / TMR2_CH2
40	56	90	PB4	I/O	FT	NJTRST	SPI3_MISO ⁽⁷⁾ / I2S3_SDEXT ⁽⁷⁾	PB4 / SPI1_MISO / I2C3_SDA / UART7_TX / TMR3_CH1
41	57	91	PB5	I/O	FT	PB5	SPI3_MOSI ⁽⁷⁾ / I2S3_SD ⁽⁷⁾ / I2C1_SMBA ⁽⁷⁾ / EMAC_PPS_OUT	SPI1_MOSI / I2S1_SD / CAN2_RX / TMR3_CH2
42	58	92	PB6	I/O	FT	PB6	I2C1_SCL ⁽⁷⁾ / SPIM_IO3 / TMR4_CH1 ⁽⁷⁾	USART1_TX / I2S1_MCK / SPI4_CS / I2S4_WS / CAN2_TX
43	59	93	PB7	I/O	FT	PB7	I2C1_SDA ⁽⁷⁾ / XMC_NADV / SPIM_IO2 / TMR4_CH2 ⁽⁷⁾	USART1_RX / SPI4_SCK / I2S4_CK
44	60	94	BOOT0	I	-	BOOT0	-	-
45	61	95	PB8	I/O	FT	PB8	SDIO1_D4 / EMAC_MII_TXD3 / TMR4_CH3 ⁽⁷⁾ / TMR10_CH1	UART5_RX / SPI4_MISO / I2C1_SCL / CAN1_RX
46	62	96	PB9	I/O	FT	PB9	SDIO1_D5 / TMR4_CH4 ⁽⁷⁾ / TMR11_CH1	UART5_TX / SPI4_MOSI / I2S4_SD / I2C1_SDA / CAN1_TX
-	-	97	PE0	I/O	FT	PE0	UART8_RX ⁽⁷⁾ / XMC_LB / TMR4_EXT	-
-	-	98	PE1	I/O	FT	PE1	UART8_TX ⁽⁷⁾ / XMC_UB	-
47	63	99	V _{SS_3}	S	-	V _{SS_3}	-	-
48	64	100	V _{DD_3}	S	-	V _{DD_3}	-	-
-/49	-	-	EPAD	S	-	V _{SS}	-	-

(1) I = input, O = output, S = supply.

(2) TC = standard 3.3 V GPIO, FT = general 5 V-tolerant GPIO, FTa = 5 V-tolerant GPIO with analog functionalities. FTa pin is 5 V-tolerant when configured as input floating, input pull-up, or input pull-down mode. However, it cannot be 5 V-tolerant when configured as analog mode. Meanwhile, its input level should not higher than $V_{DD} + 0.3 V$.

(3) Function availability depends on the chosen device.

(4) If several peripherals share the same GPIO pin, to avoid conflict between these multiple functions only one peripheral should be enabled at a time through the peripheral clock enable bit (in the corresponding RCC peripheral clock enable register).

(5) PC13, PC14, and PC15 are supplied through the power switch. Since the switch only drives a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited not to be used as a current source (e.g. to drive an LED).

(6) Main function after the first battery powered domain power-up. Later on, it depends on the contents of the battery powered registers even after reset (because these registers are not reset by the main reset). For details on how to manage these GPIOs, refer to the battery powered domain and register description sections in the AT32A403A reference manual.

(7) This multiplexed functions can be remapped by software to some other port pins (if available on the used package). For more details, refer to the multiplexed function GPIOs and debug configuration section in the AT32A403A reference manual.

(8) For the LQFP64, LQFP48, and QFN48 packages, the pin 5 and pin 6 are configured as HEXT_IN and HEXT_OUT after reset. The functionality of PD0 and PD1 can be remapped by software on these pins. However, for the LQFP100 package, PD0 and PD1 are available by default, so there is no need for remapping. For more details, refer to multiplexed function

GPIOs and debug configuration section in the AT32A403A reference manual.

- (9) SPI2, I²S2 and I²C2 must be disabled while using Ethernet.
- (10) If the device boots from Flash and leaves PB2 not used, it is advisable to pull PB2 pin down to ground.

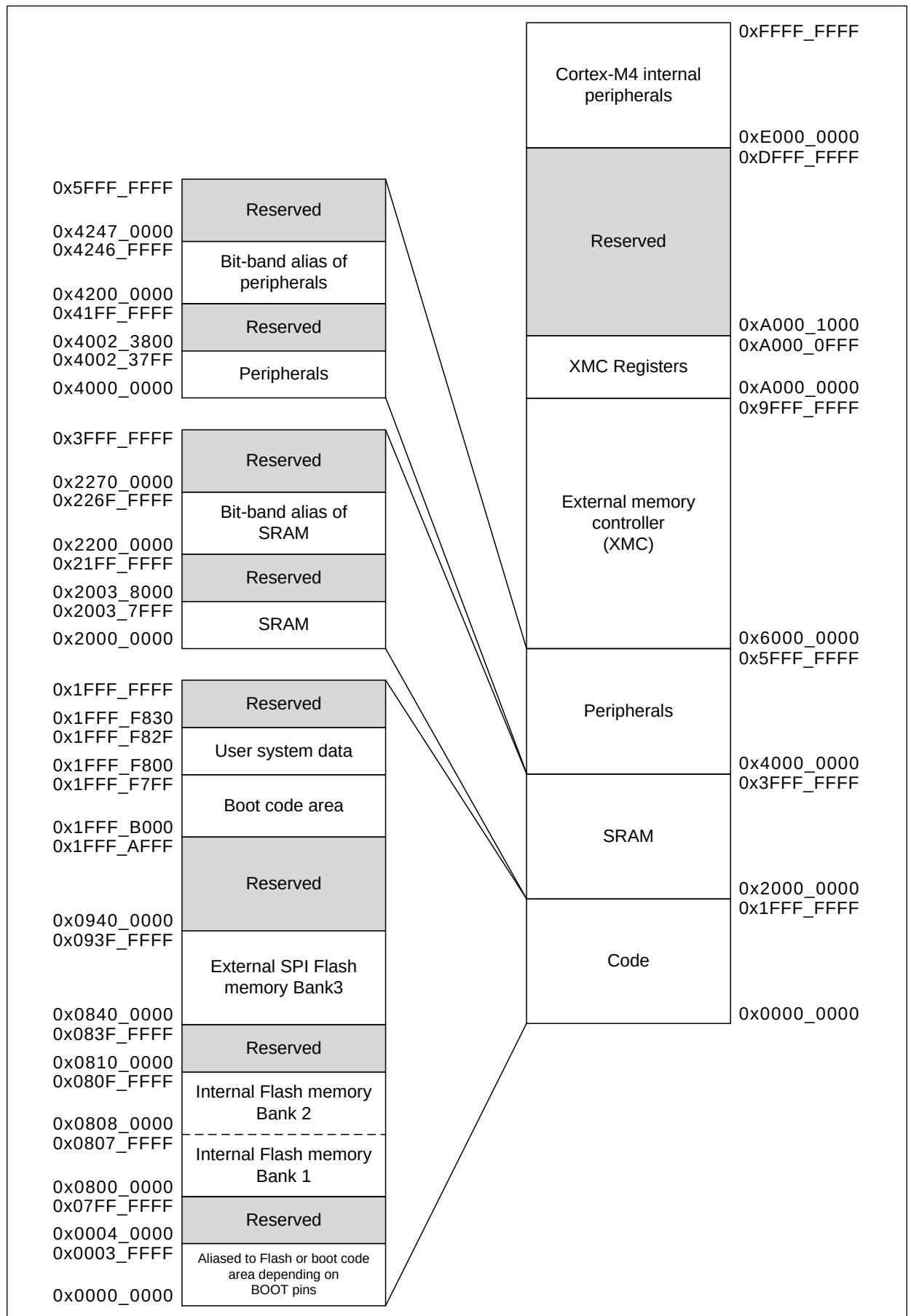
Table 7. XMC pin definitions

Pins	XMC			LQFP64
	Multiplexed PSRAM/NOR	LCD	NAND	
PE2	A23	A23	-	-
PE3	A19	A19	-	-
PE4	A20	A20	-	-
PE5	A21	A21	-	-
PE6	A22	A22	-	-
PC2	NWE	NWE	NWE	有
PC3	-	A0	-	有
PA2	AD4	D4	D4	有
PA3	AD5	D5	D5	有
PA4	AD6	D6	D6	有
PA5	AD7	D7	D7	有
PC4	NE4	NE4	-	有
PC5	NOE	NOE	NOE	有
PE7	AD4	D4	D4	-
PE8	AD5	D5	D5	-
PE9	AD6	D6	D6	-
PE10	AD7	D7	D7	-
PE11	AD8	D8	D8	-
PE12	AD9	D9	D9	-
PE13	AD10	D10	D10	-
PE14	AD11	D11	D11	-
PE15	AD12	D12	D12	-
PB12	AD13	D13	D13	有
PB14	AD0	D0	D0	有
PD8	AD13	D13	D13	-
PD9	AD14	D14	D14	-
PD10	AD15	D15	D15	-
PD11	A16	A16	CLE	-
PD12	A17	A17	ALE	-
PD13	A18	A18	-	-
PD14	AD0	D0	D0	-
PD15	AD1	D1	D1	-
PC6	AD1	D1	D1	有
PC11	AD2	D2	D2	有
PC12	AD3	D3	D3	有
PD0	AD2	D2	D2	-
PD1	AD3	D3	D3	-

Pins	XMC			LQFP64
	Multiplexed PSRAM/NOR	LCD	NAND	
PD2	NWE	NWE	NWE	有
PD3	CLK	-	-	-
PD4	NOE	NOE	NOE	-
PD5	NWE	NWE	NWE	-
PD6	NWAIT	-	NWAIT	-
PD7	NE1	NE1	NCE2	-
PB7	NADV	-	-	有
PE0	LB	-	-	-
PE1	UB	-	-	-

4 Memory mapping

Figure 6. Memory map



5 Electrical characteristics

5.1 Parameter conditions

5.1.1 Minimum and maximum values

The minimum and maximum values are obtained in the worst conditions. Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. The minimum and maximum values represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

5.1.2 Typical values

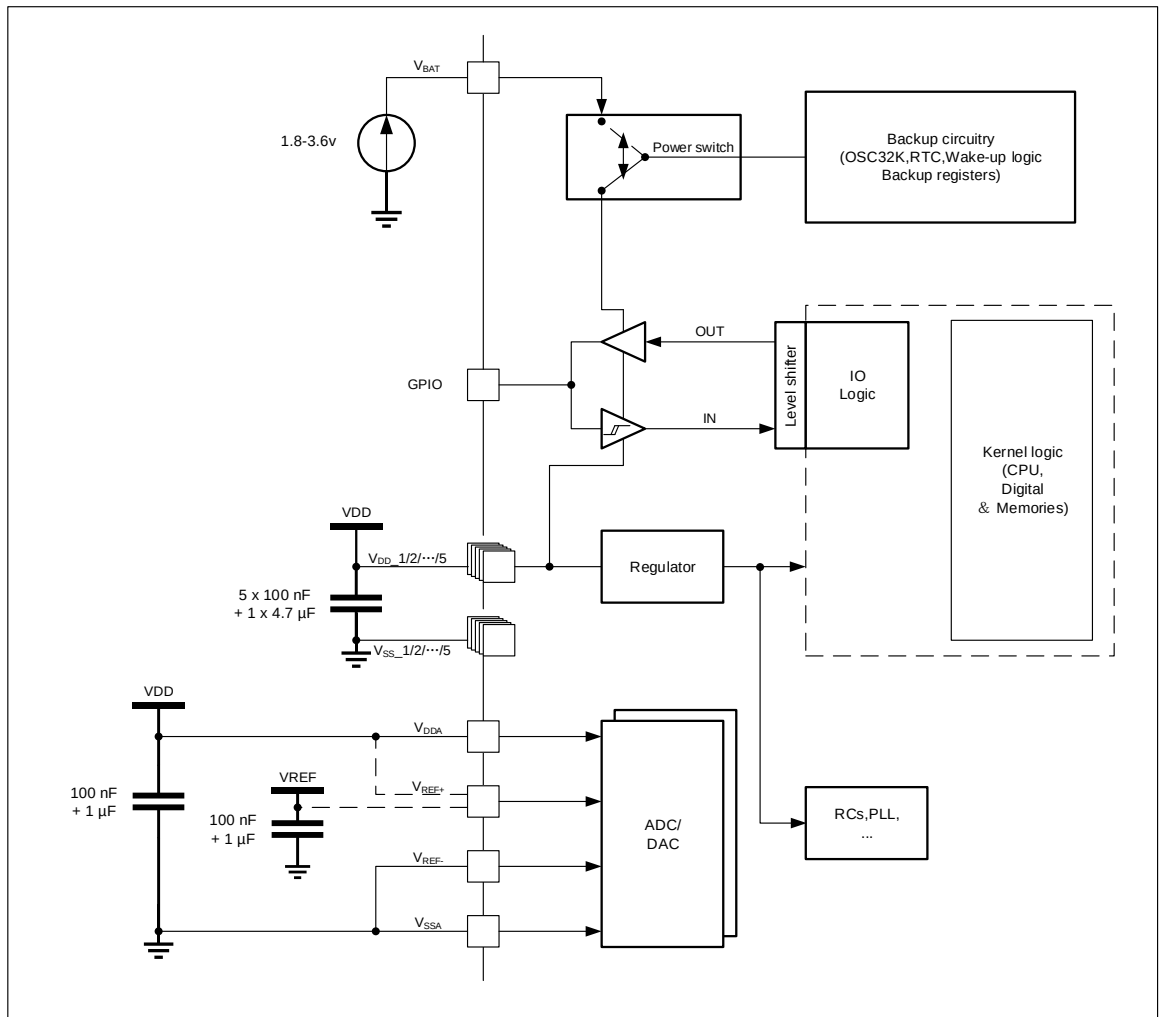
Typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$.

5.1.3 Typical curves

All typical curves are given only as design guidelines and are not tested.

5.1.4 Power supply scheme

Figure 7. Power supply scheme



Caution: In this figure, the 4.7μF capacitor must be connected to V_{DD_3} .

5.2 Absolute maximum values

5.2.1 Ratings

If stresses were out of the absolute maximum ratings listed in [Table 8](#), [Table 9](#), and [Table 10](#), it may cause permanent damage to the device. These are maximum stress ratings only that the device could bear, but the functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for an extended period of times may affect device reliability.

Table 8. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V _{DD} -V _{SS}	External main supply voltage (including V _{DDA} and V _{DD})	-0.3	4.0	V
V _{IN}	Input voltage on FT GPIO	V _{SS} -0.3	6.0	
	Input voltage on FTa GPIO (set as input floating, input pull-up, or input pull-down mode)			
	Input voltage on TC GPIO	V _{SS} -0.3	4.0	
	Input voltage on FTa GPIO (set as analog mode)			
ΔV _{DDx}	Variations between different V _{DD} power pins	-	50	mV
V _{SSx} -V _{SS}	Variations between all the different ground pins	-	50	

Table 9. Current characteristics

Symbol	Ratings	Max	Unit
I_{VDD}	Total current into V_{DD} power lines (source)	150	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)	150	
I_{IO}	Output current sunk by any GPIO and control pin	25	
	Output current source by any GPIOs and control pin	-25	

Table 10. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-60 ~ +150	°C
T_J	Maximum junction temperature	125	

5.2.2 Electrical sensitivity

Based on three different tests (HBM, CDM, and LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges are applied to the pins of each sample according to each pin combination. This test is compliant with the AEC-Q100-002-REV-E-2013 and AEC-Q100-011-REV-D-2019 standard.

Table 11. ESD values

Symbol	Parameter	Conditions	Class	Max	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforms to AEC-Q100-002-REV-E-2013	3A	5000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ }^{\circ}\text{C}$, conforms to AEC-Q100-011-REV-D-2019	III	1000	

Static latch-up

Tests compliant with AEC-Q100-004-REV-D-2012 IC latch-up test specification on integrated circuit devices are required to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin;
- A current injection is applied to each input, output and configurable GPIO pin.

Table 12. Latch-up values

Symbol	Parameter	Conditions	Level/Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$	II level A (200 mA)

5.3 Specifications

5.3.1 General operating conditions

Table 13. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency	Flash memory bank 3 (SPIM) not used	3.1 V ≤ V _{DD} ≤ 3.6 V	0	200
			2.6 V ≤ V _{DD} < 3.1 V	0	180
		Flash memory bank 3 used (SPIM)	3.1 V ≤ V _{DD} ≤ 3.6 V	0	180
			2.6 V ≤ V _{DD} < 3.1 V	0	160
f _{PCLK1}	Internal APB1 clock frequency	-	0	100	MHz
f _{PCLK2}	Internal APB2 clock frequency	-	0	100	MHz
V _{DD}	Digital operating voltage	-	2.6	3.6	V
V _{DDA}	Analog operating voltage	Must be the same potential as V _{DD}	2.6	3.6	V
V _{BAT}	Backup operating voltage	-	1.8	3.6	V
P _D	Power dissipation: T _A = 105 °C	LQFP100	-	326	mW
		LQFP64	-	309	
		LQFP48	-	290	
		QFN48	-	662	
T _A	Ambient temperature	-	-40	105	°C

5.3.2 Operating conditions at power-up / power-down

Table 14. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t _{VDD}	V _{DD} rise time rate	-	0	∞ ⁽¹⁾	ms/V
	V _{DD} fall time rate		20	∞	μs/V

(1) If V_{DD} rising time rate is slower than 120 ms/V, the code should access the backup registers after V_{DD} higher than V_{POR} + 0.1V.

5.3.3 Embedded reset and power control block characteristics

Table 15. Embedded reset and power management block characteristics

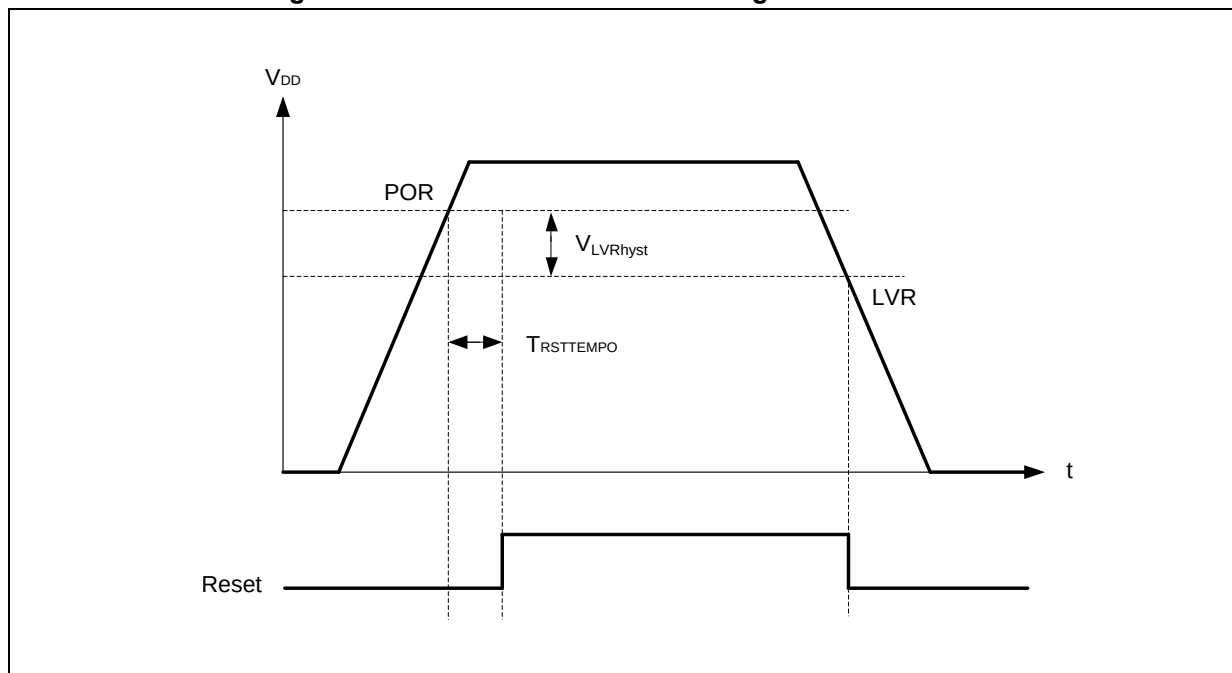
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{PVM}	Power voltage monitoring level selection	PVMSEL[2:0] = 001 (rising edge) ⁽¹⁾	2.19	2.28	2.37	V
		PVMSEL [2:0] = 001 (falling edge) ⁽¹⁾	2.09	2.18	2.27	V
		PVMSEL [2:0] = 010 (rising edge) ⁽²⁾	2.28	2.38	2.48	V
		PVMSEL [2:0] = 010 (falling edge) ⁽²⁾	2.18	2.28	2.38	V
		PVMSEL [2:0] = 011 (rising edge) ⁽²⁾	2.38	2.48	2.58	V
		PVMSEL [2:0] = 011 (falling edge) ⁽²⁾	2.28	2.38	2.48	V
		PVMSEL [2:0] = 100 (rising edge) ⁽²⁾	2.47	2.58	2.69	V
		PVMSEL [2:0] = 100 (falling edge) ⁽²⁾	2.37	2.48	2.59	V
		PVMSEL [2:0] = 101 (rising edge) ⁽²⁾	2.57	2.68	2.79	V
		PVMSEL [2:0] = 101 (falling edge) ⁽²⁾	2.47	2.58	2.69	V
		PVMSEL [2:0] = 110 (rising edge) ⁽²⁾	2.66	2.78	2.9	V
		PVMSEL [2:0] = 110 (falling edge) ⁽²⁾	2.56	2.68	2.8	V
		PVMSEL [2:0] = 111 (rising edge)	2.76	2.88	3	V
		PVMSEL [2:0] = 111 (falling edge)	2.66	2.78	2.9	V
V _{HYS+P} ⁽²⁾	PVM hysteresis	-	-	100	-	mV
V _{POR} ⁽²⁾	Power on reset threshold	-	2.03	2.18	2.35	V
V _{LVR} ⁽²⁾	Low voltage reset threshold	-	1.85 ⁽³⁾	2.02	2.2	V
V _{LVRhyst} ⁽²⁾	LVR hysteresis	-	-	160	-	mV
T _{RESTTEMPO} ⁽²⁾	Reset temporization: CPU starts execution after V _{DD} keeps higher than V _{POR} for T _{RSSTEMPO}	-	-	13	-	ms

(1) PVMSEL[2:0] = 001 may be not available for its voltage detector level may be lower than V_{POR/PDR}.

(2) Guaranteed by design, not tested in production.

(3) The product behavior is guaranteed by design down to the minimum V_{LVR} value.

Figure 8. Power on reset and low voltage reset waveform



5.3.4 Memory characteristics

Table 16. Internal Flash memory characteristics

Symbol	Parameter	Conditions	Typ ⁽¹⁾	Max ⁽¹⁾	Unit
T_{PROG}	Programming time	-	50	200	μs
t_{SE}	Sector (2 KB) erase time	-	50	500	ms
t_{BKE}	Bank erase time	AT32A403AxC	0.8	10	s
		AT32A403AxE	1.6	20	
		AT32A403AxG			

(1) Guaranteed by design, not tested in production.

Table 17. Internal Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max	Unit
N_{END}	Endurance	$T_A = -40 \sim 105\text{ }^{\circ}\text{C}$	100	-	-	kcycles
t_{RET}	Data retention	$T_A = 105\text{ }^{\circ}\text{C}$	10	-	-	years

(1) Guaranteed by design, not tested in production.

5.3.5 Supply current characteristics

The current consumption is subjected to several parameters and factors such as the operating voltage, ambient temperature, GPIO pin loading, device software configuration, operating frequencies, GPIO pin switching rate, and executed binary code. The current consumption is obtained by characterization results, not tested in production.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All GPIO pins are in analog mode.
- Prefetch ON. (Reminder: this bit must be set before setting clock and bus frequency division.)
- When the peripherals are enabled:
 - $f_{HCLK} > 100 \text{ MHz}$: $f_{PCLK1} = f_{HCLK}/2$, $f_{PCLK2} = f_{HCLK}/2$, $f_{ADCCLK} = f_{PCLK2}/4$
 - If $f_{HCLK} \leq 100 \text{ MHz}$: $f_{PCLK1} = f_{HCLK}$, $f_{PCLK2} = f_{HCLK}$, $f_{ADCCLK} = f_{PCLK2}/4$.
- Codes are executed in ZW area.
- Unless otherwise specified, the typical values are measured with $V_{DD} = 3.3 \text{ V}$ and $T_A = 25 \text{ }^\circ\text{C}$ condition and the maximum values are measured with $V_{DD} = 3.6 \text{ V}$.

Table 18. Typical current consumption in Run mode

Sym bol	Parameter	Conditions	f_{HCLK}	Typ.		Unit
				All peripherals enabled	All peripherals disabled	
I_{DD}	Supply current in Run mode	High speed external crystal (HEXT) ⁽¹⁾⁽²⁾	200 MHz	84.7	34.6	mA
			144 MHz	62.0	25.7	
			120 MHz	62.5	23.3	
			108 MHz	56.7	21.3	
			72 MHz	39.2	15.4	
			48 MHz	27.1	11.1	
			36 MHz	21.0	8.99	
			24 MHz	14.9	6.86	
			16 MHz	10.8	5.44	
			8 MHz	6.25	3.58	
			4 MHz	4.29	2.95	
			2 MHz	3.31	2.63	
			1 MHz	2.83	2.47	
			500 kHz	2.59	2.39	
			125 kHz	2.40	2.34	
		High speed internal clock (HICK) ⁽²⁾	200 MHz	84.6	34.6	mA
			144 MHz	61.9	25.6	
			120 MHz	62.5	23.2	
			108 MHz	56.6	21.2	
			72 MHz	39.2	15.4	
			48 MHz	27.0	11.1	
			36 MHz	20.9	8.91	
			24 MHz	14.8	6.78	
			16 MHz	10.7	5.36	
			8 MHz	6.16	3.49	
			4 MHz	4.20	2.86	
			2 MHz	3.22	2.54	
			1 MHz	2.74	2.39	
			500 kHz	2.50	2.31	
			125 kHz	2.32	2.25	

(1) External clock is 8 MHz.

(2) PLL is on when $f_{HCLK} > 8$ MHz.

Table 19. Typical current consumption in Sleep mode

Sym bol	Parameter	Conditions	f_{HCLK}	Typ.		Unit
				All peripherals enabled	All peripherals disabled	
I_{DD}	Supply current in Sleep mode	High speed external crystal (HEXT) ⁽¹⁾⁽²⁾	200 MHz	71.7	10.8	mA
			144 MHz	52.5	8.52	
			120 MHz	53.7	8.07	
			108 MHz	48.7	7.54	
			72 MHz	33.9	6.29	
			48 MHz	23.5	5.07	
			36 MHz	18.3	4.45	
			24 MHz	13.1	3.83	
			16 MHz	9.59	3.42	
			8 MHz	5.66	2.57	
			4 MHz	4.00	2.45	
			2 MHz	3.17	2.39	
			1 MHz	2.76	2.36	
			500 kHz	2.55	2.34	
			125 kHz	2.40	2.33	
		High speed internal clock (HICK) ⁽²⁾	200 MHz	71.7	10.8	mA
			144 MHz	52.6	8.44	
			120 MHz	53.7	7.99	
			108 MHz	48.7	7.45	
			72 MHz	33.8	6.20	
			48 MHz	23.4	4.97	
			36 MHz	18.2	4.35	
			24 MHz	13.0	3.74	
			16 MHz	9.51	3.33	
			8 MHz	5.57	2.48	
			4 MHz	3.91	2.36	
			2 MHz	3.08	2.30	
			1 MHz	2.67	2.27	
			500 kHz	2.47	2.25	
			125 kHz	2.31	2.24	

(1) External clock is 8 MHz.

(2) PLL is on when $f_{HCLK} > 8$ MHz.

Table 20. Maximum current consumption in Run mode

Symbol	Parameter	Conditions	f_{HCLK}	Max		Unit
				$T_A = 85\text{ }^{\circ}\text{C}$	$T_A = 105\text{ }^{\circ}\text{C}$	
I_{DD}	Supply current in Run mode	High speed external crystal (HEXT) ⁽¹⁾ , all peripherals enabled	200 MHz	99.2	110.2	mA
			144 MHz	75.9	87.4	
			120 MHz	76.7	86.5	
			108 MHz	70.7	81.3	
			72 MHz	52.5	62.8	
			48 MHz	39.9	50.0	
			36 MHz	33.5	43.5	
			24 MHz	27.1	37.0	
			16 MHz	22.8	32.6	
			8 MHz	18.0	27.8	
		High speed external crystal (HEXT) ⁽¹⁾ , all peripherals disabled	200 MHz	46.9	57.0	mA
			144 MHz	37.8	47.7	
			120 MHz	35.4	45.3	
			108 MHz	33.3	43.2	
			72 MHz	27.3	37.1	
			48 MHz	22.9	32.6	
			36 MHz	20.7	30.4	
			24 MHz	18.5	28.2	
			16 MHz	17.0	26.7	
			8 MHz	15.2	24.8	

(1) External clock is 8 MHz and PLL is on when $f_{HCLK} > 8\text{ MHz}$.

Table 21. Maximum current consumption in Sleep mode

Symbol	Parameter	Conditions	f_{HCLK}	Max		Unit
				$T_A = 85\text{ }^{\circ}\text{C}$	$T_A = 105\text{ }^{\circ}\text{C}$	
I_{DD}	Supply current in Sleep mode	High speed external crystal (HEXT) ⁽¹⁾ , all peripherals enabled	200 MHz	86.0	96.4	mA
			144 MHz	66.2	78.0	
			120 MHz	67.7	76.5	
			108 MHz	62.5	72.7	
			72 MHz	47.0	57.0	
			48 MHz	36.1	46.0	
			36 MHz	30.6	40.4	
			24 MHz	25.1	34.8	
			16 MHz	21.5	31.1	
			8 MHz	17.3	26.9	
		High speed external crystal (HEXT) ⁽¹⁾ , all peripherals disabled	200 MHz	22.3	31.8	mA
			144 MHz	20.0	29.4	
			120 MHz	19.6	29.0	
			108 MHz	19.0	28.4	
			72 MHz	17.7	27.1	
			48 MHz	16.4	25.8	
			36 MHz	15.8	25.2	
			24 MHz	15.2	24.6	
			16 MHz	14.8	24.2	
			8 MHz	13.9	23.3	

(1) External clock is 8 MHz and PLL is on when $f_{HCLK} > 8\text{ MHz}$.

Table 22. Typical and maximum current consumptions in Deepsleep and Standby modes

Symbol	Parameter	Conditions	Typ ⁽¹⁾		Max ⁽²⁾			Unit
			$V_{DD}/V_{BAT} = 2.6\text{ V}$	$V_{DD}/V_{BAT} = 3.3\text{ V}$	$T_A = 25\text{ }^{\circ}\text{C}$	$T_A = 85\text{ }^{\circ}\text{C}$	$T_A = 105\text{ }^{\circ}\text{C}$	
I_{DD}	Supply current in Deepsleep mode	LDO in Run mode, HICK and HEXT OFF (no WDT)	1.35	1.36	Refer to note ⁽³⁾	13.6	23.7	mA
		LDO in low-power mode, HICK and HEXT OFF (no WDT)	1.33	1.34		13.1	22.8	
	Supply current in Standby mode	LEXT and RTC OFF	3.93	5.72	7.49	10.4	14.9	μA
		LEXT and RTC ON	4.55	6.48	8.34	11.5	16.5	

(1) Typical values are measured at $T_A = 25\text{ }^{\circ}\text{C}$.

(2) Guaranteed by characterization results, not tested in production.

(3) The value may be several times the typical values due to process variation.

Figure 9. Typical current consumption in Deepsleep mode vs. temperature at different V_{DD}

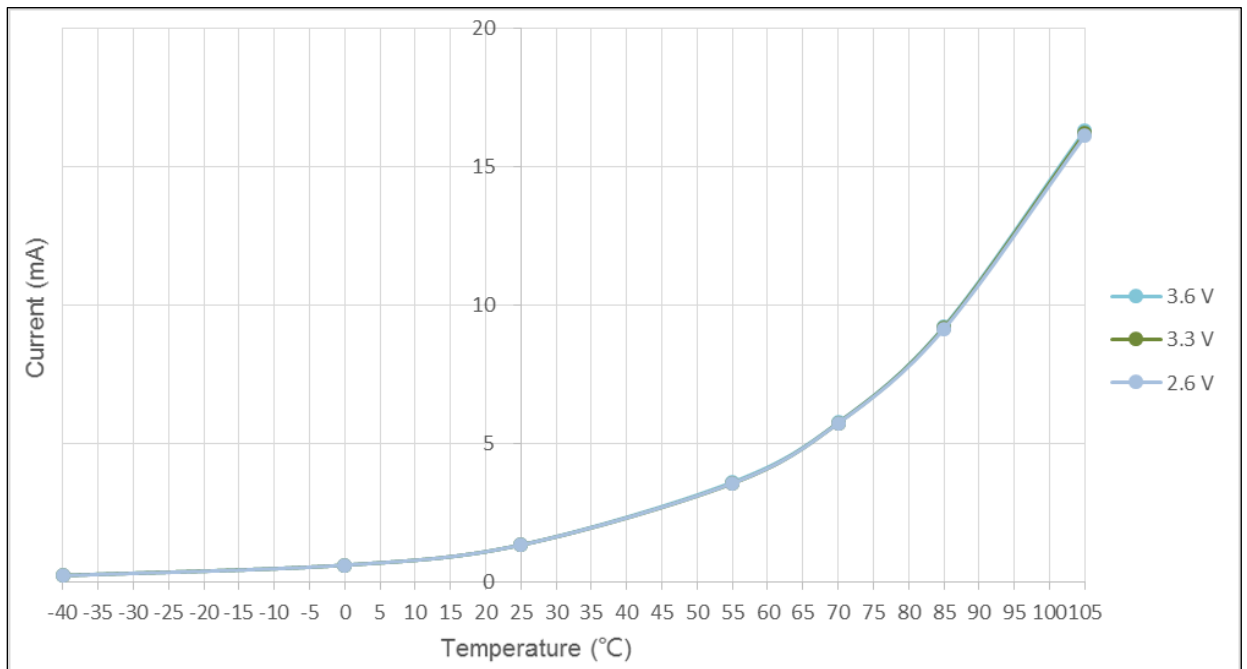


Figure 10. Typical current consumption in Standby mode vs. temperature at different V_{DD}

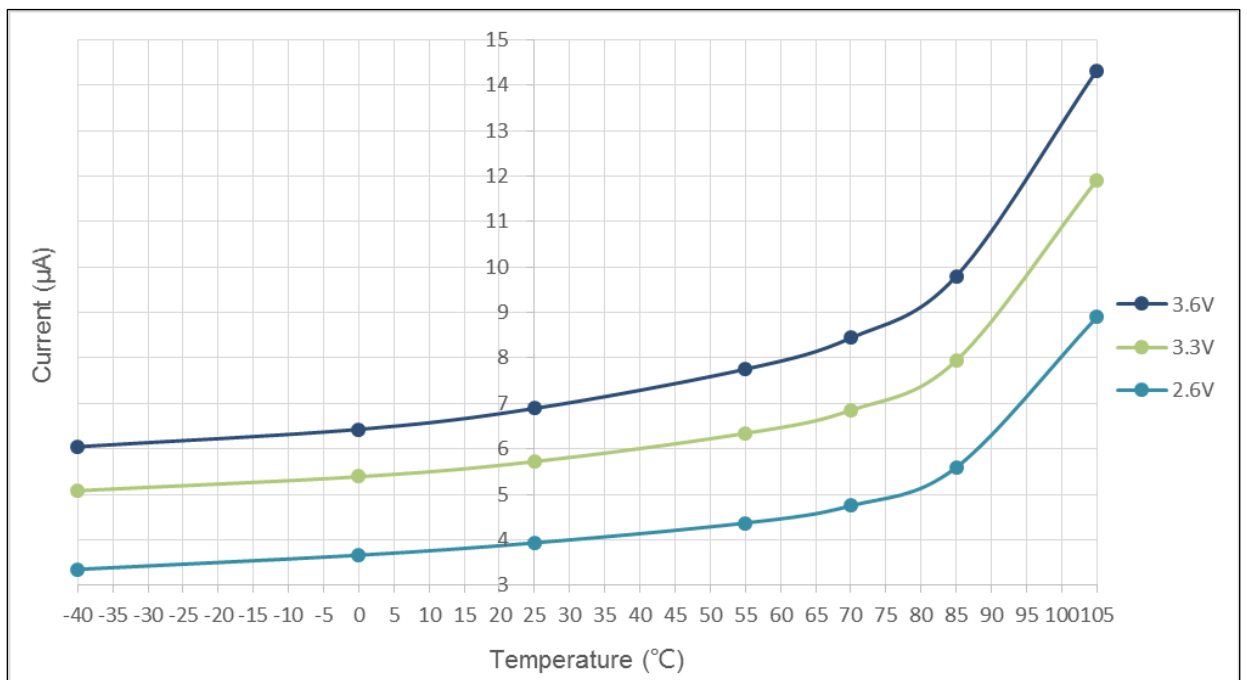


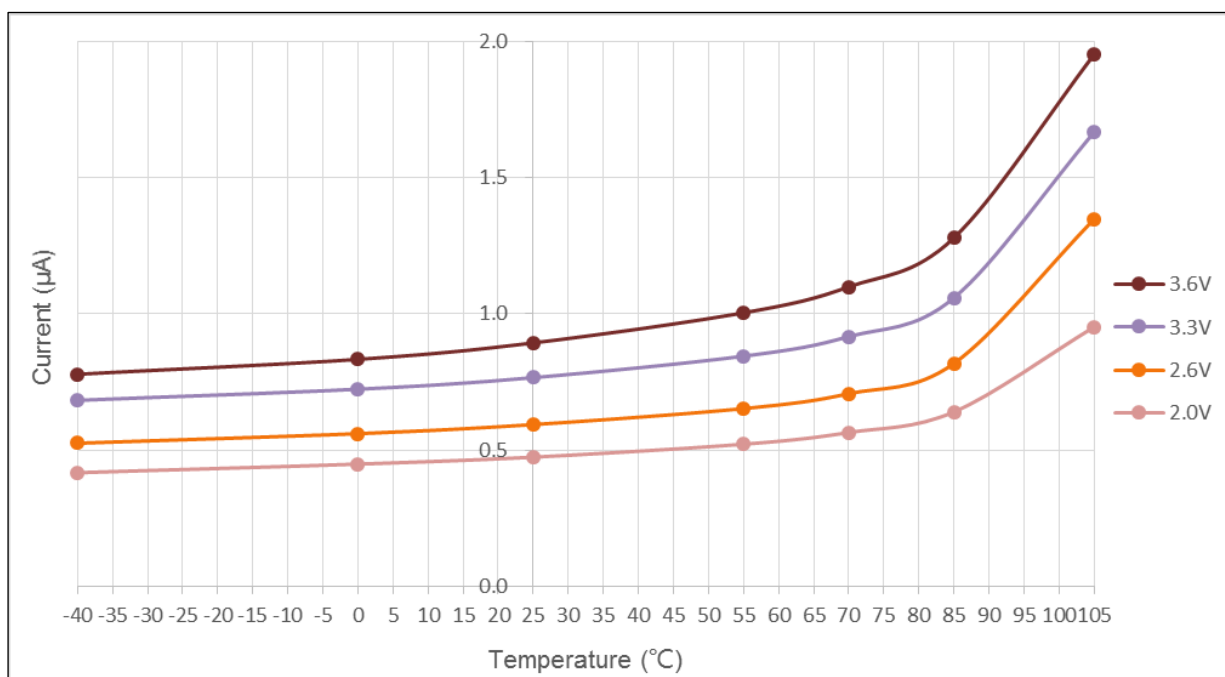
Table 23. Typical and maximum current consumptions on V_{BAT}

Symbol	Parameter	Conditions	Typ ⁽¹⁾			Max ⁽²⁾			Unit
			$V_{BAT} = 2.0\text{ V}$	$V_{BAT} = 2.6\text{ V}$	$V_{BAT} = 3.3\text{ V}$	$T_A = 25\text{ }^{\circ}\text{C}$	$T_A = 85\text{ }^{\circ}\text{C}$	$T_A = 105\text{ }^{\circ}\text{C}$	
I_{DD_VBAT}	V_{BAT} Supply current	LEXT and RTC ON, $V_{DD} < V_{LVR}$	0.47	0.59	0.77	0.92	1.34	2.04	μA

(1) Typical values are measured at $T_A = 25\text{ }^{\circ}\text{C}$.

(2) Guaranteed by characterization results, not tested in production.

Figure 11. Typical current consumption on V_{BAT} with LEXT and RTC ON vs. temperature at different V_{BAT}



On-chip peripheral current consumption

The MCU is placed under the following conditions:

- All GPIO pins are in analog mode.
- The given value is calculated by measuring the current consumption difference between “all peripherals clocked OFF” and “only one peripheral clocked ON”.

Table 24. Peripheral current consumption

Peripheral		Typ	Unit
AHB	DMA1	9.34	μA/MHz
	DMA2	9.39	
	GPIOA	1.41	
	GPIOB	1.41	
	GPIOC	1.47	
	GIPOD	1.43	
	GPIOE	1.44	
	XMC	26.89	
	CRC	1.53	
	SDIO1	19.62	
	SDIO2	20.40	
	EMAC EMAC_TX EMAC_RX EMAC_PTP	30.78	
APB1	TMR2	9.11	
	TMR3	6.52	
	TMR4	6.54	
	TMR5	8.82	
	TMR6	0.77	
	TMR7	0.75	
	TMR12	3.89	
	TMR13	2.45	
	TMR14	2.48	
	SPI2/I ² S2	5.19	
	SPI3/I ² S3	4.95	
	SPI4/I ² S4	2.62	
	USART2	2.60	
	USART3	2.57	
	UART4	2.60	
	UART5	2.63	

Peripheral		Typ	Unit
APB1	I ² C1	2.47	μA/MHz
	I ² C2	2.54	
	USBFS1	6.40	
	CAN1	3.77	
	CAN2	3.77	
	DAC1/2	2.30	
	WWDT	0.34	
	PWC	0.34	
	BPR	68.36	
APB2	IOMUX	2.32	
	SPI1/I ² S1	2.82	
	USART1	2.53	
	USART6	2.64	
	UART7	2.80	
	UART8	2.85	
	I ² C3	2.48	
	TMR1	8.99	
	TMR8	8.72	
	TMR9	3.78	
	TMR10	2.62	
	TMR11	2.56	
	ADC1	5.17	
	ADC2	5.24	
	ADC3	5.18	
	ACC	0.95	

5.3.6 External clock source characteristics

High-speed external clock generated from a crystal / ceramic resonator

The high-speed external (HEXT) clock can be supplied with a 4 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in the table below. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 25. HEXT 4-25 MHz crystal characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{\text{HEXT_IN}}$	Oscillator frequency	-	4	8	25	MHz
$t_{\text{SU(HEXT)}}^{(3)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

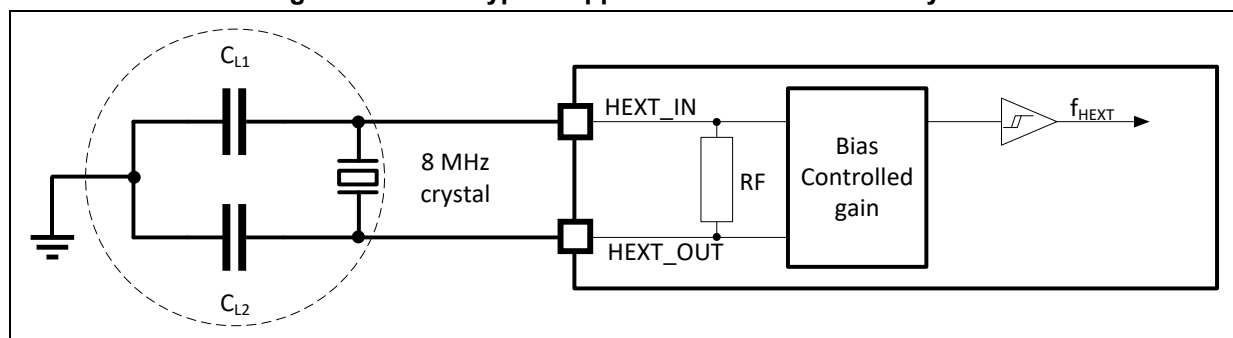
(1) Oscillator characteristics given by the crystal/ceramic resonator manufacturer.

(2) Guaranteed by characterization results, not tested in production.

(3) $t_{\text{SU(HEXT)}}$ is the startup time measured from the moment HEXT is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Figure 12. HEXT typical application with an 8 MHz crystal



High-speed external clock generated from an external source

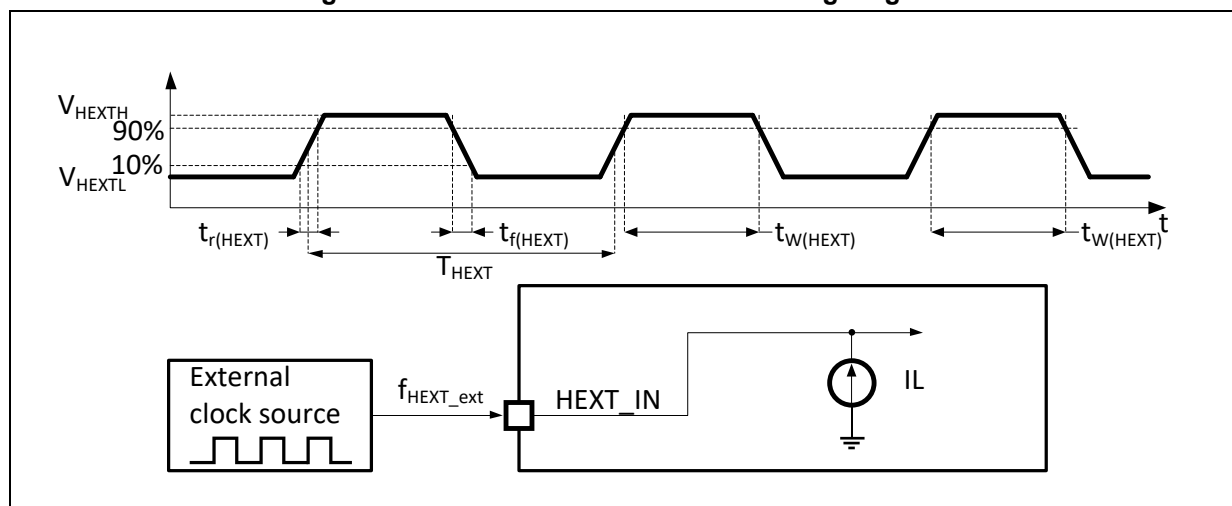
The characteristics given in the table below result from tests performed using a high-speed external clock source.

Table 26. HEXT external source characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{\text{HEXT_ext}}$	User external clock source frequency ⁽¹⁾	-	1	8	25	MHz
V_{HEXTH}	HEXT_IN input pin high level voltage		$0.7V_{\text{DD}}$	-	V_{DD}	V
V_{HEXTL}	HEXT_IN input pin low level voltage		V_{SS}	-	$0.3V_{\text{DD}}$	
$t_{\text{w(HEXT)}}$ $t_{\text{w(HEXT)}}$	HEXT_IN high or low time ⁽¹⁾		5	-	-	ns
$t_{\text{r(HEXT)}}$ $t_{\text{f(HEXT)}}$	HEXT_IN rise or fall time ⁽¹⁾		-	-	20	
$C_{\text{in(HEXT)}}$	HEXT_IN input capacitance ⁽¹⁾	-	-	5	-	pF
Duty(HEXT)	Duty cycle	-	45	-	55	%
I_{L}	HEXT_IN Input leakage current	$V_{\text{SS}} \leq V_{\text{IN}} \leq V_{\text{DD}}$	-	-	± 1	μA

(1) Guaranteed by design, not tested in production.

Figure 13. HEXT external source AC timing diagram



Low-speed external clock generated from a crystal / ceramic resonator

The low-speed external (LEXT) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in the table below. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 27. LEXT 32.768 kHz crystal characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{SU(LEXT)}	Startup time	V _{DD} is stabilized	-	150	-	ms

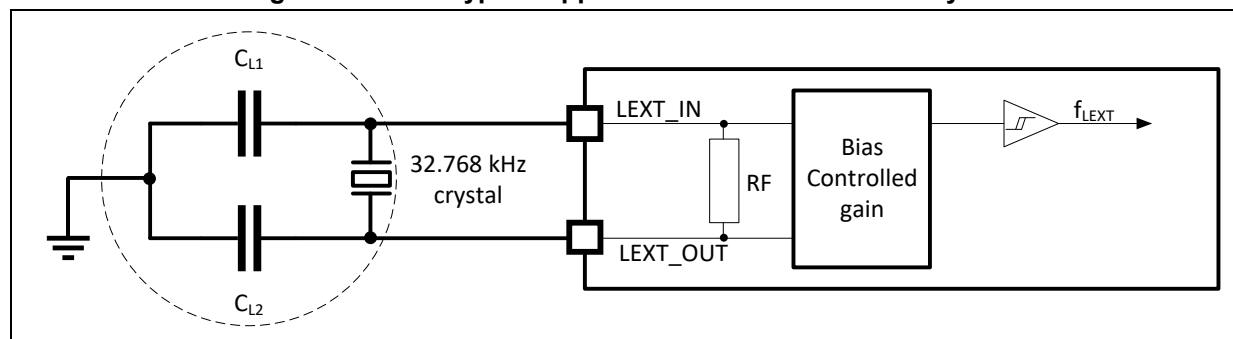
(1) Oscillator characteristics given by the crystal/ceramic resonator manufacturer.

(2) Guaranteed by characterization results, not tested in production.

For C_{L1} and C_{L2}, it is recommended to use high-quality ceramic capacitors in the 5 pF to 20 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}.

Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{\text{stray}}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Figure 14. LEXT typical application with a 32.768 kHz crystal



Note: No external resistor is required between LEXT_IN and LEXT_OUT and it is also prohibited to add it.

Low-speed external clock generated from an external source

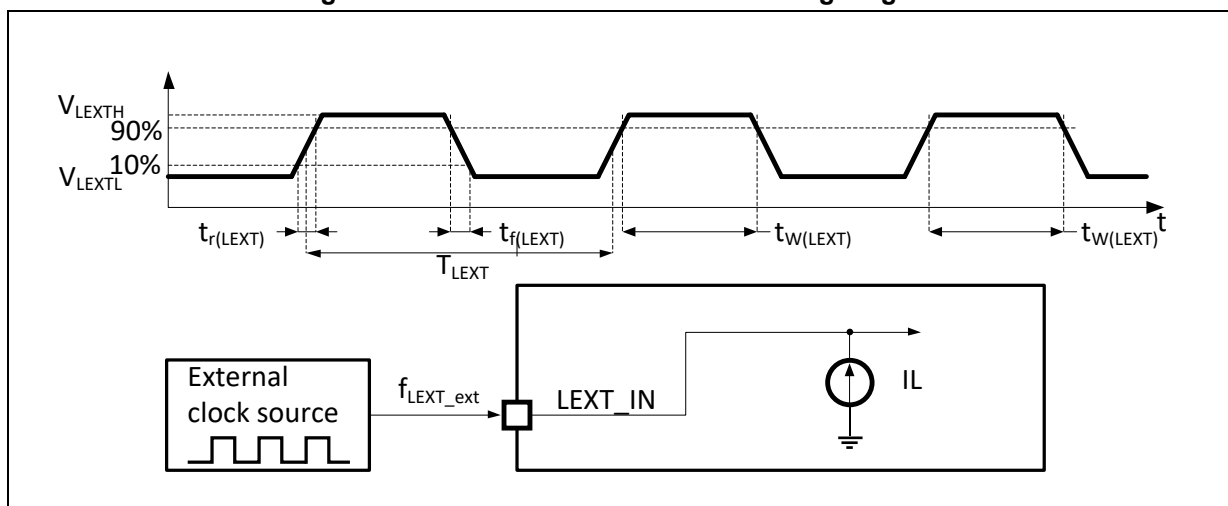
The characteristics given in the table below result from tests performed using a low-speed external clock source.

Table 28. LEXT external source characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{\text{LEXT_ext}}$	User External clock source frequency ⁽¹⁾	-	-	32.768	1000	kHz
V_{LEXTH}	LEXT_IN input pin high level voltage		$0.7V_{\text{DD}}$	-	V_{DD}	V
V_{LEXTL}	LEXT_IN input pin low level voltage		V_{SS}	-	$0.3V_{\text{DD}}$	
$t_{\text{w(LEXT)}}$ $t_{\text{w(LEXT)}}$	LEXT_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{\text{r(LEXT)}}$ $t_{\text{f(LEXT)}}$	LEXT_IN rise or fall time ⁽¹⁾		-	-	50	
$C_{\text{in(LEXT)}}$	LEXT_IN input capacitance ⁽¹⁾	-	-	5	-	pF
Duty(LEXT)	Duty cycle	-	30	-	70	%
I_{L}	LEXT_IN input leakage current	$V_{\text{SS}} \leq V_{\text{IN}} \leq V_{\text{DD}}$	-	-	± 1	μA

(1) Guaranteed by design, not tested in production.

Figure 15. LEXT external source AC timing diagram



5.3.7 Internal clock source characteristics

High-speed internal clock (HICK)

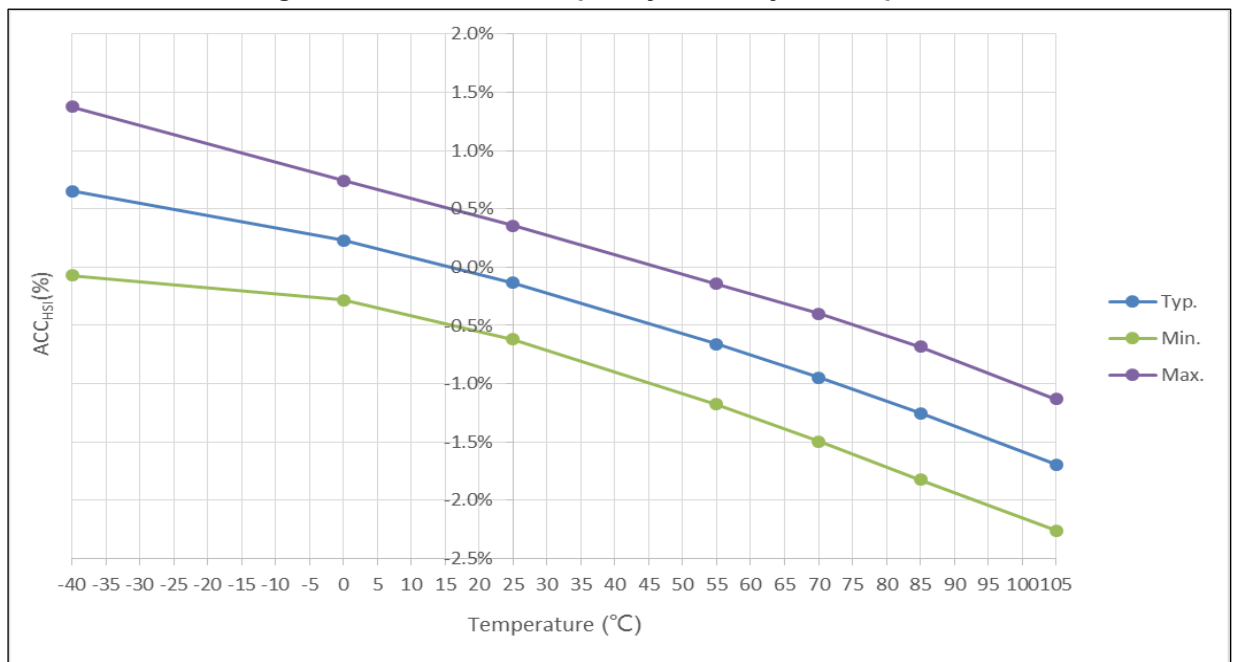
Table 29. HICK clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HICK}	Frequency	-	-	48	-	MHz
$DuCy_{(HICK)}$	Duty cycle	-	45	-	55	%
ACC_{HICK}	Accuracy of the HICK oscillator	User-trimmed with the CRM_CTRL register	-	-	1 ⁽¹⁾	%
		ACC-trimmed	-	-	0.25 ⁽¹⁾	
		Factory-calibrated ⁽²⁾	$T_A = -40 \sim 105\text{ }^{\circ}\text{C}$	-2.5	2	%
			$T_A = -40 \sim 85\text{ }^{\circ}\text{C}$	-2	2	
			$T_A = 0 \sim 70\text{ }^{\circ}\text{C}$	-1.5	1.5	
			$T_A = 25\text{ }^{\circ}\text{C}$	-1	1	
$ts_{U(HICK)}^{(2)}$	HICK oscillator startup time	-	-	-	10	μs
$I_{DD(HICK)}^{(2)}$	HICK oscillator power consumption	-	-	240	290	μA

(1) Guaranteed by design, not tested in production.

(2) Guaranteed by characterization results, not tested in production.

Figure 16. HICK clock frequency accuracy vs. temperature



Low-speed internal clock (LICK)

Table 30. LICK clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{LICK}^{(1)}$	Frequency	-	30	40	60	kHz

(1) Guaranteed by characterization results, not tested in production.

5.3.8 PLL characteristics

Table 31. PLL characteristics

Symbol	Parameter	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
f _{PLL_IN}	PLL input clock ⁽²⁾	2	8	16	MHz
	PLL input clock duty cycle	40	-	60	%
f _{PLL_OUT}	PLL multiplier output clock	16	-	200	MHz
t _{LOCK}	PLL lock time	-	-	200	μs
Jitter	Cycle-to-cycle jitter	-	-	300	ps

(1) Guaranteed by design, not tested in production.

(2) Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

5.3.9 Wakeup time from low-power mode

The wakeup times given in the table below is measured on a wakeup phase with the HICK. The clock source used to wake up the device depends from the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode.
- Deepsleep or Standby mode: the clock source is the HICK.

Table 32. Low-power mode wakeup time

Symbol	Parameter	Typ	Unit
t _{WUSLEEP}	Wakeup from Sleep mode	3.3	μs
t _{WUDEEPSLEEP}	Wakeup from Deepsleep mode (regulator in normal mode)	280	μs
	Wakeup from Deepsleep mode (regulator in low-power mode)	320	
t _{WUSTDBY}	Wakeup from Standby mode	8	ms

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

- **EFT:** A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a coupling/decoupling network, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

Table 33. EMS characteristics

Symb	Parameter	Conditions	Level/Class
V_{EFT}	Fast transient voltage burst limits to be applied through coupling/decoupling network conforms to IEC 61000-4-4 on V_{DD} and V_{SS} pins to induce a functional disturbance, V_{DD} and V_{SS} input has one 47 μF capacitor and each V_{DD} and V_{SS} pair 0.1 μF	$V_{DD} = 3.3 \text{ V}$, LQFP100, $T_A = +25 \text{ }^\circ\text{C}$, $f_{HCLK} = 200 \text{ MHz}$	4A (4kV)
		$V_{DD} = 3.3 \text{ V}$, LQFP100, $T_A = +25 \text{ }^\circ\text{C}$, $f_{HCLK} = 72 \text{ MHz}$	

EMC characterization and optimization are performed at component level with a typical application environment. It should be noted that good EMC performance is highly dependent on the user application and the software in particular. Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Electromagnetic interference (EMI)

The electromagnetic field emitted by the device is monitored while a Coremark program is running and outputting 20 kHz square wave through two GPIO pins (no load outside the device)

This emission test is compliant with SAE J1752/3 standard.

Table 34. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max.	Unit
S_{EMI}	Peak value	$V_{DD} = 3.3 \text{ V}$, LQFP100, $T_A = +25 \text{ }^\circ\text{C}$, $f_{HICK}/f_{HCLK} = 8/200 \text{ MHz}$	0.15 MHz ~ 30 MHz	Not detected	dB μ V
			30 MHz ~ 130 MHz	13.8	
			130 MHz ~ 1 GHz	16.9	
	Level	-	-	M8	-

5.3.11 GPIO port characteristics

General input / output characteristics

All GPIOs are CMOS and TTL compliant.

Table 35. GPIO static characteristics

Symb	Parameter	Conditions	Min	Typ	Max	Unit
V _{IL}	GPIO input low level voltage	-	-0.3	-	0.28 x V _{DD} + 0.1	V
V _{IH}	TC GPIO input high level voltage	-	0.31 x V _{DD} + 0.8	-	V _{DD} + 0.3	V
	FTa GPIO input high level voltage	Analog mode		-	5.5	
	FT GPIO input high level voltage	-				
	FTa GPIO input high level voltage	Input floating, input pull-up, or input pull-down mode				
V _{hys}	TC GPIO Schmitt trigger voltage hysteresis ⁽¹⁾	-	200	-	-	mV
	FT and FTa GPIO Schmitt trigger voltage hysteresis ⁽¹⁾		5% V _{DD}	-	-	-
I _{lkg}	Input leakage current ⁽²⁾	V _{SS} ≤ V _{IN} ≤ V _{DD} TC GPIOs	-	-	±1	μA
		V _{SS} ≤ V _{IN} ≤ 5.5V FT and FTa GPIO	-	-	±1	
R _{PU}	Weak pull-up equivalent resistor ⁽³⁾	V _{IN} = V _{SS}	60	70	100	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁽³⁾ (4)	V _{IN} = V _{DD}	60	70	100	kΩ
C _{IO}	GPIO pin capacitance	-	-	9	-	pF

(1) Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

(2) Leakage could be higher than max if negative current is injected on adjacent pins.

(3) When the input is higher than $V_{DD} + 0.3$ V, the internal pull-up and pull-down resistors must be disabled for FT, and FTa pins.

(4) The pull-down resistor of BOOT0 exists permanently.

All GPIOs are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters.

Output driving current

In the user application, the number of GPIO pins which can drive current must be controlled to respect the absolute maximum rating defined in [Section 5.2.1](#):

- The sum of the currents sourced by all GPIOs on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating I_{VDD} (see [Table 9](#)).
- The sum of the currents sunk by all GPIOs on V_{SS} , plus the maximum Run consumption of the MCU sunk on V_{SS} , cannot exceed the absolute maximum rating I_{VSS} (see [Table 9](#)).

Output voltage levels

All GPIOs are CMOS and TTL compliant.

Table 36. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
Maximum sourcing/sinking strength					
V _{OL}	Output low level voltage	CMOS standard, I _{IO} = 15 mA	-	0.4	V
V _{OH}	Output high level voltage		V _{DD} -0.4	-	
V _{OL}	Output low level voltage	TTL standard, I _{IO} = 6 mA	-	0.4	V
V _{OH}	Output high level voltage		2.4	-	
Large sourcing/sinking strength					
V _{OL}	Output low level voltage	CMOS standard, I _{IO} = 6 mA	-	0.4	V
V _{OH}	Output high level voltage		V _{DD} -0.4	-	
V _{OL}	Output low level voltage	TTL standard, I _{IO} = 3 mA	-	0.4	V
V _{OH}	Output high level voltage		2.4	-	
V _{OL} ⁽¹⁾	Output low level voltage	I _{IO} = 20 mA	-	1.3	V
V _{OH} ⁽¹⁾	Output high level voltage		V _{DD} -1.3	-	
Normal sourcing/sinking strength					
V _{OL}	Output low level voltage	CMOS standard, I _{IO} = 4 mA	-	0.4	V
V _{OH}	Output high level voltage		V _{DD} -0.4	-	
V _{OL}	Output low level voltage	TTL standard, I _{IO} = 2 mA	-	0.4	V
V _{OH}	Output high level voltage		2.4	-	
V _{OL} ⁽¹⁾	Output low level voltage	I _{IO} = 10 mA	-	1.3	V
V _{OH} ⁽¹⁾	Output high level voltage		V _{DD} -1.3	-	

(1) Guaranteed by characterization results.

Input AC characteristics

The definition and values of input AC characteristics are given as follows.

Table 37. Input AC characteristics

Symbol	Parameter	Min	Max	Unit
$t_{EXINTpw}$	Pulse width of external signals detected by EXINT controller	10	-	ns

5.3.12 NRST pin characteristics

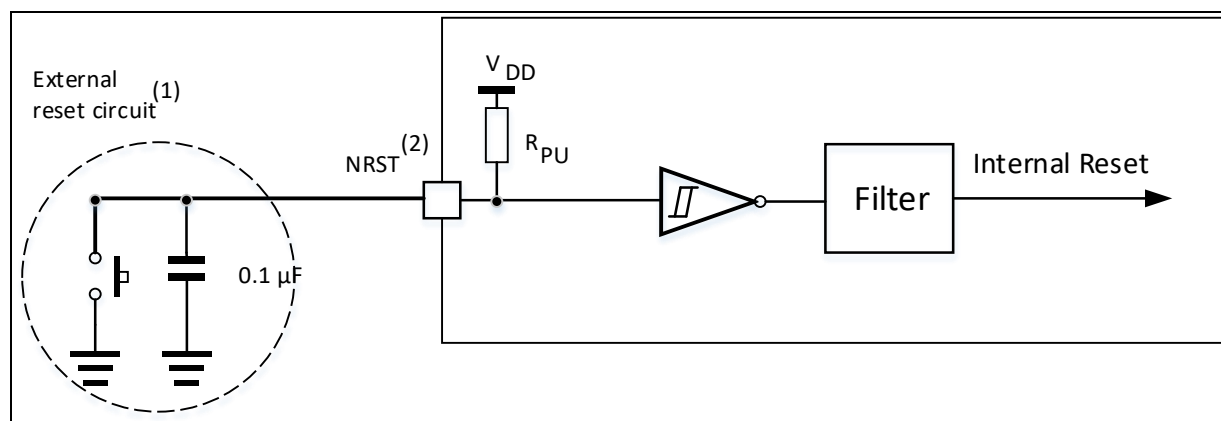
The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see the table below).

Table 38. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage	-	-0.5	-	0.8	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage	-	2	-	$V_{DD} + 0.3$	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	500	-	mV
R_{PU}	Weak pull-up equivalent resistor	$V_{IN} = V_{SS}$	30	40	50	k Ω
$t_{ILV(NRST)}^{(1)}$	NRST input low level invalid time	-	-	-	33.3	μ s
$t_{ILNV(NRST)}^{(1)}$	NRST input low level valid time	-	66.7	-	-	μ s

(1) Guaranteed by design, not tested in production.

Figure 17. Recommended NRST pin protection



(1) The reset network protects the device against parasitic resets.

(2) The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 38](#). Otherwise the reset will not be taken into account by the device.

5.3.13 XMC characteristics

The parameters given in the table below are guaranteed by design and not tested in production.

Asynchronous waveforms and timings of PSRAM / NOR

The results shown in these tables are obtained with the following XMC configuration:

- AddressSetupTime = 0
- AddressHoldTime = 1
- DataSetupTime = 1

Table 39. Asynchronous multiplexed PSRAM / NOR read timings

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	XMC_NE low time	$7t_{HCLK} - 2$	$7t_{HCLK} + 2$	ns
$t_{v(NO_NE)}$	XMC_NE low to XMC_NOE low	$3t_{HCLK} - 0.5$	$3t_{HCLK} + 1.5$	ns
$t_{w(NO)}$	XMC_NOE low time	$4t_{HCLK} - 1$	$4t_{HCLK} + 2$	ns
$t_{h(NE_NO)}$	XMC_NOE high to XMC_NE high hold time	-1	-	ns
$t_{v(A_NE)}$	XMC_NE low to XMC_A valid	-	0	ns
$t_{v(NADV_NE)}$	XMC_NE low to XMC_NADV low	3	5	ns
$t_{w(NADV)}$	XMC_NADV low time	$t_{HCLK} - 1.5$	$t_{HCLK} + 1.5$	ns
$t_{h(AD_NADV)}$	XMC_AD (address) valid hold time after XMC_NADV high	$t_{HCLK} + 3$	-	ns
$t_{h(A_NO)}$	Address hold time after XMC_NOE high	$t_{HCLK} + 3$	-	ns
$t_{h(UBLB_NO)}$	XMC_UB/LB hold time after XMC_NOE high	0	-	ns
$t_{v(UBLB_NE)}$	XMC_NE low to XMC_UB/LB valid	-	0	ns
$t_{su(Data_NE)}$	Data to XMC_NE high setup time	$2t_{HCLK} + 24$	-	ns
$t_{su(Data_NO)}$	Data to XMC_NOE high setup time	$2t_{HCLK} + 25$	-	ns
$t_{h(Data_NE)}$	Data hold time after XMC_NE high	0	-	ns
$t_{h(Data_NO)}$	Data hold time after XMC_NOE high	0	-	ns

Figure 18. Asynchronous multiplexed PSRAM / NOR read waveforms

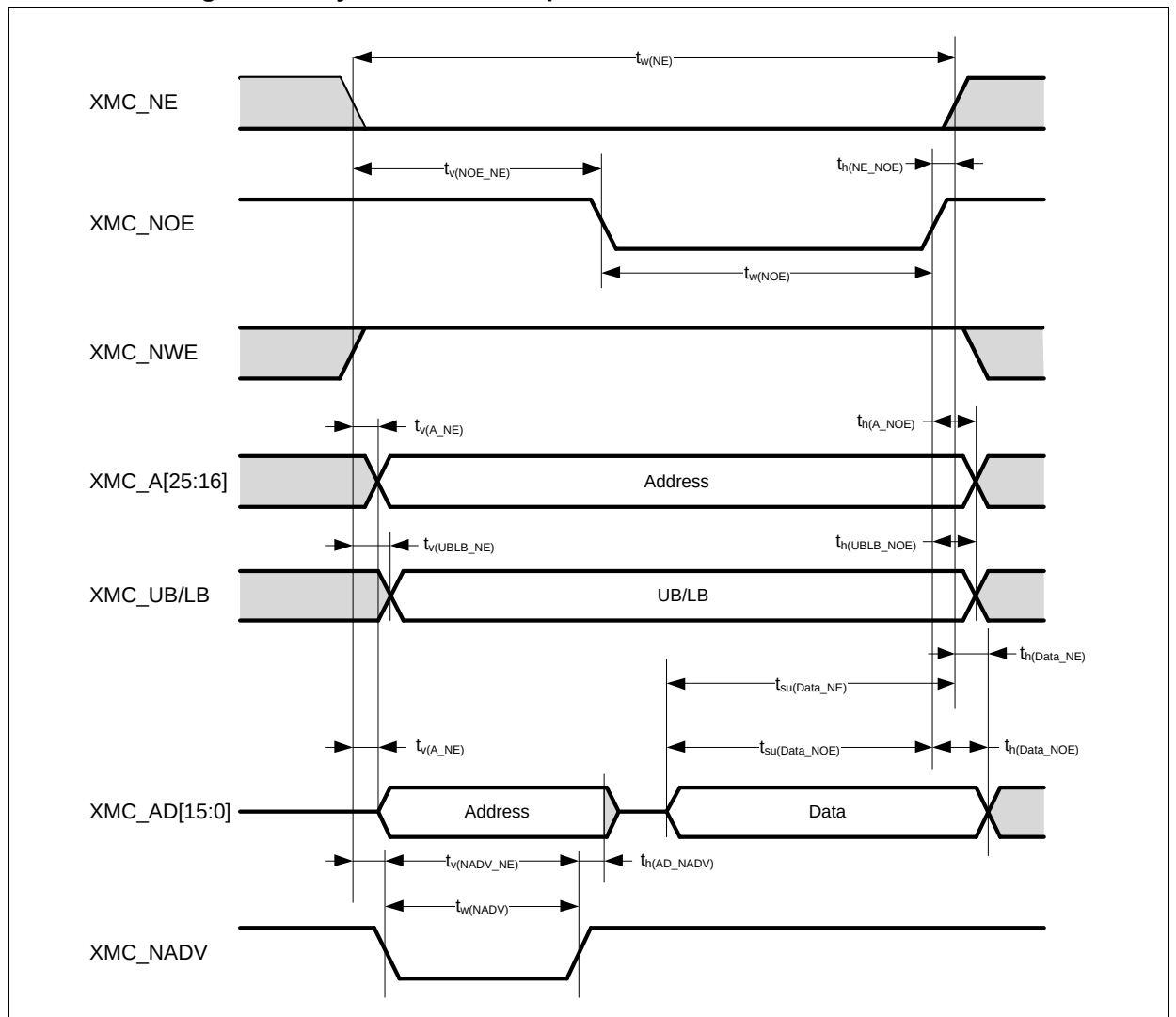
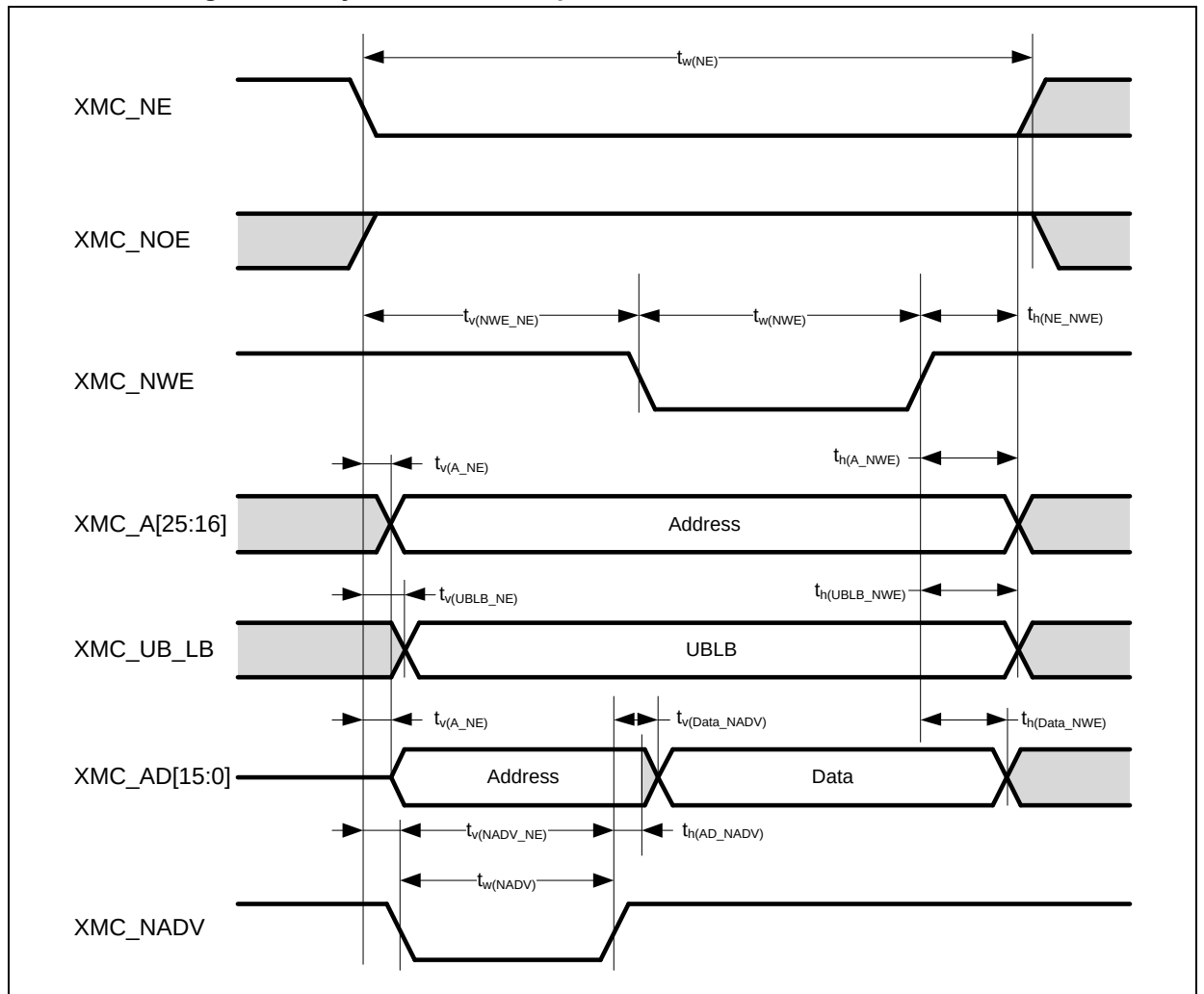


Table 40. Asynchronous multiplexed PSRAM / NOR write timings

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	XMC_NE low time	$5t_{HCLK} - 1$	$5t_{HCLK} + 2$	ns
$t_{v(NWE_NE)}$	XMC_NE low to XMC_NWE low	$2t_{HCLK}$	$2t_{HCLK} + 1$	ns
$t_{w(NWE)}$	XMC_NWE low time	$2t_{HCLK} - 1$	$2t_{HCLK} + 2$	ns
$t_{h(NE_NWE)}$	XMC_NWE high to XMC_NE high hold time	$t_{HCLK} - 1$	-	ns
$t_{v(A_NE)}$	XMC_NE low to XMC_A valid	-	7	ns
$t_{v(NADV_NE)}$	XMC_NE low to XMC_NADV low	3	5	ns
$t_{w(NADV)}$	XMC_NADV low time	$t_{HCLK} - 1$	$t_{HCLK} + 1$	ns
$t_{h(AD_NADV)}$	XMC_AD (address) valid hold time after XMC_NADV high	$t_{HCLK} - 3$	-	ns
$t_{h(A_NWE)}$	Address hold time after XMC_NWE high	$4t_{HCLK} + 2.5$	-	ns
$t_{h(UBLB_NWE)}$	XMC_UB/LB hold time after XMC_NWE high	$t_{HCLK} - 1.5$	-	ns
$t_{v(UBLB_NE)}$	XMC_NE low to XMC_UB/LB valid	-	1.6	ns
$t_{v(Data_NADV)}$	XMC_NADV high to Data valid	-	$t_{HCLK} + 1.5$	ns
$t_{h(Data_NWE)}$	Data hold time after XMC_NWE high	$t_{HCLK} - 5$	-	ns

Figure 19. Asynchronous multiplexed PSRAM / NOR write waveforms



Synchronous waveforms and timings of PSRAM / NOR

The results shown in these tables are obtained with the following XMC configuration:

- BurstAccessMode = XMC_BurstAccessMode_Enable (enable burst transfer mode)
- MemoryType = XMC_MemoryType_CRAM (memory type is CRAM)
- WriteBurst = XMC_WriteBurst_Enable (enable burst write operation)
- CLKPrescale = 1; (memory cycle = 2 HICK cycles) (note: CLKPrescale refers to the CLKPSC bit in XMC_BK1TMGx register. Refer to the AT32A403A reference manual.)
- DataLatency = 1 stands for NOR Flash; DataLatency = 0 for PSRAM (Note: DataLatency refers to the DATLAT bit in XMC_BK1TMGx register. Refer to the AT32A403A reference manual.)

Table 41. Synchronous multiplexed PSRAM / NOR read timings

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	XMC_CLK period	20	-	ns
$t_{d(CLKL-NEL)}$	XMC_CLK low to XMC_NE low	-	1.5	ns
$t_{d(CLKH-NEH)}$	XMC_CLK low to XMC_NE high	1	-	ns
$t_{d(CLKL-NADVL)}$	XMC_CLK low to XMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	XMC_CLK low to XMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	XMC_CLK low to XMC_A valid	-	0	ns
$t_{d(CLKH-AIV)}$	XMC_CLK low to XMC_A invalid	2	-	ns
$t_{d(CLKL-NOEL)}$	XMC_CLK high to XMC_NOE low	-	1	ns
$t_{d(CLKH-NOEH)}$	XMC_CLK low to XMC_NOE high	0.5	-	ns
$t_{d(CLKL-ADV)}$	XMC_CLK low to XMC_AD valid	-	12	ns
$t_{d(CLKL-ADIV)}$	XMC_CLK low to XMC_AD invalid	0	-	ns
$t_{su(ADV-CLKH)}$	XMC_AD valid data before XMC_CLK high	6	-	ns
$t_h(CLKH-ADV)$	XMC_AD valid data after XMC_CLK high	6	-	ns
$t_{su(NWAITV-CLKH)}$	XMC_NWAIT valid before XMC_CLK high	8	-	ns
$t_h(CLKH-NWAITV)$	XMC_NWAIT valid after XMC_CLK high	6	-	ns

Figure 20. Synchronous multiplexed PSRAM / NOR read timings

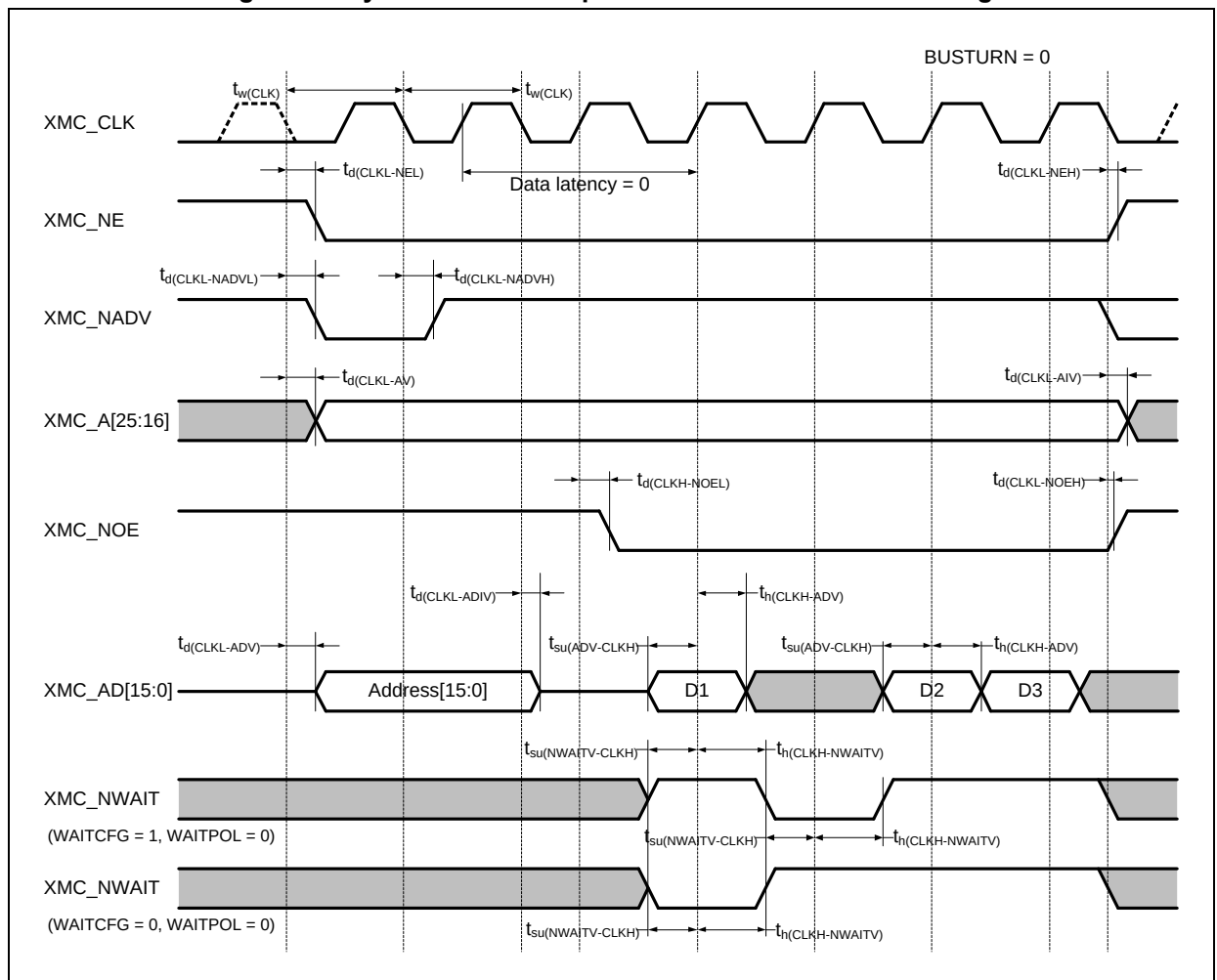
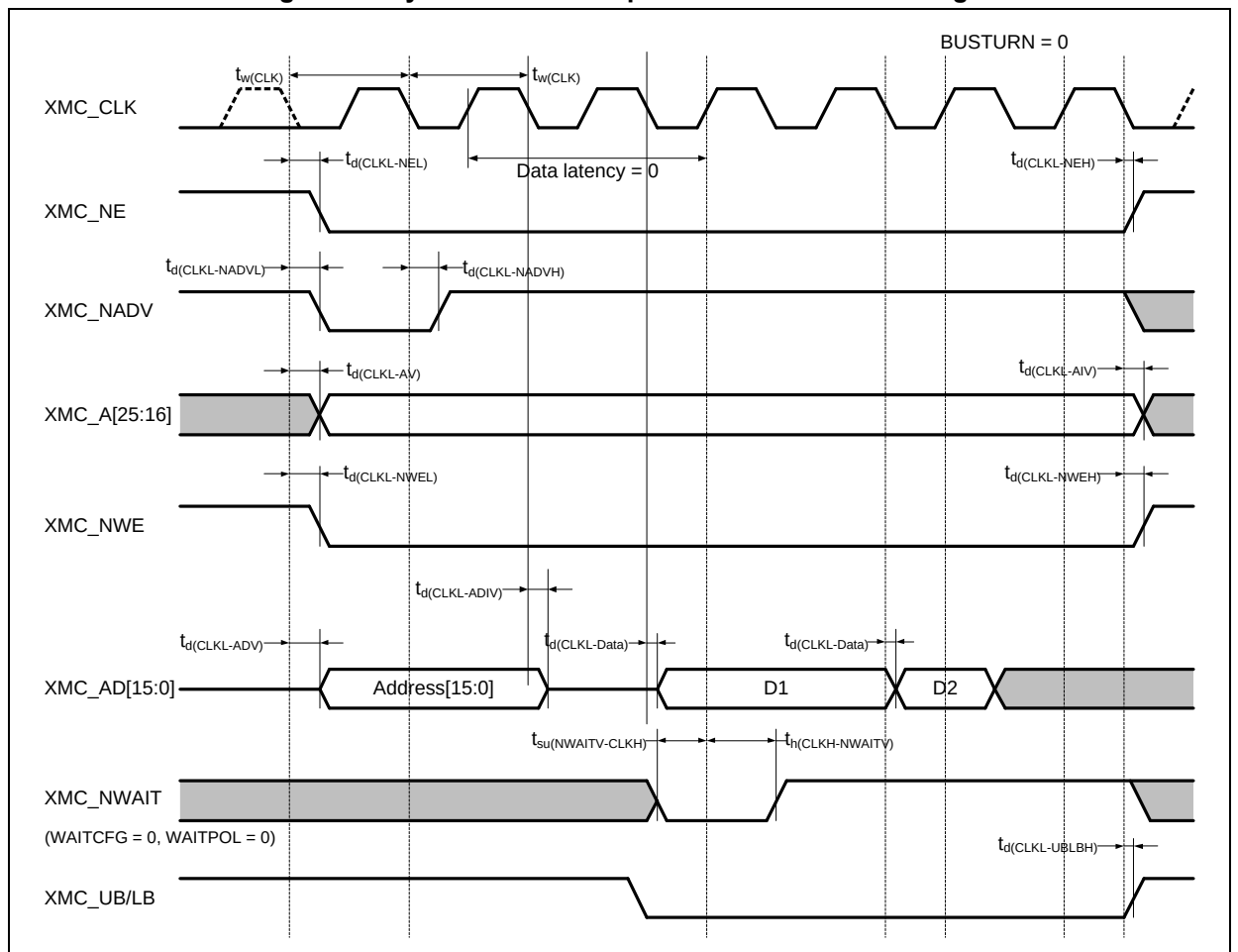


Table 42. Synchronous multiplexed PSRAM write timings

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	XMC_CLK period	20	-	ns
$t_{d(CLKL-NEL)}$	XMC_CLK low to XMC_NE low	-	2	ns
$t_{d(CLKH-NEH)}$	XMC_CLK low to XMC_NE high	2	-	ns
$t_{d(CLKL-NADV)}$	XMC_CLK low to XMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	XMC_CLK low to XMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	XMC_CLK low to XMC_A valid	-	0	ns
$t_{d(CLKH-AIV)}$	XMC_CLK low to XMC_A invalid	2	-	ns
$t_{d(CLKL-NWEL)}$	XMC_CLK low to XMC_NWE low	-	1	ns
$t_{d(CLKH-NWEH)}$	XMC_CLK low to XMC_NWE high	0.5	-	ns
$t_{d(CLKL-ADV)}$	XMC_CLK low to XMC_AD valid	-	12	ns
$t_{d(CLKL-ADIV)}$	XMC_CLK low to XMC_AD invalid	3	-	ns
$t_{d(CLKL-Data)}$	XMC_AD valid after XMC_CLK low	-	6	ns
$t_{d(CLKL-UBLBH)}$	XMC_CLK low to XMC_UB/LB high	1	-	ns
$t_{su(NWAITV-CLKH)}$	XMC_NWAIT valid before XMC_CLK high	7	-	ns
$t_h(CLKH-NWAITV)$	XMC_NWAIT valid after XMC_CLK high	2	-	ns

Figure 21. Synchronous multiplexed PSRAM write timings



NAND controller waveforms and timings

The results shown in this table are obtained with the following XMC configuration:

- COM.XMC_SetupTime = 0x01; (Note: STP in XMC_BK2TMGMEM)
- COM.XMC_WaitSetupTime = 0x03; (Note: OP in XMC_BK2TMGMEM)
- COM.XMC_HoldSetupTime = 0x02; (Note: HLD in XMC_BK2TMGMEM)
- COM.XMC_HiZSetupTime = 0x01; (Note: WRSTP in XMC_BK2TMGMEM)
- ATT.XMC_SetupTime = 0x01; (Note: STP in XMC_BK2TMGATT)
- ATT.XMC_WaitSetupTime = 0x03; (Note: OP in XMC_BK2TMGATT)
- ATT.XMC_HoldSetupTime = 0x02; (Note: HLD in XMC_BK2TMGATT)
- ATT.XMC_HiZSetupTime = 0x01; (Note: WRSTP in XMC_BK2TMGATT)
- Bank = XMC_Bank_NAND;
- MemoryDataWidth = XMC_MemoryDataWidth_16b; (Note: Memory data width = 16 bits)
- ECC = XMC_ECC_Enable; (Note: enable ECC calculation)
- ECCPageSize = XMC_ECCPageSize_512Bytes; (Note: ECC page size = 512 Bytes)
- DLYCRSetupTime = 0; (Note: DLYCR in XMC_BK2CTRL)
- DLYARSetupTime = 0; (Note: DLYAR in XMC_BK2CTRL)

Table 43. NAND Flash read and write timings

Symbol	Parameter	Min	Max	Unit
$t_{w(NOE)}$	XMC_NWE low width	$4T_{HCLK} - 1.5$	$4T_{HCLK} + 1.5$	ns
$t_{su(D-NOE)}$	XMC_D valid data before XMC_NOE high	25	-	ns
$t_{h(NOE-D)}$	XMC_D valid data after XMC_NOE high	14	-	ns
$t_{d(ALE-NOE)}$	XMC_ALE valid before XMC_NOE low	-	$3T_{HCLK} + 2$	ns
$t_{h(NOE-ALE)}$	XMC_NOE high to XMC_ALE invalid	$3T_{HCLK} + 4.5$	-	ns
$t_{w(NWE)}$	XMC_NWE low width	$4T_{HCLK} - 1$	$4T_{HCLK} + 2.5$	ns
$t_{v(NWE-D)}$	XMC_NWE low to XMC_D valid	-	0	ns
$t_{h(NWE-D)}$	XMC_NWE high to XMC_D invalid	$10T_{HCLK} + 4$	-	ns
$t_{d(D-NWE)}$	XMC_D valid before XMC_NWE high	$6T_{HCLK} + 12$	-	ns
$t_{d(ALE-NWE)}$	XMC_ALE valid before XMC_NWE low	-	$3T_{HCLK} + 1.5$	ns
$t_{h(NWE-ALE)}$	XMC_NWE high to XMC_ALE invalid	$3T_{HCLK} + 4.5$	-	ns

Figure 22. NAND controller read waveforms

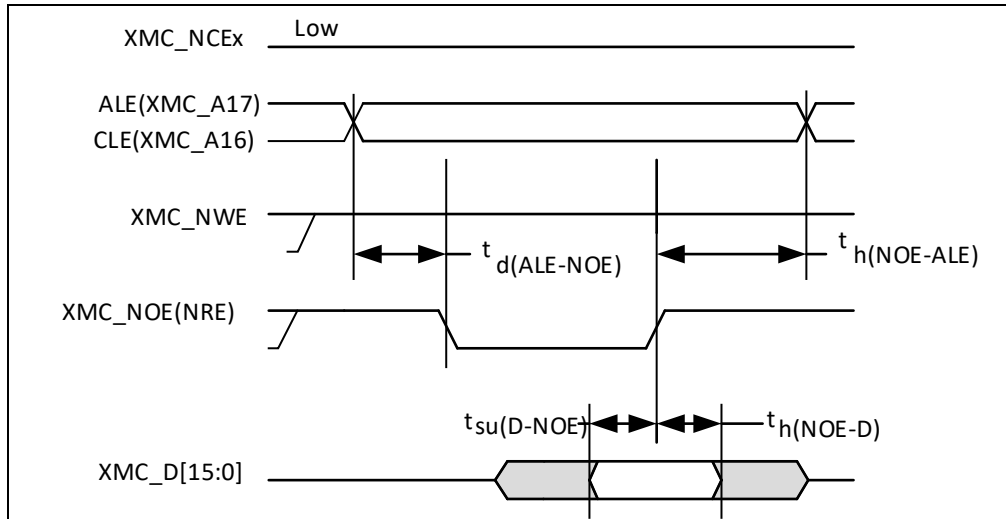


Figure 23. NAND controller write waveforms

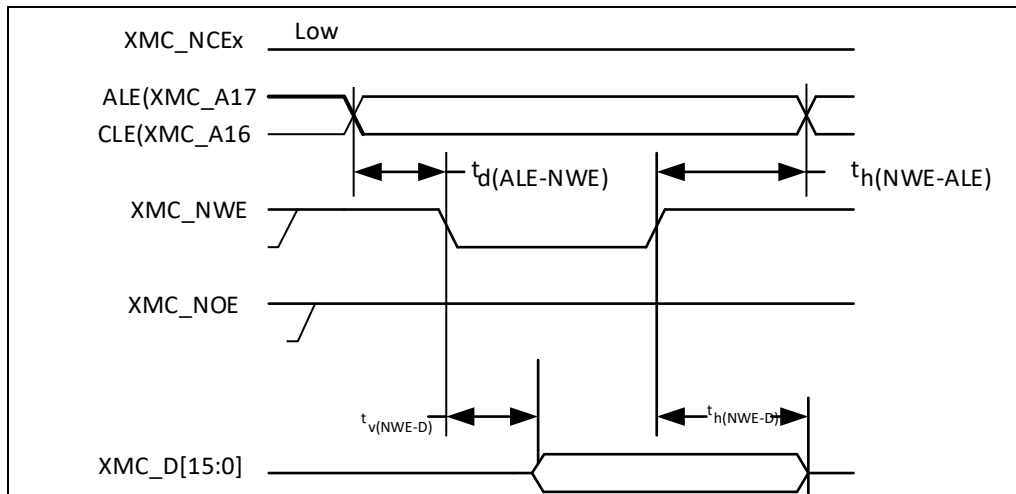


Figure 24. NAND controller common memory read waveforms

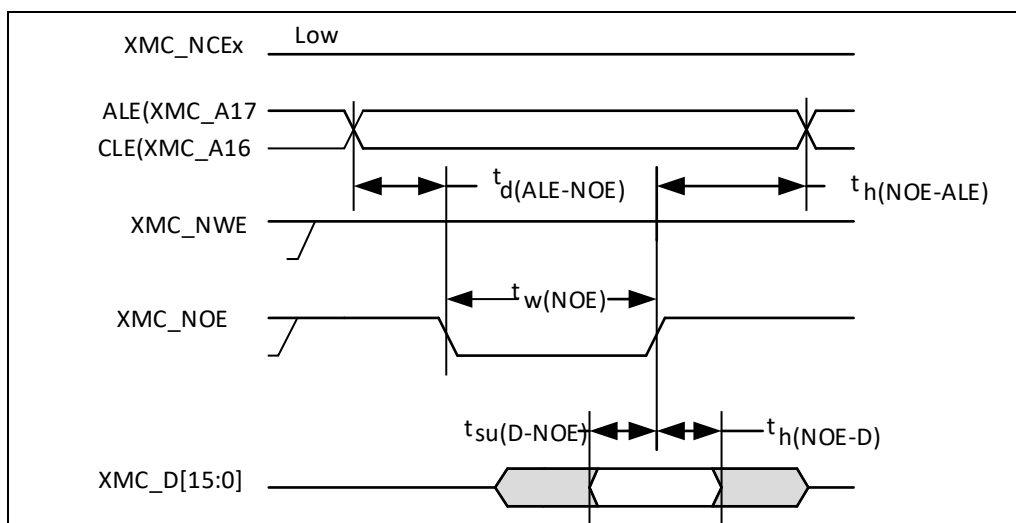
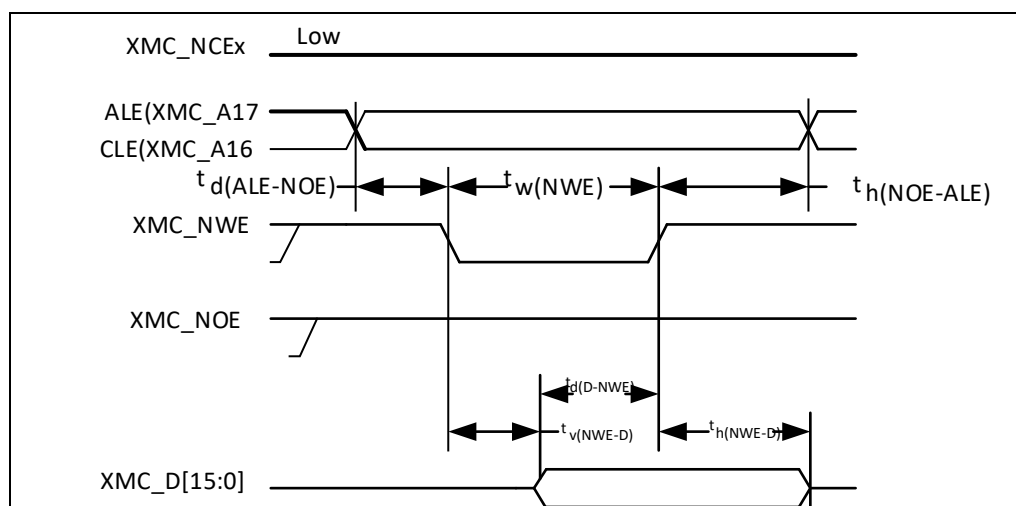


Figure 25. NAND controller for common memory write waveforms



5.3.14 TMR timer characteristics

The parameters given in the table below are guaranteed by design.

Table 44. TMR characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{\text{res(TMR)}}$	Timer resolution time	-	1	-	t_{TMRxCLK}
		$f_{\text{TMRxCLK}} = 200 \text{ MHz}$	5	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{\text{TMRxCLK}}/2$	MHz
				50	MHz

5.3.15 SPI characteristics

Table 45. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $(1/t_{c(SCK)})^{(1)}$	SPI clock frequency ⁽²⁾⁽³⁾	$V_{DD} = 3.3\text{ V}, T_A = 25\text{ }^{\circ}\text{C}$	-	50	MHz
		$V_{DD} = 3.3\text{ V}, T_A = 105\text{ }^{\circ}\text{C}$	-	36	
		$V_{DD} = 2.6\text{ V}, T_A = 105\text{ }^{\circ}\text{C}$	-	30	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: $C = 30\text{ pF}$	-	8	ns
$t_{su(CS)}^{(1)}$	CS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(CS)}^{(1)}$	CS hold time	Slave mode	$2t_{PCLK}$	-	ns
$t_{w(SCKH)}^{(1)}$ $t_{w(SCKL)}^{(1)}$	SCK high and low time	Master mode, prescaler = 4	$2t_{PCLK} - 3$	$2t_{PCLK} + 3$	ns
$t_{su(MI)}^{(1)}$	Data input setup time	Master mode	6	-	ns
$t_{su(SI)}^{(1)}$		Slave mode	5	-	
$t_{h(MI)}^{(1)}$	Data input setup time	Master mode	4	-	ns
$t_{h(SI)}^{(1)}$		Slave mode	5	-	
$t_{a(SO)}^{(1)(4)}$	Data output access time	Slave mode	$t_{PCLK} - 2$	$2t_{PCLK} + 2$	ns
$t_{dis(SO)}^{(1)(5)}$	Data output disable time	Slave mode	$t_{PCLK} - 2$	$2t_{PCLK} + 2$	ns
$t_{v(SO)}^{(1)}$	Data output valid time	Slave mode (after enable edge)	-	25	ns
$t_{v(MO)}^{(1)}$	Data output valid time	Master mode (after enable edge)	-	10	ns
$t_{h(SO)}^{(1)}$	Data output hold time	Slave mode (after enable edge)	9	-	ns
$t_{h(MO)}^{(1)}$		Master mode (after enable edge)	2	-	

(1) Guaranteed by design, not tested in production.

(2) The maximum SPI clock frequency should not exceed $f_{PCLK}/2$.

(3) The maximum SPI clock frequency is highly related with devices and the PCB layout. For more details about the complete solution, please contact your local Artery sales representative.

(4) Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.

(5) Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

Figure 26. SPI timing diagram - slave mode and CPHA = 0

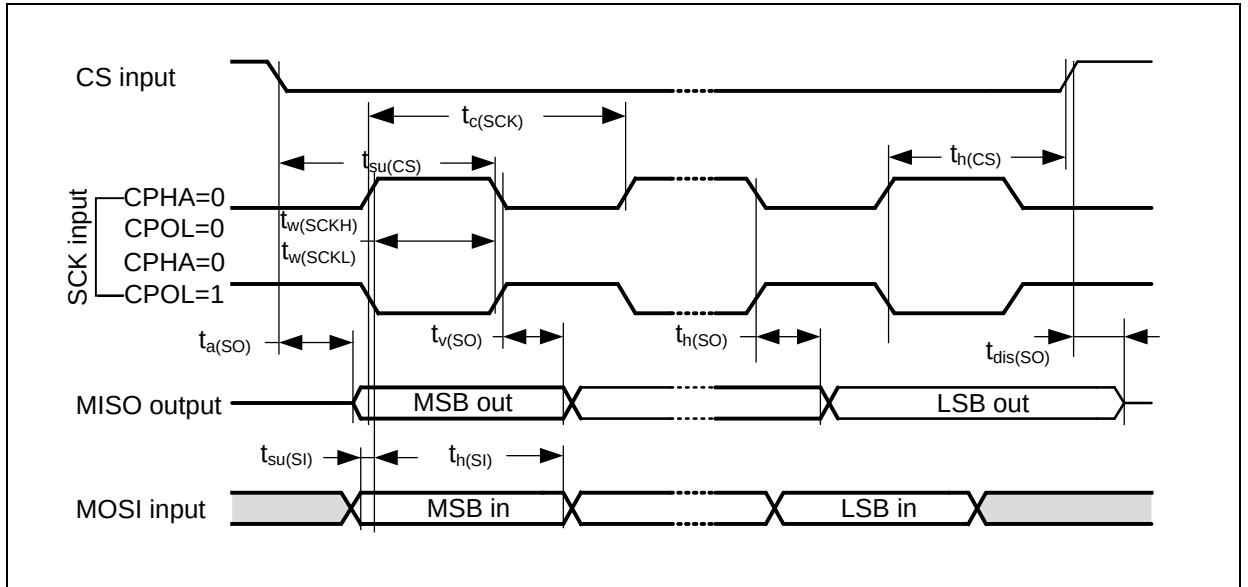


Figure 27. SPI timing diagram - slave mode and CPHA = 1

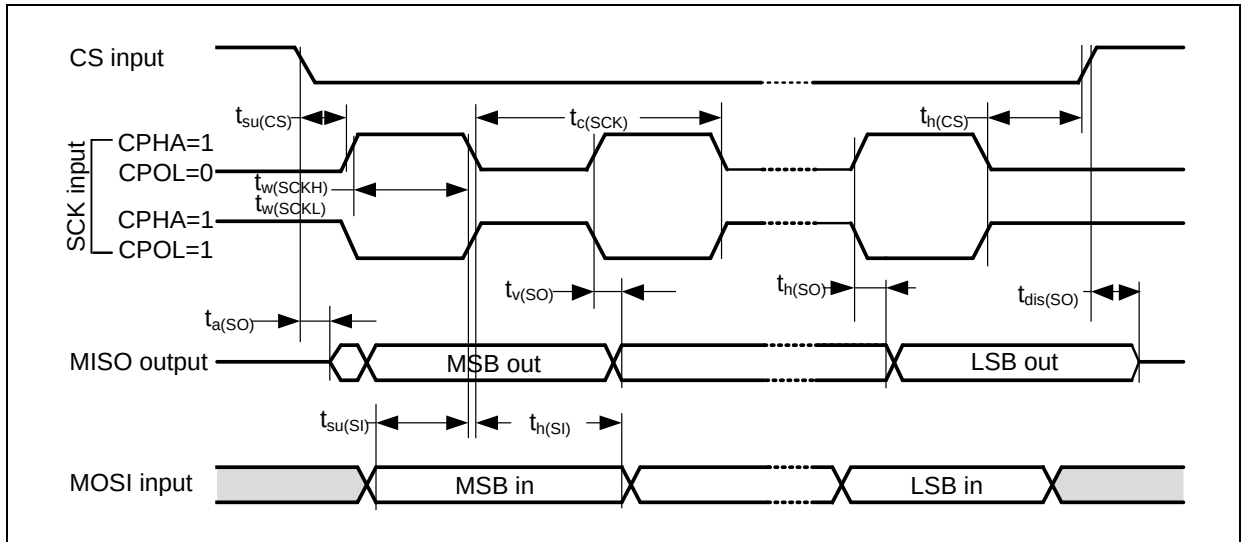
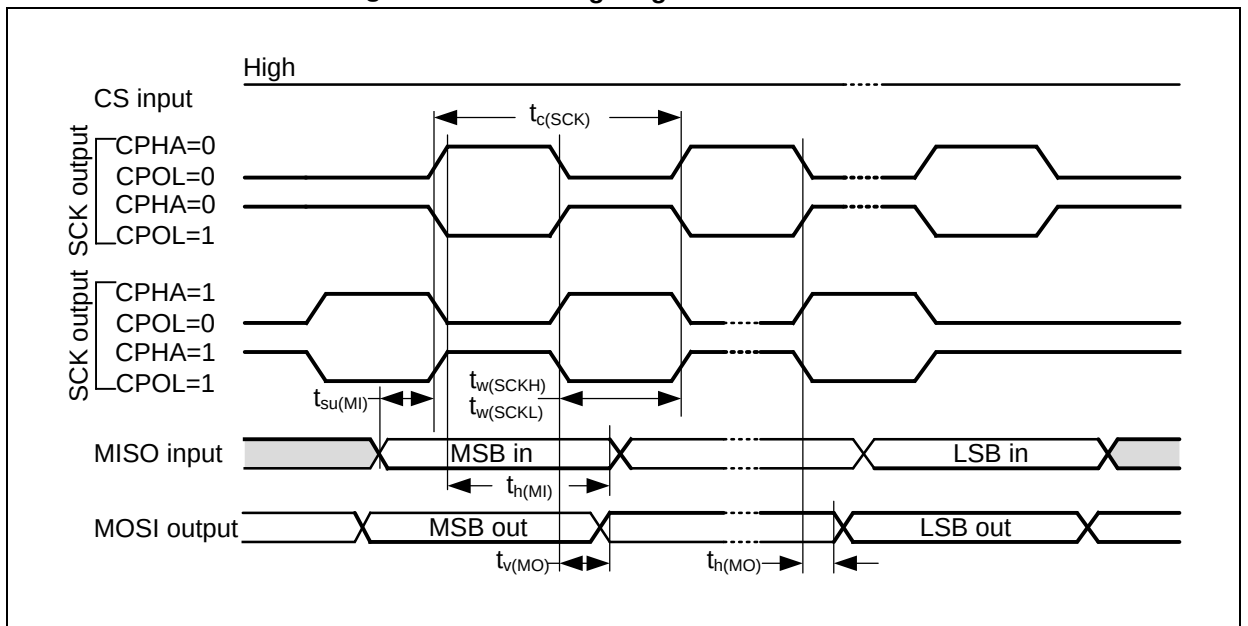


Figure 28. SPI timing diagram - master mode



5.3.16 I²S characteristics

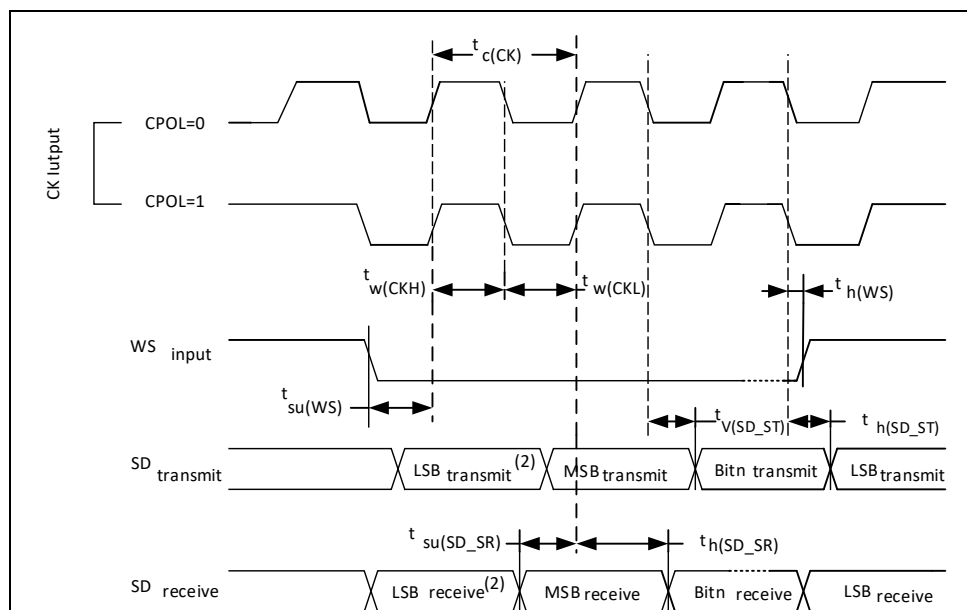
Table 46. I²S characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{r(CK)}$ $t_{f(CK)}$	I ² S clock rise and fall time	Capacitive load: C = 15 pF	-	12	ns
$t_{v(WS)}^{(1)}$	WS valid time	Master mode	0	4	
$t_{h(WS)}^{(1)}$	WS hold time	Master mode	0	4	
$t_{su(WS)}^{(1)}$	WS setup time	Slave mode	9	-	
$t_{h(WS)}^{(1)}$	WS hold time	Slave mode	0	-	
$t_{su(SD_MR)}^{(1)}$	Data input setup time	Master receiver	6	-	
$t_{su(SD_SR)}^{(1)}$		Slave receiver	2	-	
$t_{h(SD_MR)}^{(1)(2)}$	Data input hold time	Master receiver	0.5	-	
$t_{h(SD_SR)}^{(1)(2)}$		Slave receiver	0.5	-	
$t_{v(SD_ST)}^{(1)(2)}$	Data output valid time	Slave transmitter (after enable edge)	-	20	
$t_{h(SD_ST)}^{(1)}$	Data output hold time	Slave transmitter (after enable edge)	9	-	
$t_{v(SD_MT)}^{(1)(2)}$	Data output valid time	Master transmitter (after enable edge)	-	15	
$t_{h(SD_MT)}^{(1)}$	Data output hold time	Master transmitter (after enable edge)	0	-	

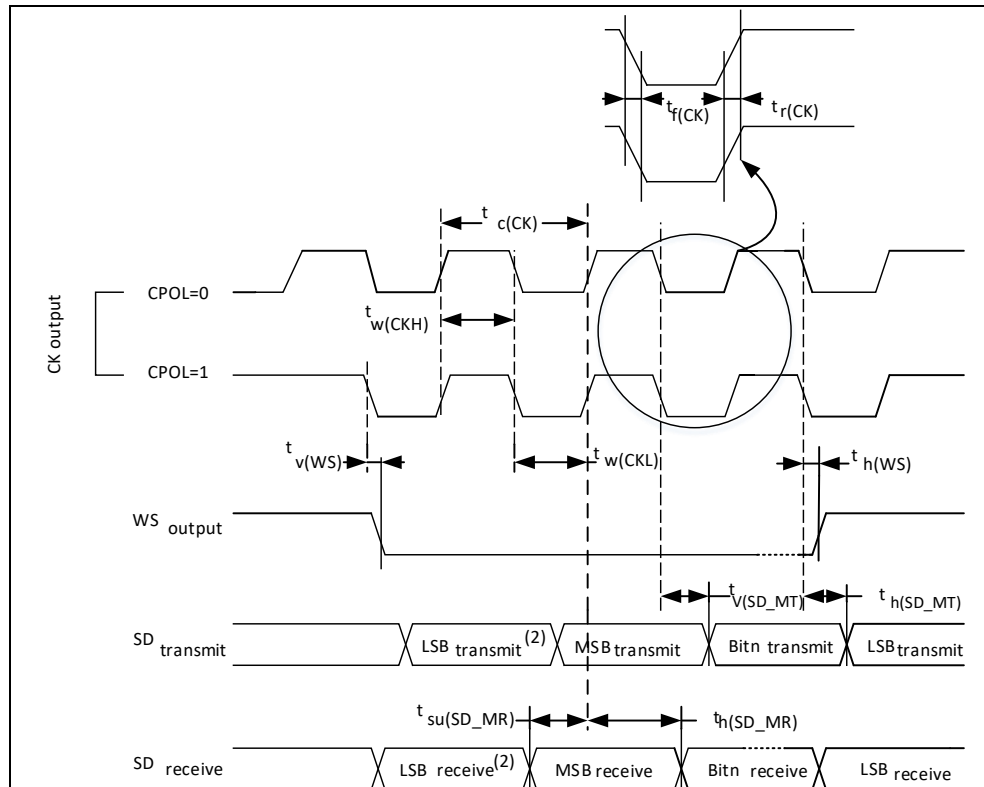
(1) Guaranteed by design, not tested in production.

(2) Depends on f_{PCLK} . For example, if $f_{PCLK}=8$ MHz, then $T_{PCLK} = 1/f_{PCLK} = 125$ ns.

Figure 29. I²S slave timing diagram (Philips protocol)



(1) LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 30. I²S master timing diagram (Philips protocol)

(1) LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

5.3.17 I²C characteristics

GPIO pins SDA and SCL have limitation as follows: they are not "true" open-drain. When configured as open-drain, the PMOS connected between the GPIO pin and V_{DD} is disabled, but is still present.

I²C bus interface can support standard mode (max. 100 kHz) and fast mode (max. 400 kHz). The I²C bus frequency can be increased up to 1 MHz. For more complete information, please contact your local Artery sales office for technical support.

5.3.18 SDIO characteristics

Figure 31. SDIO high-speed mode

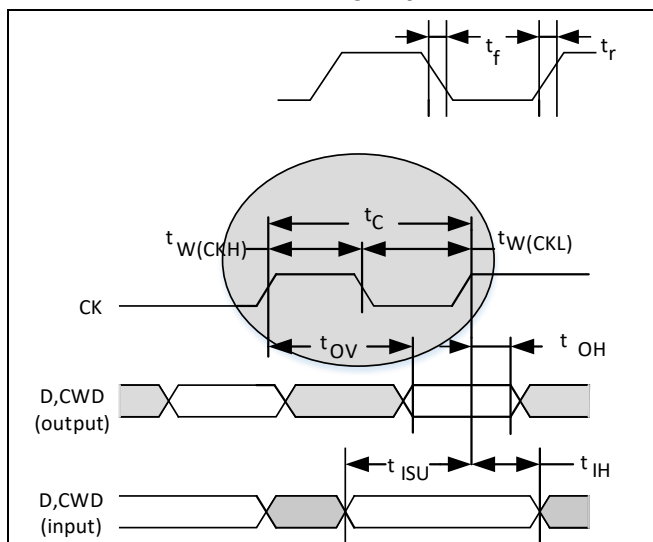


Figure 32. SD default mode

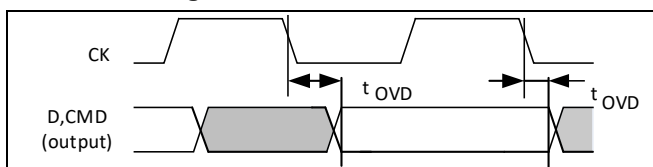


Table 47. SD / MMC characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f _{PP}	Clock frequency in data transfer mode	-	0	48	MHz
t _{W(CKL)}	Clock low time	-	32	-	ns
t _{W(CKH)}	Clock high time	-	30	-	
t _r	Clock rise time	-	-	4	
t _f	Clock fall time	-	-	5	
CMD, D inputs (referenced to CK)					
t _{ISU}	Input setup time	-	2	-	ns
t _{IH}	Input hold time	-	0	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode					
t _{OV}	Output valid time	-	-	6	ns
t _{OH}	Output hold time	-	0	-	
CMD, D outputs (referenced to CK) in SD default mode ⁽¹⁾					
t _{OVD}	Output valid default time	-	-	7	ns
t _{OHD}	Output hold default time	-	0.5	-	

(1) Refer to SDIO_CLKCTRL, the SDIO clock control register to control the CK output.

5.3.19 USBFS characteristics

Table 48. USBFS startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USBFS transceiver startup time	1	μs

(1) Guaranteed by design, not tested in production.

Table 49. USBFS DC electrical characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
Input levels	V_{DD}	USBFS operating voltage	-	3.0 ⁽²⁾	3.6	V
	$V_{\text{DI}}^{(3)}$	Differential input sensitivity	I (USBFS_D+, USBFS_D-)	0.2	-	V
	$V_{\text{CM}}^{(3)}$	Differential common mode range	Includes V_{DI} range	0.8	2.5	
	$V_{\text{SE}}^{(3)}$	Single ended receiver threshold	-	1.3	2.0	
Output levels	V_{OL}	Static output level low	R_{L} of 1.24 k Ω to 3.6 V ⁽⁴⁾	-	0.3	V
	V_{OH}	Static output level high	R_{L} of 15 k Ω to $V_{\text{SS}}^{(4)}$	2.8	3.6	
R_{PU}	USBFS_D+ internal pull-up	$V_{\text{IN}} = V_{\text{SS}}$	0.97	1.24	1.58	k Ω

(1) All the voltages are measured from the local ground potential.

(2) The AT32A403A USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7 to 3.0 V V_{DD} voltage range.

(3) Guaranteed by design, not tested in production.

(4) R_{L} is the load connected on the USB drivers.

Figure 33. USBFS timings: definition of data signal rise and fall time

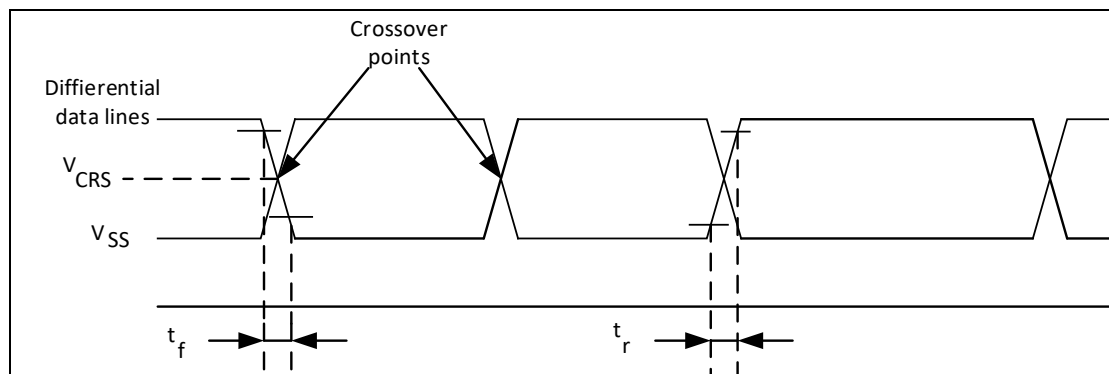


Table 50. USBFS electrical characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Max ⁽¹⁾	Unit
t_{r}	Rise time ⁽²⁾	$C_{\text{L}} \leq 50 \text{ pF}$	4	20	ns
t_{f}	Fall Time ⁽²⁾	$C_{\text{L}} \leq 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/fall time matching	$t_{\text{r}}/t_{\text{f}}$	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

(1) Guaranteed by design, not tested in production.

(2) Measured from 10% to 90% of the data signal. For more detailed information, please refer to USB Specification - Chapter 7 (version 2.0).

5.3.20 EMAC characteristics

Operating voltage

Table 51. EMAC DC electrical characteristics

Symbol	Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
V _{DD}	EMAC operating voltage	3.0	3.6	V

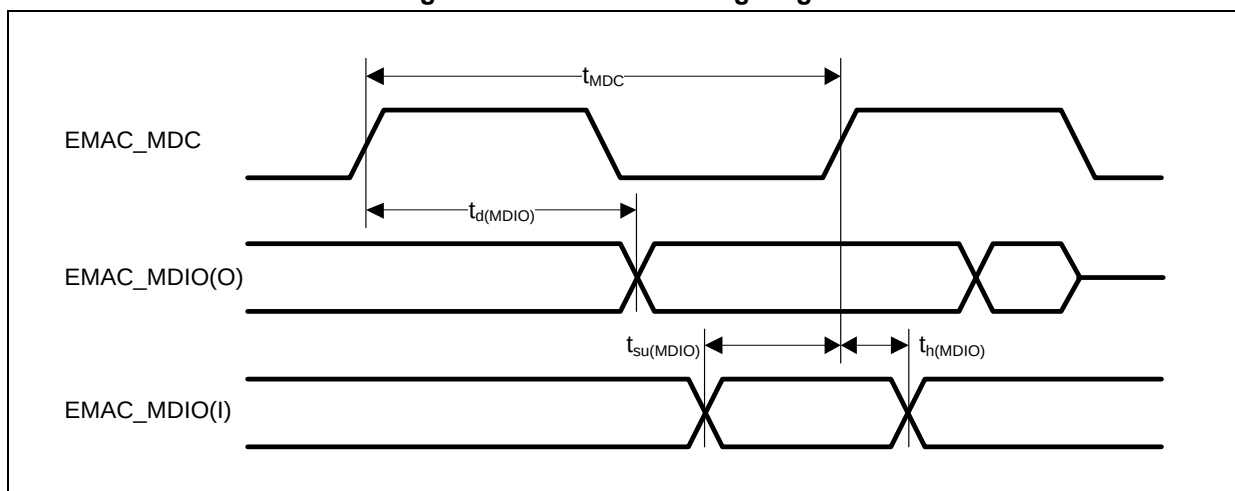
(1) All the voltages are measured from the local ground potential.

SMI (station management interface)

Table 52. Dynamic characteristics: EMAC signals for SMI

Symbol	Parameter	Min	Typ	Max	Unit
t _{MDC}	MDC cycle time (1.96 MHz, f _{AHB} = 200 MHz)	509	510	511	ns
t _{d(MDIO)}	MDIO write data valid time	13.5	14.5	15.5	
t _{su(MDIO)}	Read data setup time	35	-	-	
t _{h(MDIO)}	Read data hold time	0	-	-	

Figure 34. EMAC SMI timing diagram

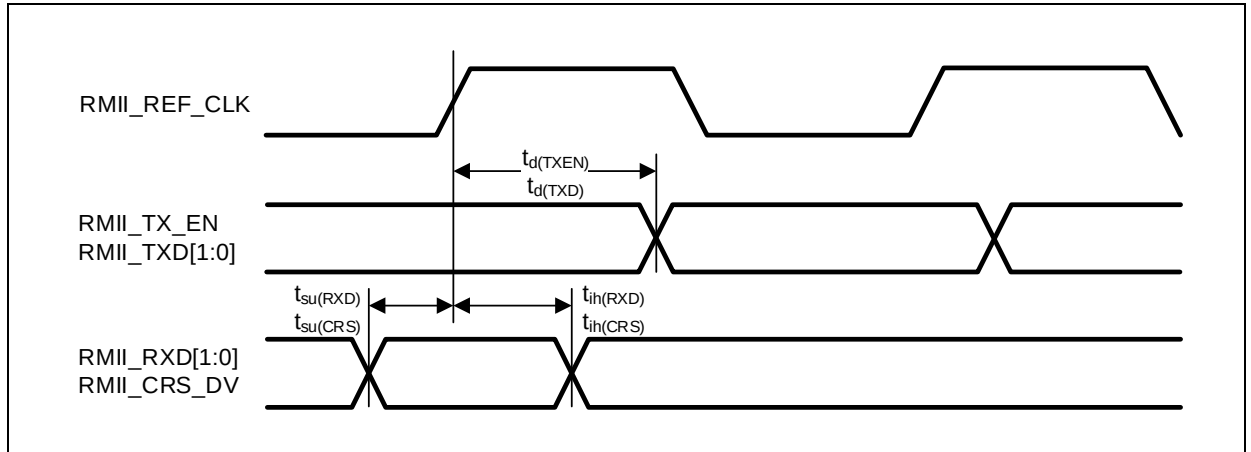


RMI

Table 53. Dynamic characteristics: EMAC signals for RMII

Symbol	Parameter	Min	Typ	Max	Unit
t _{su(RXD)}	Receive data setup time	4	-	-	ns
t _{h(RXD)}	Receive data hold time	2	-	-	
t _{su(DV)}	Carrier sense set-up time	4	-	-	
t _{h(DV)}	Carrier sense hold time	2	-	-	
t _{d(TXEN)}	Transmit enable valid delay time	8	10	16	
t _{d(TXD)}	Transmit data valid delay time	7	10	16	

Figure 35. EMAC RMII timing diagram

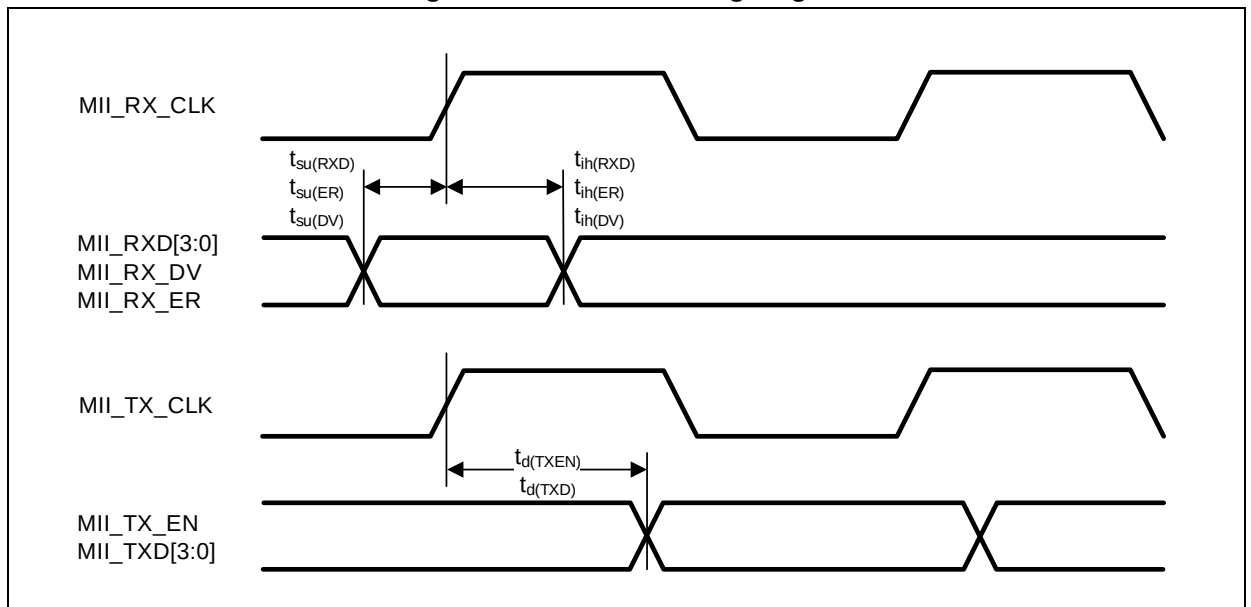


MII

Table 54. Dynamic characteristics: EMAC signals for MII

Symbol	Parameter	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	10	-	-	ns
$t_{ih}(RXD)$	Receive data hold time	10	-	-	
$t_{su}(DV)$	Data valid setup time	10	-	-	
$t_{ih}(DV)$	Data valid hold time	10	-	-	
$t_{su}(ER)$	Error setup time	10	-	-	
$t_{ih}(ER)$	Error hold time	10	-	-	
$t_d(TXEN)$	Transmit enable valid delay time	14	16	18	
$t_d(TXD)$	Transmit data valid delay time	13	16	20	

Figure 36. EMAC MII timing diagram



5.3.21 12-bit ADC characteristics

Unless otherwise specified, the parameters given in the table below are preliminary values derived from tests performed under ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in [Table 13](#).

Note: It is recommended to perform a calibration after each power-up.

Table 55. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	2.6	-	3.6	V
V_{REF+}	Positive reference voltage ⁽³⁾	-	2.0	-	V_{DDA}	V
I_{DDA}	Current on the V_{DDA} input pin	-	-	380 ⁽¹⁾	445	μA
I_{VREF}	Current on the V_{REF} input pin ⁽³⁾	-	-	200 ⁽¹⁾	220	μA
f_{ADC}	ADC clock frequency	-	0.6	-	28	MHz
$f_s^{(2)}$	Sampling rate	-	0.05	-	2	MHz
$f_{TRIG}^{(2)}$	External trigger frequency	$f_{ADC} = 28 \text{ MHz}$	-	-	1.65	MHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range ⁽³⁾	-	0 (V_{SSA} or V_{REF-} internally connected to ground)	-	V_{REF+}	V
$R_{AIN}^{(2)}$	External input impedance	-	See Table 56 and Table 57 for details			Ω
$C_{ADC}^{(2)}$	Internal sample and hold capacitor	-	-	10	-	pF
$t_{CAL}^{(2)}$	Calibration time	$f_{ADC} = 28 \text{ MHz}$	6.61			μs
		-	185			$1/f_{ADC}$
$t_{lat}^{(2)}$	Injection trigger conversion latency	$f_{ADC} = 28 \text{ MHz}$	-	-	107	ns
		-	-	-	3 ⁽⁴⁾	$1/f_{ADC}$
$t_{latr}^{(2)}$	Regular trigger conversion latency	$f_{ADC} = 28 \text{ MHz}$	-	-	71.4	ns
		-	-	-	2 ⁽⁴⁾	$1/f_{ADC}$
$t_s^{(2)}$	Sampling time	$f_{ADC} = 28 \text{ MHz}$	0.053	-	8.55	μs
		-	1.5	-	239.5	$1/f_{ADC}$
$t_{STAB}^{(2)}$	Power-up time	-	42			$1/f_{ADC}$
$t_{CONV}^{(2)}$	Total conversion time (including sampling time)	$f_{ADC} = 28 \text{ MHz}$	0.5	-	9	μs
		-	14 to 252 (t_s for sampling + 12.5 for successive approximation)			$1/f_{ADC}$

(1) Guaranteed by characterization results, not tested in production.

(2) Guaranteed by design, not tested in production.

(3) V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA} , depending on the package.

(4) For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in [Table 55](#).

[Table 56](#) and [Table 57](#) are used to determine the maximum external impedance allowed for an error below 1/4 of LSB.

Table 56. R_{AIN} max for $f_{ADC} = 14$ MHz

T_s (Cycle)	t_s (μs)	R_{AIN} max (k Ω) ⁽¹⁾
1.5	0.11	0.25
7.5	0.54	1.3
13.5	0.96	2.5
28.5	2.04	5.0
41.5	2.96	8.0
55.5	3.96	10.5
71.5	5.11	13.5
239.5	17.11	40

(1) Guaranteed by design.

Table 57. R_{AIN} max for $f_{ADC} = 28$ MHz

T_s (Cycle)	t_s (μs)	R_{AIN} max (k Ω) ⁽¹⁾
1.5	0.05	0.1
7.5	0.27	0.6
13.5	0.48	1.2
28.5	1.02	2.5
41.5	1.48	4.0
55.5	1.98	5.2
71.5	2.55	7.0
239.5	8.55	20

(1) Guaranteed by design.

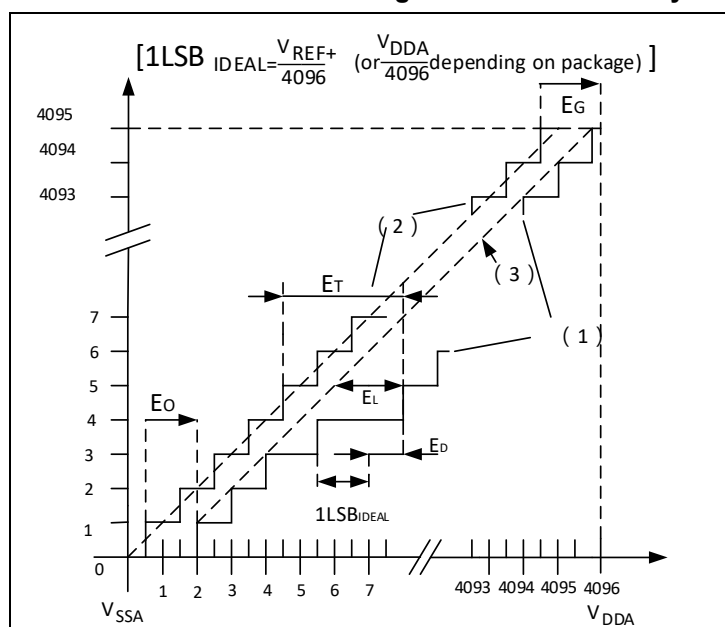
Table 58. ADC accuracy^{(1) (2)}

Symbol	Parameter	Test Conditions	Typ ⁽²⁾	Max ⁽²⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 28 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$, $V_{DDA} = 3.0 \text{ to } 3.6 \text{ V}$, $T_A = 25 \text{ }^\circ\text{C}$ $V_{REF+} = V_{DDA}$	± 1.5	± 2.5	LSB
EO	Offset error		$+0.5$	± 1.5	
EG	Gain error		$+1$	$+2/-0.5$	
ED	Differential linearity error		± 0.6	± 0.9	
EL	Integral linearity error		± 0.8	± 1.5	
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 28 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$, $V_{DDA} = 2.6 \text{ to } 3.6 \text{ V}$, $T_A = -40 \sim 105 \text{ }^\circ\text{C}$	± 2	± 4	LSB
EO	Offset error		$+0.5$	± 2	
EG	Gain error		$+1$	$+2.5/-1.5$	
ED	Differential linearity error		± 0.6	± 1.2	
EL	Integral linearity error		± 1	± 2	

(1) ADC DC accuracy values are measured after internal calibration.

(2) Guaranteed by characterization results, not tested in production.

Figure 37. ADC accuracy characteristics



(1) Example of an actual transfer curve.

(2) Ideal transfer curve.

(3) End point correlation line.

(4) ET = Maximum deviation between the actual and the ideal transfer curves.

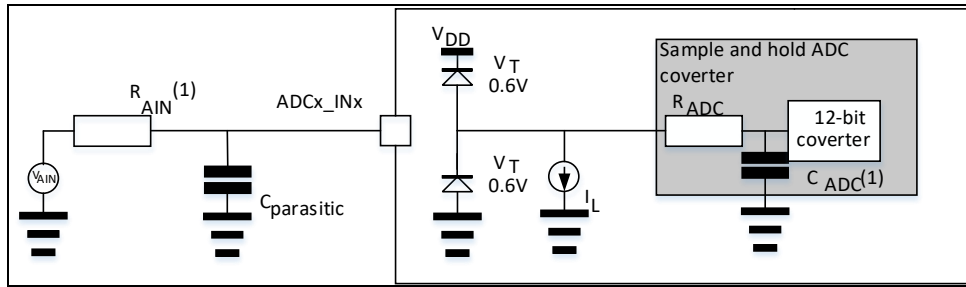
EO = Deviation between the first actual transition and the first ideal one.

EG = Deviation between the last ideal transition and the last actual one.

ED = Maximum deviation between actual steps and the ideal one.

EL = Maximum deviation between any actual transition and the end point correlation line.

Figure 38. Typical connection diagram using the ADC



- (1) Refer to [Table 55](#) for the values of R_{AIN} and C_{ADC} .
- (2) $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

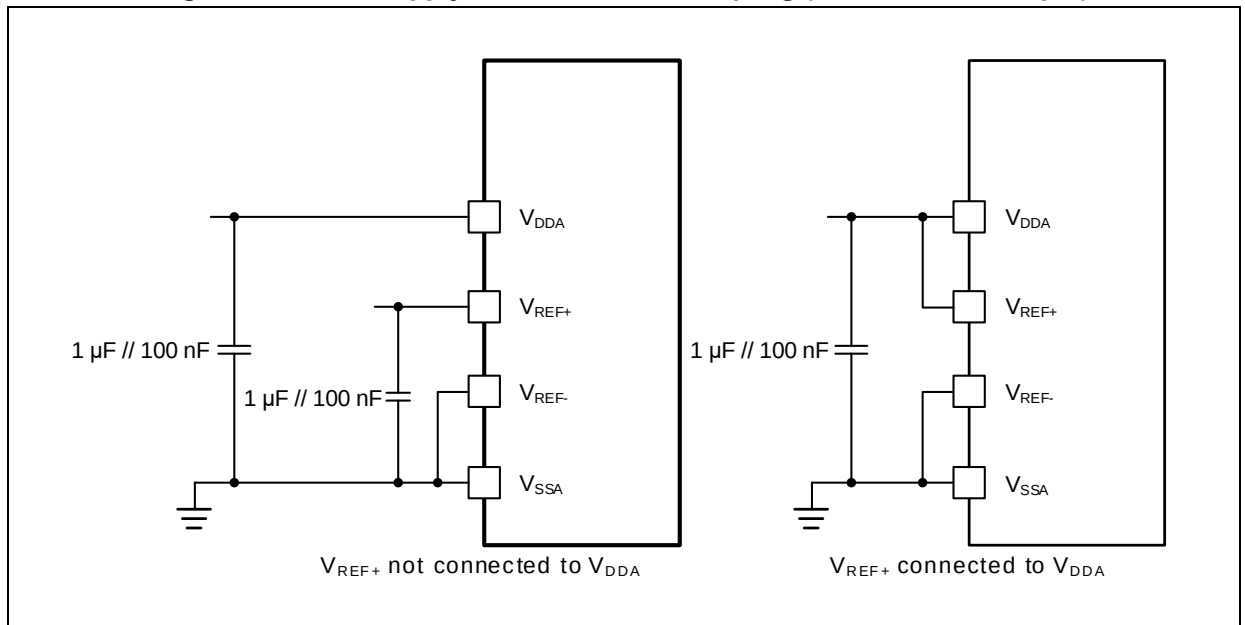
General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 39](#) or [Figure 40](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 100 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

If HEXT is enabled while using any input channel of ADC123_IN10~13, follow PCB layout guide line below to isolate the high frequency interference from HEXT emitting to ADC input signals nearby.

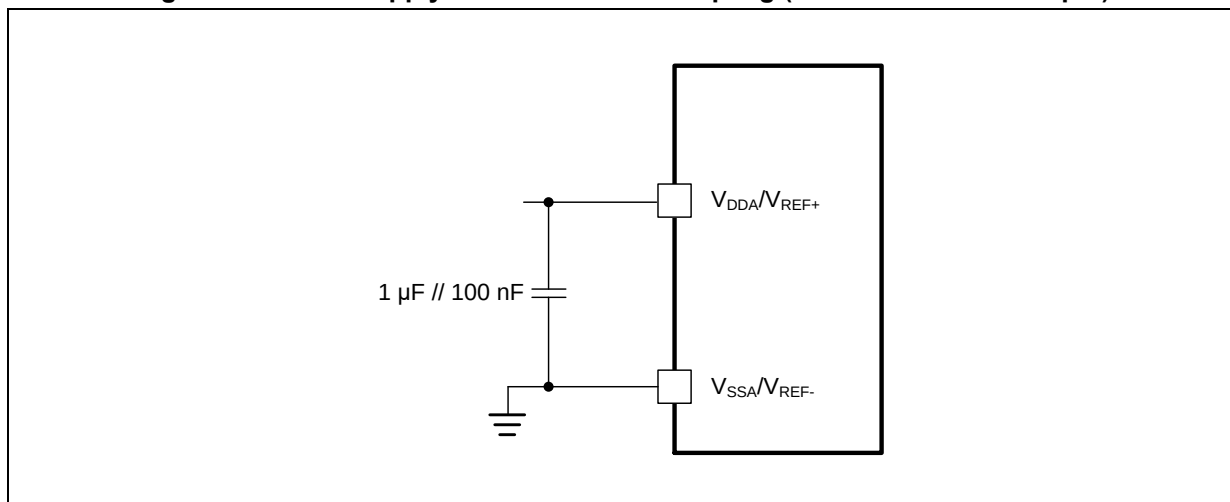
- Use different PCB layers to route ADC_IN signal apart from HEXT path
- Do not route ADC_IN signals and HEXT path parallel

Figure 39. Power supply and reference decoupling (with external V_{REF} pin)



- (1) V_{REF} input is available only on 100-pin package and above.

Figure 40. Power supply and reference decoupling (without external V_{REF} pin)



(1) V_{REF} input is available only on 100-pin package and above.

5.3.22 Internal reference voltage (V_{INTRV}) characteristics

Table 59. Internal reference voltage characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{INTRV}^{(1)}$	Internal reference voltage	-	1.16	1.20	1.24	V
$T_{Coeff}^{(1)}$	Temperature coefficient	-	-	-	120	ppm/°C
$T_{S_VINTRV}^{(2)}$	ADC sampling time when reading the internal reference voltage	-	5.1	-	-	μs

(1) Guaranteed by characterization results, not tested in production.

(2) Guaranteed by design, not tested in production.

5.3.23 Temperature sensor (V_{TS}) characteristics

Table 60. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{TS} linearity with temperature	-	±2	±4	°C
$Avg_Slope^{(1)(2)}$	Average slope	-4.11	-4.26	-4.41	mV/°C
$V_{25}^{(1)(2)}$	Voltage at 25 °C	1.19	1.28	1.37	V
$t_{START}^{(3)}$	Startup time	-	-	100	μs
$T_{S_temp}^{(3)}$	ADC sampling time when reading the temperature	5.1	-	-	μs

(1) Guaranteed by characterization results, not tested in production.

(2) The temperature sensor output voltage changes linearly with temperature. The offset of this line varies from chip to chip due to process variation (up to 50 °C from one chip to another). The internal temperature sensor is more suited to applications that detect temperature variations instead of absolute temperatures. If accurate temperature readings are needed, an external temperature sensor part should be used.

(3) Guaranteed by design, not tested in production.

Obtain the temperature using the following formula:

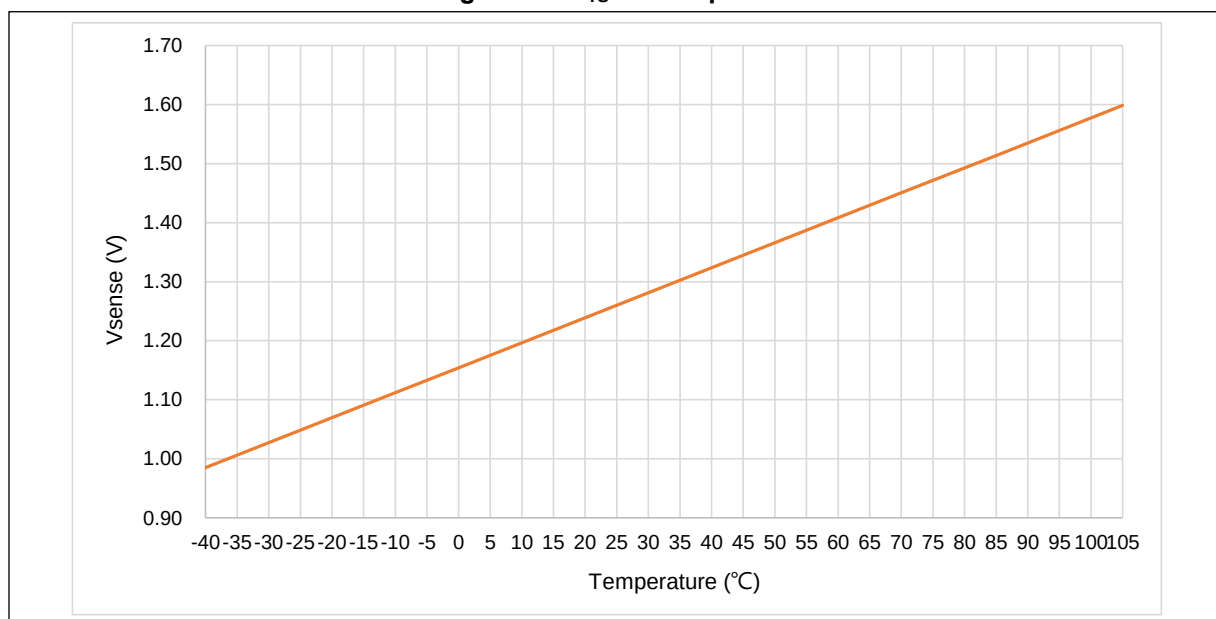
$$\text{Temperature (in } ^\circ\text{C)} = \{(V_{25} - V_{TS}) / Avg_Slope\} + 25.$$

Where,

$V_{25} = V_{TS}$ value for 25° C and

Avg_Slope = Average Slope for curve between Temperature vs. V_{SENSE} (given in mV/° C).

Figure 41. V_{TS} vs. temperature



5.3.24 12-bit DAC specifications

Table 61. DAC characteristics

Symbol	Parameter	Comments	Min	Typ	Max	Unit
V _{DDA}	Analog supply voltage	-	2.6	-	3.6	V
V _{REF+} ⁽³⁾	Reference supply voltage	-	2.0	-	3.6	V
V _{SSA}	Ground	-	0	-	0	V
R _{LOAD} ⁽¹⁾	Resistive load with buffer ON	-	5	-	-	kΩ
R _O ⁽²⁾	Impedance output with buffer OFF	-	-	13.2	16	kΩ
C _{LOAD} ⁽¹⁾	Capacitive load	-	-	-	50	pF
DAC_OUT ⁽¹⁾	Lower DAC_OUT voltage with buffer ON	-	0.15	-	-	V
	Higher DAC_OUT voltage with buffer ON	-	-	-	V _{REF+} - 0.2	V
	Lower DAC_OUT voltage with buffer OFF	-	-	0.5	3.5	mV
	Higher DAC_OUT voltage with buffer OFF	-	-	-	V _{REF+} - 1.5 mV	V
I _{DDA}	DC current consumption in quiescent mode	With no load, V _{REF+} = 3.6 V	-	480	625	μA
I _{VREF} ⁽³⁾	DC current consumption in quiescent mode	With no load, V _{REF+} = 3.6 V	-	330	340	μA
DNL ⁽²⁾	Differential non linearity	-	-	±0.4	±0.8	LSB
INL ⁽²⁾	Integral non linearity (difference between measured value and a line drawn between DAC_OUT min and DAC_OUT max)	-	-	±0.8	±1.5	LSB
Offset ⁽²⁾	Offset error (difference between measured value at Code (0x800) and the ideal value = V _{REF+} /2)	-	-	15	30	mV
			-	20	35	LSB
Gain error ⁽²⁾	Gain error	-	-	0.1	0.25	%
t _{SETTLING}	Settling time	C _{LOAD} ≤ 50 pF, R _{LOAD} ≥ 5 kΩ	-	1	4	μs
Update rate	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1 LSB)	C _{LOAD} ≤ 50 pF, R _{LOAD} ≥ 5 kΩ	-	-	1	MSPS
t _{WAKEUP}	Wakeup time from off state (setting the EN bit in the DAC Control register)	C _{LOAD} ≤ 50 pF, R _{LOAD} ≥ 5 kΩ	-	1.2	4	μs

(1) Guaranteed by design, not tested in production.

(2) Guaranteed by characterization results, not tested in production.

(3) V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package.

6 Package information

6.1 LQFP100 package information

Figure 42. LQFP100 – 14 x 14 mm 100 pin low-profile quad flat package outline

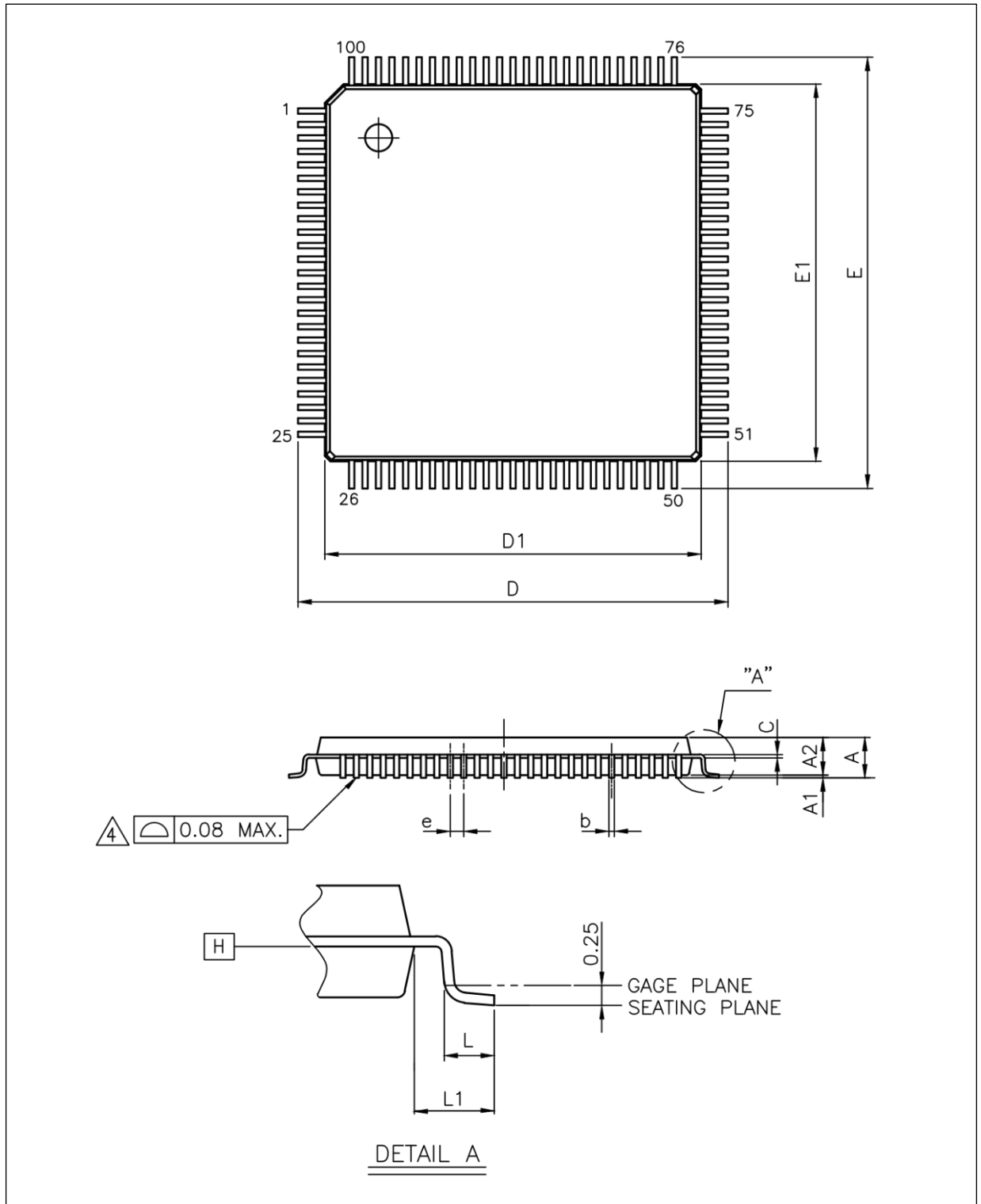


Table 62. LQFP100 – 14 x 14 mm 100 pin low-profile quad flat package mechanical data

Symbol	Millimeters		
	Min	Typ	Max
A	-	-	1.60
A1	0.05	-	0.15
A2	1.35	1.40	1.45
b	0.17	0.20	0.26
c	0.10	0.127	0.20
D	15.75	16.00	16.25
D1	13.90	14.00	14.10
E	15.75	16.00	16.25
E1	13.90	14.00	14.10
e	0.50 BSC.		
L	0.45	0.60	0.75
L1	1.00 REF.		

6.2 LQFP64 package information

Figure 43. LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline

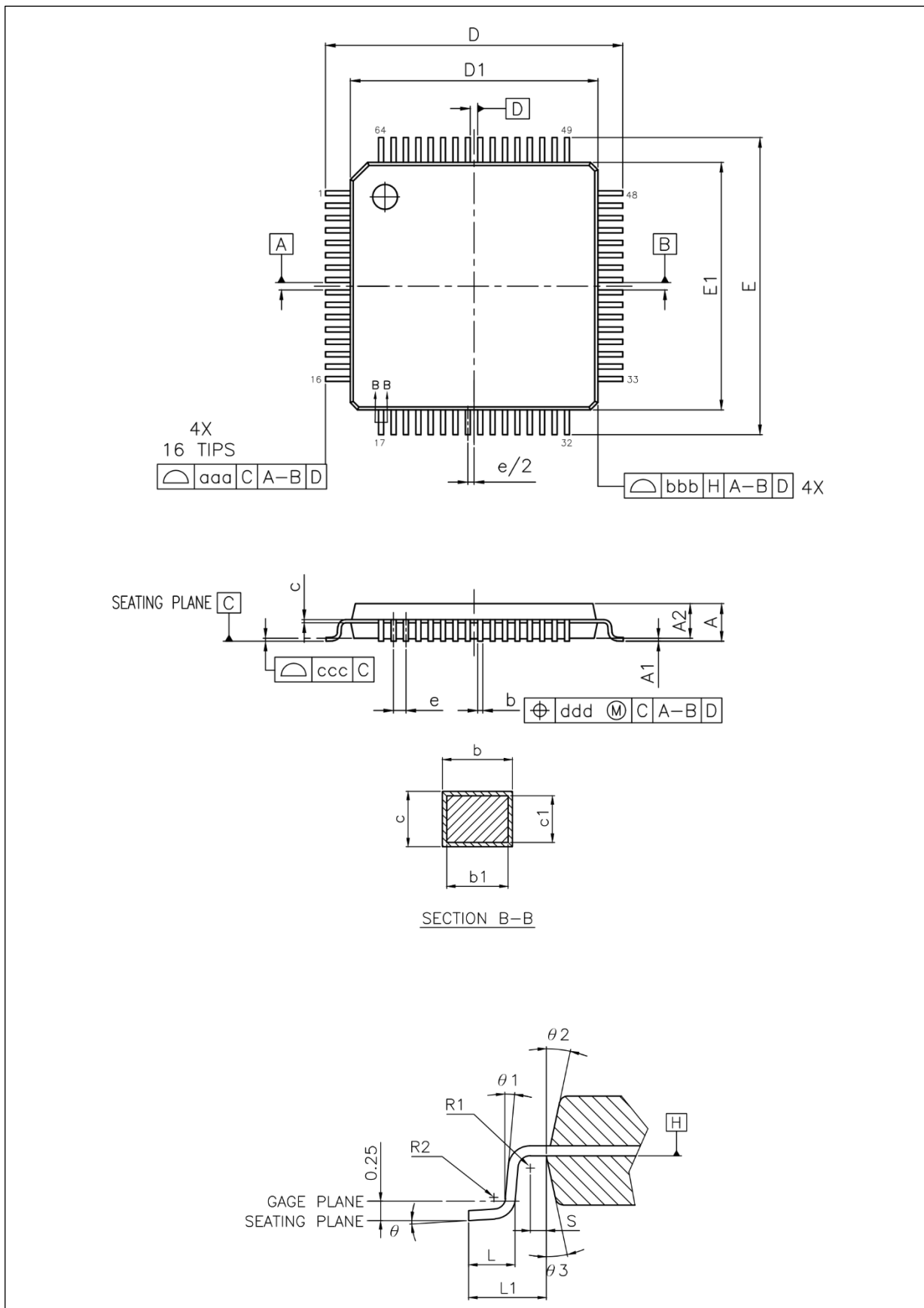


Table 63. LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package mechanical data

Symbol	millimeters		
	Min	Typ	Max
A	-	-	1.60
A1	0.05	-	0.15
A2	1.35	1.40	1.45
b	0.17	0.20	0.27
c	0.09	-	0.20
D	11.75	12.00	12.25
D1	9.90	10.00	10.10
E	11.75	12.00	12.25
E1	9.90	10.00	10.10
e	0.50 BSC.		
Θ	3.5° REF.		
L	0.45	0.60	0.75
L1	1.00 REF.		
ccc	0.08		

6.3 LQFP48 package information

Figure 44. LQFP48 – 7 x 7 mm 48 pin low-profile quad flat package outline

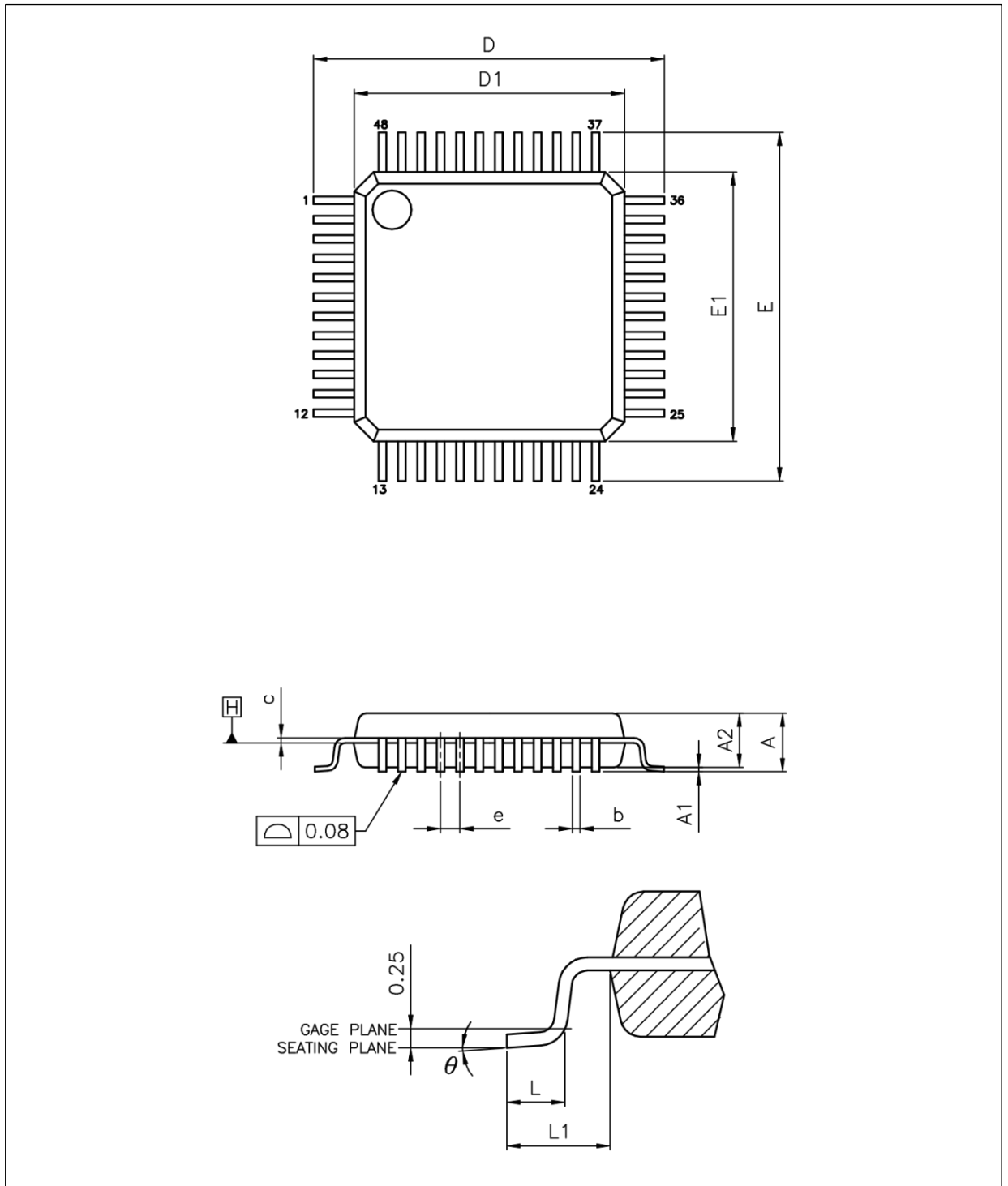


Table 64. LQFP48 – 7 x 7 mm 48 pin low-profile quad flat package mechanical data

Symbol	millimeters		
	Min	Typ	Max
A	-	-	1.60
A1	0.05	-	0.15
A2	1.35	1.40	1.45
b	0.17	0.22	0.27
c	0.09	-	0.20
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
E	8.80	9.00	9.20
E1	6.90	7.00	7.10
e	0.50 BSC.		
Θ	0°	3.5°	7°
L	0.45	0.60	0.75
L1	1.00 REF.		

6.4 QFN48 package information

Figure 45. QFN48 – 6 x 6 mm 48 pin quad flat no-leads package outline

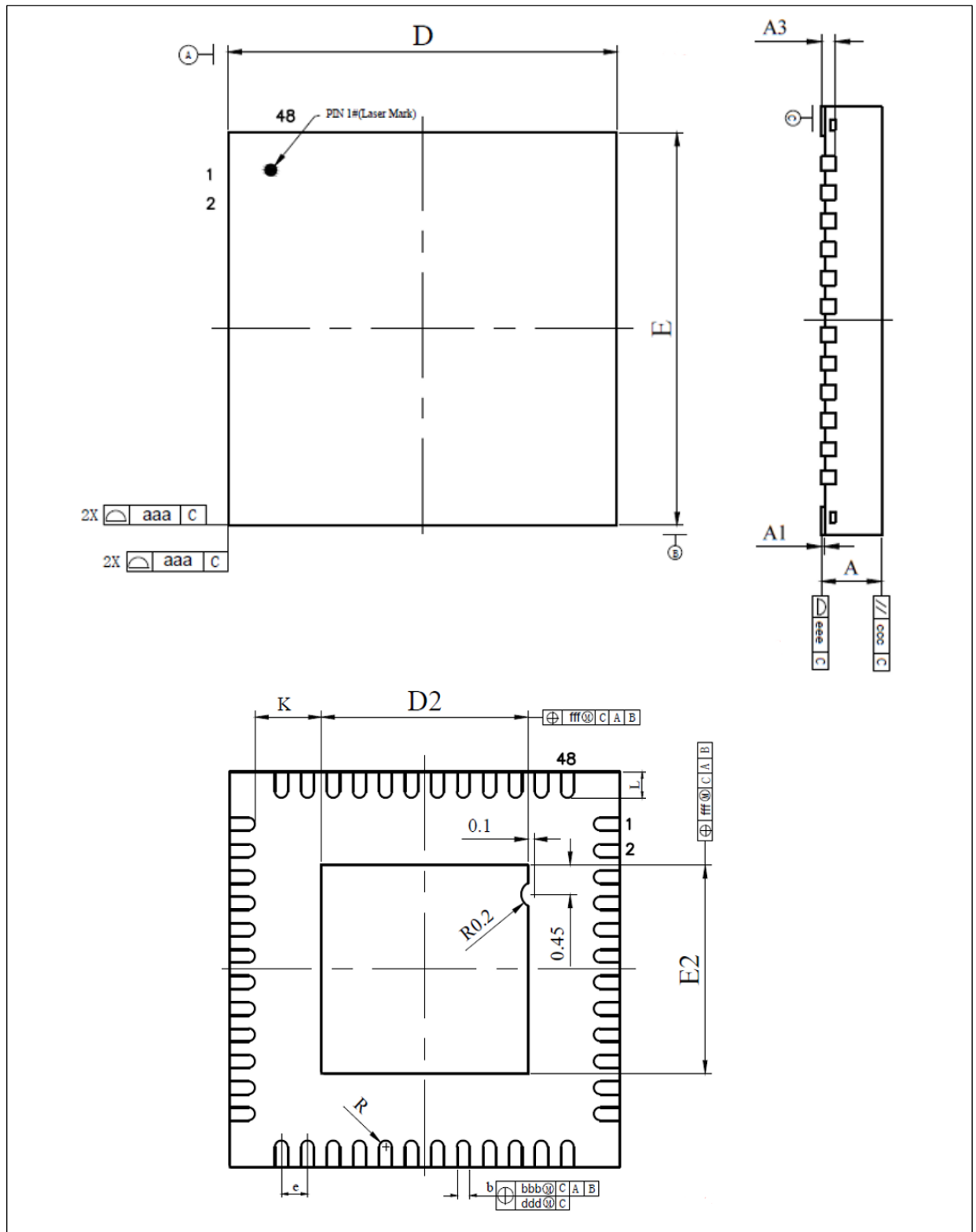
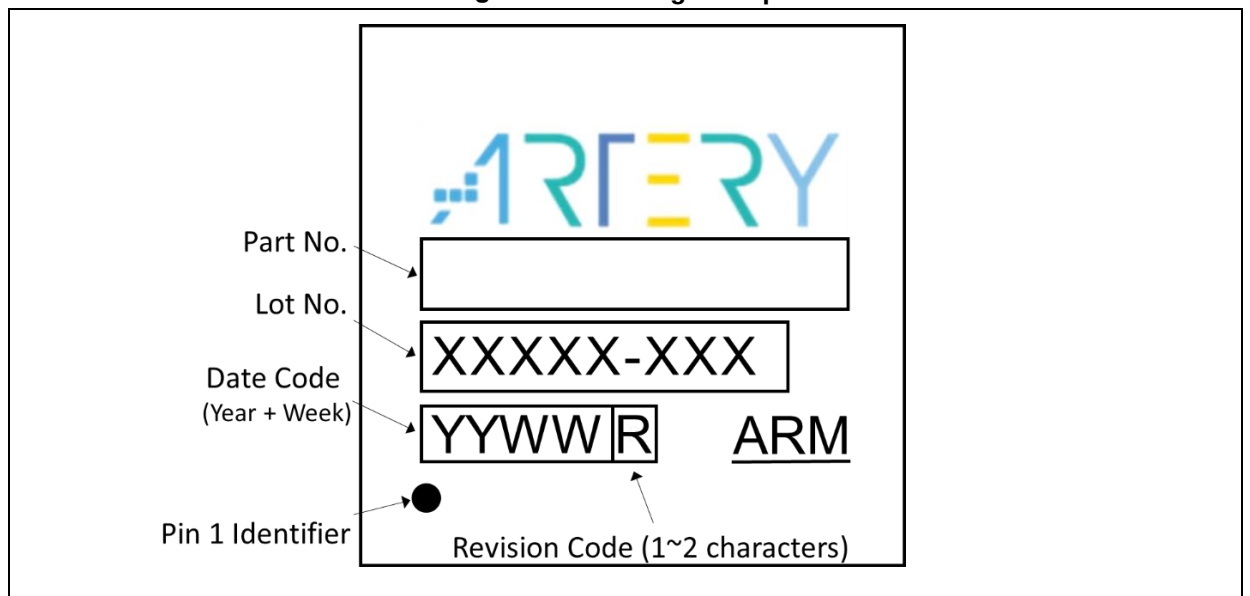


Table 65. QFN48 – 6 x 6 mm 48 pin quad flat no-leads package mechanical data

Symbol	millimeters		
	Min	Typ	Max
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
A3	0.203 REF.		
b	0.15	0.20	0.25
D	5.90	6.00	6.10
D2	3.07	3.17	3.27
E	5.90	6.00	6.10
E2	3.07	3.17	3.27
e	0.40 BSC.		
K	0.20	-	-
L	0.35	0.40	0.45

6.5 Device marking

Figure 46. Marking example



(1) Not In Scale.

6.6 Thermal characteristics

Thermal characteristics are calculated based on two-layer board that uses FR-4 material in 1.6mm thickness. They are guaranteed by design, not tested in production.

Table 66. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP100 – 14 × 14 mm/0.5 mm pitch	61.2	°C/W
	Thermal resistance junction-ambient LQFP64 – 10 × 10 mm/0.5 mm pitch	64.6	
	Thermal resistance junction-ambient LQFP48 – 7 × 7 mm/0.5 mm pitch	68.8	
	Thermal resistance junction-ambient QFN48 – 6 × 6 mm/0.4 mm pitch	37.8	

7 Part numbering

Table 67. AT32A403A series part numbering

Example:	AT32	A	4	0	3A	V	G	T	7									
Product family																		
AT32 = ARM®-based 32-bit microcontroller																		
Product type																		
A = Certified with AEC Q-100 automotive series																		
Core																		
4 = Cortex®-M4																		
Product series																		
0 = Main Stream																		
Product application																		
3A = CAN + USB + EMAC series advanced version																		
Pin count																		
C = 48 pins																		
R = 64 pins																		
V = 100 pins																		
Internal Flash memory size																		
C = 256 KBytes of the internal Flash memory																		
E = 512 KBytes of the internal Flash memory																		
G = 1 MBytes of the internal Flash memory																		
Package																		
T = LQFP																		
U = QFN																		
Temperature range																		
7 = -40 °C to +105 °C																		

For a list of available options (speed, package, etc.) or for more information concerning this device, please contact your local Artery sales office.

8 Document revision history

Table 68. Document revision history

Date	Version	Change
2023.7.10	2.00	Initial release
2023.10.17	2.01	Added Table 34 EMI characteristics to the section 5.3.10 EMC characteristics
2023.11.27	2.02	Added Section 5.3.20 EMAC characteristics

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